

PATENT ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

| SUBMISSION TYPE: | CORRECTIVE ASSIGNMENT | | | | | | | | | | | | |
|--|---|---------------|-------------------------|---|---------------------|-------------------|----------|-------|-------|----------------|-------|--------------|------------|
| NATURE OF CONVEYANCE: | Corrective Assignment to correct the Remove Patent Number 6440516. previously recorded on Reel 029485 Frame 0816. Assignor(s) hereby confirms the Assignment. | | | | | | | | | | | | |
| CONVEYING PARTY DATA | | | | | | | | | | | | | |
| <table border="1"> <thead> <tr> <th>Name</th> <th>Execution Date</th> </tr> </thead> <tbody> <tr> <td>STMicroelectronics, Inc. (formerly known as SGS-Thomson Microelectronics, Inc.)</td> <td>01/27/2008</td> </tr> </tbody> </table> | | Name | Execution Date | STMicroelectronics, Inc. (formerly known as SGS-Thomson Microelectronics, Inc.) | 01/27/2008 | | | | | | | | |
| Name | Execution Date | | | | | | | | | | | | |
| STMicroelectronics, Inc. (formerly known as SGS-Thomson Microelectronics, Inc.) | 01/27/2008 | | | | | | | | | | | | |
| RECEIVING PARTY DATA | | | | | | | | | | | | | |
| <table border="1"> <tr> <td>Name:</td> <td>Micron Technology, Inc.</td> </tr> <tr> <td>Street Address:</td> <td>8000 S. Federal Way</td> </tr> <tr> <td>Internal Address:</td> <td>MS 1-525</td> </tr> <tr> <td>City:</td> <td>Boise</td> </tr> <tr> <td>State/Country:</td> <td>IDAHO</td> </tr> <tr> <td>Postal Code:</td> <td>83716-9632</td> </tr> </table> | | Name: | Micron Technology, Inc. | Street Address: | 8000 S. Federal Way | Internal Address: | MS 1-525 | City: | Boise | State/Country: | IDAHO | Postal Code: | 83716-9632 |
| Name: | Micron Technology, Inc. | | | | | | | | | | | | |
| Street Address: | 8000 S. Federal Way | | | | | | | | | | | | |
| Internal Address: | MS 1-525 | | | | | | | | | | | | |
| City: | Boise | | | | | | | | | | | | |
| State/Country: | IDAHO | | | | | | | | | | | | |
| Postal Code: | 83716-9632 | | | | | | | | | | | | |
| PROPERTY NUMBERS Total: 1 | | | | | | | | | | | | | |
| <table border="1"> <thead> <tr> <th>Property Type</th> <th>Number</th> </tr> </thead> <tbody> <tr> <td>Patent Number:</td> <td>5440516</td> </tr> </tbody> </table> | | Property Type | Number | Patent Number: | 5440516 | | | | | | | | |
| Property Type | Number | | | | | | | | | | | | |
| Patent Number: | 5440516 | | | | | | | | | | | | |
| CORRESPONDENCE DATA | | | | | | | | | | | | | |
| <p>Fax Number: <i>Correspondence will be sent via US Mail when the fax attempt is unsuccessful.</i></p> <p>Phone: (208) 3684591 Email: tpaulin@micron.com Correspondent Name: Micron Technology, Inc. Address Line 1: 8000 S. Federal Way Address Line 2: MS 1-525 Address Line 4: Boise, IDAHO 83716-9632</p> | | | | | | | | | | | | | |
| NAME OF SUBMITTER: | Michael E. Romani | | | | | | | | | | | | |
| <p>Total Attachments: 67 source=Assignment Cover Sheet#page1.tif source=Assignment Cover Sheet#page2.tif source=Assignment Cover Sheet#page3.tif</p> | | | | | | | | | | | | | |

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source=Numonyx_Micron#page7.tif
source=Numonyx_Micron#page8.tif
source=Numonyx_Micron#page9.tif
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source=Numonyx_Micron#page19.tif
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| PATENT ASSIGNMENT |
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Electronic Version v1.1

Stylesheet Version v1.1

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|---|-------------------------|
| SUBMISSION TYPE: | NEW ASSIGNMENT |
| NATURE OF CONVEYANCE: | ASSIGNMENT |
| CONVEYING PARTY DATA | |
| Name | Execution Date |
| STMicroelectronics, Inc. (formerly known as SGS-Thomson Microelectronics, Inc.) | 01/27/2008 |
| RECEIVING PARTY DATA | |
| Name: | Micron Technology, Inc. |
| Street Address: | 8000 S. Federal Way |
| Internal Address: | MS 1-525 |
| City: | Boise |
| State/Country: | IDAHO |
| Postal Code: | 83716-9632 |
| PROPERTY NUMBERS Total: 19 | |
| Property Type | Number |
| Patent Number: | 5526318 |
| Patent Number: | 5365129 |
| Patent Number: | 5349246 |
| Patent Number: | 5469116 |
| Patent Number: | 6440516 |
| Patent Number: | 5491444 |
| Patent Number: | 5424985 |
| Patent Number: | 5493537 |
| Patent Number: | 5471157 |
| Patent Number: | 5521880 |

PATENT

REEL: 029505 FRAME: 0013

| | |
|----------------|---------|
| Patent Number: | 5493532 |
| Patent Number: | 5625603 |
| Patent Number: | 5592422 |
| Patent Number: | 5619462 |
| Patent Number: | 5703512 |
| Patent Number: | 5612918 |
| Patent Number: | 5790462 |
| Patent Number: | 5557573 |
| Patent Number: | 5719445 |

CORRESPONDENCE DATA

Fax Number:

Phone: (208) 368-4591

Email: tpaulin@micron.com

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent via US Mail.

Correspondent Name: Micron Technology, Inc.

Address Line 1: 8000 S. Federal Way

Address Line 2: MS 1-525

Address Line 4: Boise, IDAHO 83716-9632

| | |
|--------------------|---------------------|
| NAME OF SUBMITTER: | Michael E. Romani |
| Signature: | /Michael E. Romani/ |
| Date: | 12/17/2012 |

Total Attachments: 60

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PATENT

REEL: 029505 FRAME: 0014

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source=Numonyx_Micron#page2.tif
source=Numonyx_Micron#page3.tif
source=Numonyx_Micron#page4.tif
source=Numonyx_Micron#page5.tif
source=Numonyx_Micron#page6.tif
source=Numonyx_Micron#page7.tif
source=Numonyx_Micron#page8.tif
source=Numonyx_Micron#page9.tif
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RECEIPT INFORMATION**PATENT****REEL: 029505 FRAME: 0015**

| | |
|---------------|------------|
| EPAS ID: | PAT2205058 |
| Receipt Date: | 12/17/2012 |
| Fee Amount: | \$760 |

PATENT

REEL: 029505 FRAME: 0016

ASSIGNMENT

WHEREAS, STMicroelectronics, Inc., (formerly known as SGS-Thomson Microelectronics, Inc.), a corporation organized under the laws of the State of Delaware, having a place of business at 1310 Electronics Drive, Carrollton, Texas 75006 (hereinafter referred to as "Assignor") has rights in and to the following:

LISTED IN EXHIBIT A

(said patents, patent applications and invention disclosures listed in Exhibit A being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Assignor is a wholly owned subsidiary of STMicroelectronics NV, a Dutch corporation organized under the laws of The Netherlands, acting through its Swiss branch, having an office at 39 Chemin du Champ-des-Filles, 1228 Plan-les-Ouates, Geneva, Switzerland (hereinafter referred to as "Assignee");

WHEREAS, Assignee requested Assignor to develop certain technology for Assignee;

WHEREAS, Assignee sponsored, paid for and is the equitable and beneficial owner of all resulting intellectual property resulting from such technology development, including SAID PATENT RIGHTS and related rights;

WHEREAS, Assignee and Assignor recognize that Assignee already owns all equitable and beneficial ownership in SAID PATENT RIGHTS and related rights;

WHEREAS, Assignor now desires to transfer the legal title in and to SAID PATENT RIGHTS to Assignee and confirm all ownership in Assignee to SAID PATENT RIGHTS and related rights that may have unintentionally remained in Assignor; and

WHEREAS, Assignee desires to perfect registration in Assignee's name all the above mentioned rights, title and interest in and to SAID PATENT RIGHTS and related rights.

NOW, THEREFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, Assignor does hereby transfer and assign to Assignee legal title, and any and all rights it may own (beyond said legal title, if any) in and to SAID PATENT RIGHTS, together with any and all continuations, continuations-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing (to the extent not already owned by Assignee), together

with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WITNESS WHEREOF, Assignor has caused this Assignment to be executed by its duly authorized officer on this 21st day of January, 2008.

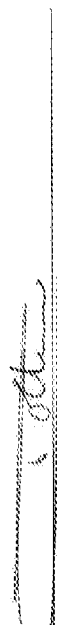
STMicroelectronics, Inc.

By: 

Printed Name: Reza Kazerooni

Title: President & CEO North America

STMicroelectronics NV

By: 

Printed Name: Peter Ollivier

Title: Corporate General Counsel

| US Pat. No. | US Ref | Country | Status | Non-US Pat. number | Filing Number |
|-------------|-------------|---------|-----------------------------------|--------------------|---------------|
| 5400007 | 92-C-081 | US | Granted | | 08020045 |
| 5424983 | 92-C-081 | US | Granted | 3517442 | 022811 |
| 5445432 | 92-C-082 | US | Granted | | 06954705 |
| 5300828 | 92-C-083 | US | Granted | | 07936389 |
| 5365129 | 92-C-072 | US | Granted | | 08055080 |
| 5339277 | 92-C-080 | US | Granted | | 08056078 |
| 5341339 | 92-C-080 | GB | Granted | 522803 | 84303082.5 |
| 5349246 | 92-C-082 | FR | Granted | 542803 | 84303082.5 |
| 5331228 | 92-C-247/25 | US | Granted | | 09058376 |
| 6404331 | 92-C-277/28 | US | Granted | | 07823136 |
| 5781043 | 92-C-277/28 | FR | Granted | 637036 | 08099606 |
| | 93-C-087 | US | Granted | | 84305553.3 |
| | 93-C-007 | US | Request for Continued Examination | | 09522830 |
| | | | | | 09618821 |
| 5471431 | 93-C-010 | US | Granted | | 08051184 |
| RE36319 | 93-C-013 | US | Granted | | 08969042 |
| 5458243 | 93-C-023 | US | Granted | | 08085760 |
| 5428311 | 93-C-024 | US | Granted | | 08085580 |
| 545537 | 93-C-026 | US | Granted | | 08410383 |
| 546813 | 93-C-031 | US | Granted | | 08487189 |
| 537150 | 93-C-034 | US | Granted | | 08095847 |
| 5479587 | 93-C-034 | US | Granted | | 08298786 |
| 5402379 | 93-C-038 | US | Granted | | 08114749 |
| 5579326 | 93-C-039 | US | Granted | | 08189588 |
| 5841783 | 93-C-059 | US | Granted | | 08547222 |
| 572456 | 93-C-040 | US | Granted | | 08114747 |
| 5252427 | 93-C-041 | US | Granted | | 08189588 |
| 540516 | 93-C-043 | US | Granted | | 08139226 |
| 5935427 | 93-C-056 | US | Granted | | 08188158 |
| 6101618 | 93-C-057 | US | Granted | | 08172854 |
| 5558061 | 93-C-058 | US | Granted | | 08172848 |
| 5703783 | 93-C-059 | US | Granted | | 08492219 |
| 5392108 | 93-C-060 | US | Granted | | 08171139 |
| 5418756 | 93-C-081 | US | Granted | 3526821 | 08129677 |
| 5589073 | 93-C-079 | US | Granted | | 08129763 |
| 6440178 | 93-C-080 | US | Granted | | 08172853 |
| 5491444 | 93-C-081 | US | Granted | | 08160608 |
| 5777051 | 93-C-082 | US | Granted | | 08174139 |
| 5424983 | 93-C-083 | US | Granted | | 08173197 |
| 5385324 | 94-C-004 | US | Granted | | 08170812 |
| 5317455 | 94-C-003 | US | Granted | | 08340136 |
| 5471157 | 94-C-005 | US | Granted | | 08220878 |
| | 94-C-005 | JP | Granted | | 08220834 |
| | 94-C-005 | GB | Granted | 3573572 | 774338 |
| 5506874 | 94-C-005 | FR | Granted | | 94309216.9 |
| 5458746 | 94-C-028 | US | Granted | 675597 | 84309216.9 |
| 5452794 | 94-C-030 | US | Granted | | 08362187 |
| 5521880 | 94-C-051 | US | Granted | | 08267686 |
| 5493532 | 94-C-052 | US | Granted | | 08251718 |
| 5585783 | 94-C-056 | US | Granted | | 08251337 |
| 5982185 | 94-C-057 | US | Granted | | 08282177 |
| 5561112 | 94-C-080 | US | Granted | | 08282047 |
| 5493416 | 94-C-087 | US | Granted | | 08288334 |
| 5502678 | 94-C-070 | US | Granted | | 08318059 |
| 5517148 | 94-C-081 | US | Granted | | 08319337 |
| 5510669 | 94-C-092 | US | Granted | | 08331892 |
| 5574885 | 94-C-093 | US | Granted | | 08331899 |
| 5722653 | 94-C-098 | US | Granted | | 08438903 |
| 5560185 | 94-C-114 | US | Granted | | 08369187 |
| 5586287 | 94-C-116 | US | Granted | | 08370824 |
| 5548241 | 94-C-121 | US | Granted | | 08360228 |
| 5594373 | 94-C-123 | US | Granted | | 08360229 |
| 5581208 | 94-C-124 | US | Granted | 3679178 | 7330188 |
| 5589125 | 94-C-124 | JP | Granted | | 08359397 |
| 5593794 | 94-C-128 | US | Granted | 3598837 | 83186398 |
| 5917553 | 94-C-128 | US | Granted | | 08369227 |
| 5572470 | 94-C-133 | US | Granted | | 08369227 |
| 5525603 | 95-C-007 | US | Granted | | 08369227 |
| 5792347 | 95-C-009 | US | Granted | | 08439349 |
| 5840128 | 95-C-017 | US | Granted | | 08477244 |
| | 95-C-017 | FR | Granted | | 08567481 |
| 5576658 | 95-C-018 | US | Granted | | 08567481 |
| RE37878 | 95-C-028 | US | Granted | | 08414103 |
| 5788208 | 95-C-036 | US | Granted | | 08568201 |
| | 95-C-036 | GB | Granted | | 08484491 |
| 582422 | 95-C-052 | FR | Granted | 747624 | 95303448.3 |
| 5618462 | 95-C-052 | US | Granted | 747824 | 95303448.3 |
| | 95-C-057 | US | Granted | | 08439158 |
| 5745420 | 95-C-058 | US | Granted | | 8200145 |
| 6703512 | 95-C-058 | US | Granted | | 08833587 |
| 5608573 | 95-C-071 | US | Granted | | 08712960 |
| 5649593 | 95-C-090 | US | Granted | | 08508551 |
| 602839 | 95-C-091 | US | Granted | | 08509211 |
| 6144564 | 95-C-137 | US | Granted | | 08565429 |
| 6297986 | 95-C-137 | US | Granted | | 08567709 |
| 5701275 | 95-C-138 | US | Granted | | 09457558 |
| 5788980 | 95-C-138 | US | Granted | | 08568730 |
| | | | | | 08878512 |

| US Pat No. | US ST Ref | Country | Status | Non-US Pat. number | Filing Number |
|------------|------------|---------|-----------------------------------|--------------------|---------------|
| 5901563 | 95-C-139 | US | Granted | | 0858588 |
| 5790402 | 95-C-143 | US | Granted | | 08590827 |
| 5957422 | 95-C-144 | US | Granted | | 08588662 |
| 5745432 | 95-C-147 | US | Granted | | 08589741 |
| 5909960 | 95-C-148 | US | Granted | | 08582285 |
| 5825691 | 95-C-148 | JP | Filing | | 98724 |
| 5825691 | 95-C-149 | US | Granted | | 08583788 |
| 5825691 | 95-C-149 | JP | Filing | | 98736 |
| 5825691 | 95-C-150 | US | Granted | | 08587728 |
| 5825691 | 95-C-151 | US | Granted | | 08586833 |
| 5848016 | 95-C-151 | US | Granted | | 08529833 |
| 6864698 | 95-C-156 | US | Granted | | 08587711 |
| 6006339 | 95-C-156 | US | Granted | | 09020430 |
| 5919468 | 95-C-198 | US | Filing | | 98721 |
| 5883338 | 95-C-199 | US | Granted | | 08589024 |
| 5825691 | 95-C-200 | US | Granted | | 08529927 |
| 5825691 | 95-C-203 | US | Granted | | 0854777 |
| 5825691 | 95-C-203 | JP | Filing | | 8222288 |
| 5825691 | 95-C-203 | US | Granted | | 8222288 |
| 5825691 | 95-C-203 | FR | Granted | 760518 | 95305855 |
| 5825691 | 95-C-203 | DE | Granted | 760518 | 95305855 |
| 5825691 | 95-C-203 | US | Granted | 69017390 | 95305855 |
| 5825691 | 95-C-203 | US | Granted | | 08484609 |
| 5782951 | 95-C-209 | JP | Filing | | 8219954 |
| 5784331 | 95-C-208 | US | Granted | | 08579864 |
| 5805027 | 95-C-208 | US | Granted | | 08542271 |
| 5784592 | 95-C-261 | US | Granted | | 08771642 |
| 5825691 | 95-C-251 | JP | Filing | | 9345970 |
| 6037792 | 95-C-253 | US | Granted | | 08771645 |
| 5810485 | 95-C-253 | US | Granted | | 09491654 |
| 6518746 | 95-C-253 | US | Granted | | 09831820 |
| 5718445 | 95-C-253 | US | Granted | | 08780053 |
| 5959910 | 95-C-257 | US | Granted | | 08844696 |
| 6037799 | 95-C-117 | US | Granted | | 08758587 |
| 6058450 | 95-C-127 | US | Granted | | 08771643 |
| 5825691 | 95-C-127 | US | Request for Continued Examination | | 10745606 |
| 5808947 | 95-C-52/54 | US | Granted | | 08710357 |
| 595444 | 97-C-002 | US | Granted | | 08000547 |
| 6107865 | 97-C-009 | US | Granted | | 09429864 |
| 5995421 | 97-C-175 | US | Granted | | 09087399 |
| 6519582 | 97-LJ-186 | US | Granted | | 09205996 |
| 97-LJ-186 | 97-LJ-186 | GB | Granted | 1006448 | 59309641 |
| 97-LJ-186 | 97-LJ-186 | FR | Granted | 1006448 | 59309641 |
| 611288 | 98-C-072 | US | Granted | | 09217321 |
| 604260 | 98-C-072 | US | Granted | | 08780053 |
| 603497 | 98-C-099 | US | Granted | | 09183331 |
| 6081466 | 98-C-114 | US | Granted | | 09183451 |
| 6041000 | 98-C-115 | US | Granted | | 09183940 |
| 6434,189 | 98-OT-144 | US | Granted | | 09386024 |
| 98-OT-144 | 98-OT-144 | GB | Granted | 1061659 | 00305020 |
| 98-OT-144 | 98-OT-144 | FR | Granted | 1061659 | 00305020 |
| 6901794 | 98-C-181 | US | Granted | | 09476036 |
| 6994192 | 98-C-181 | US | Granted | | 09553185 |
| 6781816 | 98-C-180 | US | Granted | | 10642844 |
| 4802124 | 96-F-005 | US | Granted | | 07081032 |
| 4787068 | 96-P-007 | US | Granted | | 07081037 |

| ST Ref | Country | Filing Number | Status |
|----------|---------|---------------|---------------------|
| 03-C-041 | US | 10690366 | Notice of Allowance |
| 03-C-041 | JP | 2004307123 | Filing |
| 03-C-041 | EP | 04250444.3 | Publication |
| 03-C-046 | US | 10788581 | Notice of Allowance |
| 03-C-132 | US | 10595751 | Publication |
| 03-C-133 | US | 10753365 | Notice of Allowance |
| 03-C-134 | US | 11012712 | Publication |
| 03-C-136 | US | 11012533 | Publication |
| 03-C-137 | US | 11012712 | Publication |

EXHIBIT A
ST Ref - Invention Disclosure(G)
08-C-082

CONFIRMATION OF ASSIGNMENT

WHEREAS, STMicroelectronics NV, a Dutch corporation organized under the laws of The Netherlands, acting through its Swiss branch, having an office at 39 Chemin du Champ-des-Filles, 1228 Plan-les-Ouates, Geneva, Switzerland (hereinafter referred to as "Assignor") previously assigned its rights in and to the following:

LISTED IN EXHIBIT A

(said patents, patent applications and invention disclosures listed in Exhibit A being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Numonyx BV is a corporation having a principal place of business at A-ONE Biz Center, Z.A. Vers la Piece, Rte de l'Etraz, 1180 Rolle, Switzerland (hereinafter referred to as "Assignee") previously obtained rights to SAID PATENT RIGHTS;

NOW, THEREFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, this agreement confirms that Assignor has sold, conveyed, transferred and assigned to Assignee, its successors, assigns and legal representatives, subject to prior encumbrances, all right, title and interest in and to SAID PATENT RIGHTS, together with any and all continuations, continuations-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing, together with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WITNESS WHEREOF, Assignor has caused this Confirmation of Assignment to be executed by its duly authorized officer on this 25 day of April, 2012.

ASSIGNOR

STMicroelectronics, NV

By: [Signature]

Printed Name: P. O'Connell

Title: Corporate General Counsel

ASIGNEE

Numonyx, BV

By: [Signature]

Printed Name: Thomas L. Law Jr.

Title: Director

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 6639833 | US | | 10076023 |
| | EP | | 01830097.0 |
| 6724658 | US | | 10133231 |
| | EP | | 01830276.0 |
| 7017099 | US | | 10159782 |
| | IT | | TO01A00529 |
| 7084032 | US | | 10356351 |
| | US | | 11476361 |
| | EP | | 02425044.1 |
| | US | | 10323615 |
| | EP | | 02014408.5 |
| 6720271 | US | | 10189152 |
| 6816001 | US | | 10290030 |
| | JP | | 02302131 |
| | EP | | 01830695.1 |
| 6496439 | US | | 09895491 |
| 6292405 | US | | 09636363 |
| 6701419 | US | | 09977561 |
| | EP | | 00830675.5 |
| 6489807 | US | | 09925842 |
| | IT | VA20000027 | VA00A00027 |
| 6650153 | US | | 10033711 |
| | IT | 1220448 | 01130836.8 |
| | GB | 1220448 | 01130836.8 |
| | FR | 1220448 | 01130836.8 |
| | DE | 60102212 | 01130836.8 |
| 6650569 | US | | 10076134 |
| | IT | | TO01A00143 |
| 6560145 | US | | 10068560 |
| | EP | | 01830070.7 |
| 6674666 | US | | 10077687 |
| | IT | | TO01A00148 |
| 6917994 | US | | 10115888 |
| | IT | | TO01A00333 |
| 6549486 | US | | 09998903 |
| 6720822 | US | | 09998902 |
| 6549048 | US | | 09925979 |
| | FR | 2812984 | 0010554 |
| 6807103 | US | | 10438733 |
| | GB | 1342244 | 01996861.9 |
| | FR | 1342244 | 01996861.9 |
| 6774663 | US | | 10060105 |
| | GB | 1227329 | 02290165.6 |
| | FR | 1227329 | 02290165.6 |
| 6928530 | US | | 10081740 |
| | JP | | 200246868 |
| | EP | | 02290278.7 |
| 6568510 | US | | 09997214 |
| 6714453 | US | | 10352581 |
| | FR | 2816750 | 0014742 |
| 5557124 | US | | 08212176 |
| 6654287 | US | | 10171078 |
| | IT | 1325862 | MI01A01232 |
| 6567296 | US | | 09041684 |
| | IT | 1306852 | 02078984.8 |
| | GB | 1306852 | 02078984.8 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 5031152 | US | | 07414775 |
| | KR | 223623 | 9013107 |
| 5072137 | US | | 07569009 |
| 5053996 | US | | 07661555 |
| 5265100 | US | | 07552567 |
| 5311473 | US | | 08071448 |
| 5161159 | US | | 07568968 |
| | JP | 3616564 | 2000317923 |
| 5408435 | US | | 07984233 |
| 5706232 | US | | 08424722 |
| 5119340 | US | | 07588601 |
| 5128897 | US | | 07588577 |
| 5072138 | US | | 07570203 |
| 5099148 | US | | 07601288 |
| | GB | 482869 | 91309721.8 |
| | FR | 482869 | 91309721.8 |
| 5121358 | US | | 07588609 |
| 5526318 | US | | 08376127 |
| 5124951 | US | | 07588600 |
| 5124584 | US | | 07601287 |
| | JP | 3375143 | 3272191 |
| | GB | 482868 | 91309720.0 |
| | FR | 482868 | 91309720.0 |
| 5265054 | US | | 07827403 |
| 5297090 | US | | 07627050 |
| 5258952 | US | | 07627236 |
| | JP | 3609837 | 3330242 |
| | GB | 490679 | 91311570.5 |
| | FR | 490679 | 91311570.5 |
| 5355340 | US | | 08101347 |
| 5311477 | US | | 07731803 |
| 5319768 | US | | 07694451 |
| | GB | 0514050 | 92303960.6 |
| | FR | 0514050 | 92303960.6 |
| 5428632 | US | | 07693670 |
| 5339322 | US | | 07677313 |
| | GB | 0506474 | 92302736.1 |
| | FR | 0506474 | 92302736.1 |
| 5297094 | US | | 07731487 |
| 5287322 | US | | 07731802 |
| 5321314 | US | | 08109697 |
| 5377153 | US | | 07982988 |
| 5623438 | US | | 08697482 |
| 5734602 | US | | 08651233 |
| 5285419 | US | | 07809393 |
| 5748556 | US | | 08777836 |
| 5377143 | US | | 08040916 |
| 5483489 | US | | 08307332 |
| 5487048 | US | | 08041321 |
| 5295104 | US | | 07809735 |
| 5471426 | US | | 07830315 |
| | JP | 3598119 | 514481 |
| 5257229 | US | | 07830314 |
| 5311467 | US | | 07864481 |
| 5357235 | US | | 07876959 |
| | JP | 3509894 | 5104270 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 5319347 | US | | 07876851 |
| | JP | 3515591 | 5104305 |
| 5386377 | US | | 08122804 |
| | GB | 564137 | 93302156.0 |
| | FR | 564137 | 93302156.0 |
| 5357236 | US | | 07890919 |
| 5355113 | US | | 07901667 |
| 5381126 | US | | 07923855 |
| 5508679 | US | | 08303172 |
| 5257226 | US | | 07809733 |
| 5534448 | US | | 08282408 |
| 5589701 | US | | 08486747 |
| 5831457 | US | | 08477283 |
| 5355344 | US | | 07975628 |
| 5526317 | US | | 08263048 |
| 6262617 | US | | 08367681 |
| | GB | 586207 | 93306835.5 |
| | FR | 586207 | 93306835.5 |
| | DE | 69309196 | 93306835.5 |
| 5422591 | US | | 08176960 |
| 5485430 | US | | 08306527 |
| 5455802 | US | | 07995581 |
| 5389577 | US | | 08180692 |
| 5400007 | US | | 08020045 |
| | JP | 3517442 | 622814 |
| 5424988 | US | | 07954276 |
| 5644542 | US | | 08460409 |
| 5300828 | US | | 07938399 |
| 5365129 | US | | 08055080 |
| 5339277 | US | | 08056078 |
| | GB | 622803 | 94303082.5 |
| | FR | 622803 | 94303082.5 |
| 5341336 | US | | 08056376 |
| 5349246 | US | | 07995666 |
| 5331228 | US | | 07923135 |
| 5404331 | US | | 08099606 |
| | GB | 637036 | 94305553.3 |
| | FR | 637036 | 94305553.3 |
| 5644216 | US | | 08454926 |
| 5627403 | US | | 08473552 |
| 5795821 | US | | 08751244 |
| | IT | 0627763 | 93830243.7 |
| | GB | 0627763 | 93830243.7 |
| | FR | 0627763 | 93830243.7 |
| | DE | 69333722 | 93830243.7 |
| 5546044 | US | | 08311941 |
| 5535157 | US | | 08347653 |
| 5612641 | US | | 08380309 |
| 5659501 | US | | 08639931 |
| 5818760 | US | | 08871226 |
| | JP | 2718902 | 28634994 |
| | GB | 0654791 | 93830464.9 |
| | FR | 0654791 | 93830464.9 |
| 5566114 | US | | 08349783 |
| 5644529 | US | | 08635455 |
| 5659509 | US | | 08391999 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 5493531 | US | | 08350961 |
| 5708601 | US | | 08602237 |
| 5559743 | US | | 08412550 |
| 5546054 | US | | 08377524 |
| | JP | 2743853 | 720895 |
| | IT | 0665485 | 94830022.3 |
| | GB | 0665485 | 94830022.3 |
| | FR | 0665485 | 94830022.3 |
| | DE | 69413793 | 94830022.3 |
| 5515332 | US | | 08391160 |
| 5663921 | US | | 08391159 |
| 5717642 | US | | 08803915 |
| 5687135 | US | | 08700126 |
| 5594703 | US | | 08365510 |
| 5768115 | US | | 08855922 |
| 5499217 | US | | 08348461 |
| 5627790 | US | | 08408589 |
| 5717698 | US | | 08345530 |
| 5600600 | US | | 08381530 |
| 5600594 | US | | 08412326 |
| 5687124 | US | | 08521304 |
| 5583820 | US | | 08366211 |
| 5748548 | US | | 08711132 |
| | IT | 0661713 | 93830537.2 |
| | GB | 0661713 | 93830537.2 |
| | FR | 0661713 | 93830537.2 |
| | DE | 69325277 | 93830537.2 |
| 6392469 | US | | 08347788 |
| 5617356 | US | | 08395361 |
| 5586077 | US | | 08366212 |
| 5519656 | US | | 08366259 |
| 5659516 | US | | 08368211 |
| 5905677 | US | | 08831046 |
| 5548554 | US | | 08365154 |
| 5541884 | US | | 08391147 |
| | JP | 2737686 | 753777 |
| 5532972 | US | | 08391920 |
| 5563826 | US | | 08422813 |
| 5638327 | US | | 08412162 |
| 5602786 | US | | 08389599 |
| 5541880 | US | | 08411904 |
| 5576990 | US | | 08367538 |
| 5486486 | US | | 831792 |
| 5528536 | US | | 8344232 |
| 5781043 | US | | 08932930 |
| | US | | 09616821 |
| 5471431 | US | | 08051184 |
| RE36319 | US | | 08966042 |
| 5349243 | US | | 08085760 |
| 5428311 | US | | 08085580 |
| 5546537 | US | | 08410383 |
| 5627793 | US | | 08413789 |
| 5469116 | US | | 08188153 |
| 5377150 | US | | 08099947 |
| 5473567 | US | | 08298766 |
| 5402379 | US | | 08114749 |

Exhibit A

FMG with US Granted:

| US Pat.No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 5579326 | US | | 08189589 |
| 5841789 | US | | 08647222 |
| 5572456 | US | | 08114747 |
| 6014050 | US | | 08801452 |
| 6252447 | US | | 09139225 |
| 5440516 | US | | 08188158 |
| 5835427 | US | | 08172854 |
| 6101618 | US | | 08172848 |
| 5568061 | US | | 08492219 |
| 5708789 | US | | 08717139 |
| 5396108 | US | | 08129257 |
| | JP | 3526921 | 6236207 |
| 5418756 | US | | 08129763 |
| 5568073 | US | | 08172853 |
| 5440178 | US | | 08160608 |
| 5491444 | US | | 08174139 |
| 5577051 | US | | 08173197 |
| 5424985 | US | | 08170612 |
| 5493537 | US | | 08202830 |
| | JP | 2720013 | 3140291994 |
| 5430319 | US | | 08246070 |
| 5661324 | US | | 08399900 |
| | IT | 651394 | 94460037.8 |
| | GB | 651394 | 94460037.8 |
| | FR | 651394 | 94460037.8 |
| | DE | 651394 | 94460037.8 |
| 5555216 | US | | 08361313 |
| 5537349 | US | | 08361996 |
| | JP | 2886472 | 33625894 |
| 5886386 | US | | 08379337 |
| 6265277 | US | | 09220635 |
| 5900756 | US | | 08767521 |
| 5579265 | US | | 08393464 |
| | IT | 0669576 | 95400420.6 |
| | GB | 0669576 | 95400420.6 |
| | FR | 0669576 | 95400420.6 |
| | DE | 0669576 | 95400420.6 |
| 5610860 | US | | 08402519 |
| 5729162 | US | | 08811358 |
| | JP | 2919299 | 9956195 |
| 5606523 | US | | 08380737 |
| 5592417 | US | | 08380738 |
| 5677870 | US | | 08752814 |
| 5721706 | US | | 08754432 |
| 5561621 | US | | 08381529 |
| 5612611 | US | | 08423398 |
| | FR | 678868 | 95470013.4 |
| 5619451 | US | | 08421671 |
| 5796653 | US | | 08394314 |
| | JP | 2833646 | 5972695 |
| 5644530 | US | | 08418636 |
| 5651128 | US | | 08484873 |
| 5594693 | US | | 08408016 |
| 5590075 | US | | 08479081 |
| 5696716 | US | | 08794965 |
| 5715204 | US | | 08432838 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| | FR | 0737643 | 95830153.3 |
| | DE | 69518826 | 95830153.3 |
| 5764570 | US | | 08691796 |
| | JP | | |
| | GB | 0757357 | 95830354.7 |
| | FR | 0757357 | 95830354.7 |
| 5841728 | US | | 08724495 |
| | GB | 768672 | 95830405.7 |
| | FR | 768672 | 95830405.7 |
| 5905683 | US | | 08940045 |
| 5517455 | US | | 08220976 |
| 5471157 | US | | 08220834 |
| | JP | 3573372 | 774338 |
| | GB | 675597 | 94309218.9 |
| | FR | 675597 | 94309218.9 |
| 5530674 | US | | 08235161 |
| 5583816 | US | | 08267667 |
| 5455799 | US | | 08267666 |
| 5521880 | US | | 08251718 |
| 5493532 | US | | 08251337 |
| 5589783 | US | | 08282177 |
| 5982188 | US | | 08282047 |
| 5566112 | US | | 08288334 |
| 5570316 | US | | 08438276 |
| 5495446 | US | | 08316087 |
| 5502678 | US | | 08315337 |
| 5517148 | US | | 08331892 |
| 5610866 | US | | 08331699 |
| 5574688 | US | | 08438903 |
| 5579263 | US | | 08362187 |
| 5568084 | US | | 08357664 |
| 5654663 | US | | 08631063 |
| 5596297 | US | | 08360228 |
| 5548241 | US | | 08360229 |
| | JP | 3679178 | 7330189 |
| 5594373 | US | | 08359397 |
| 5581209 | US | | 08359927 |
| | JP | 3596637 | 33198395 |
| 5598122 | US | | 08359926 |
| 5589794 | US | | 08360227 |
| 5917353 | US | | 08848342 |
| 5572470 | US | | 08438349 |
| 6052806 | US | | 08519192 |
| | JP | 2898230 | 21890495 |
| 6052806 | US | | 08519192 |
| | JP | 2898230 | 21890495 |
| 5734608 | US | | 08580549 |
| 5675539 | US | | 08575953 |
| 5742546 | US | | 08526500 |
| 5699295 | US | | 08649282 |
| 5652720 | US | | 08573897 |
| 5841314 | US | | 08663524 |
| | FR | 750244 | 96470009.0 |
| 5717323 | US | | 08576881 |
| 5774390 | US | | 08652710 |
| 5701265 | US | | 08593650 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| | IT | 0856886 | 97830029.1 |
| | GB | 0856886 | 97830029.1 |
| | FR | 0856886 | 97830029.1 |
| 5917768 | US | | 08847385 |
| | GB | 0805453 | 96830239.8 |
| 5878049 | US | | 08840056 |
| | GB | 0805452 | 96830238.0 |
| | FR | 0805452 | 96830238.0 |
| 5777941 | US | | 08853732 |
| | GB | 0810606 | 96830275.2 |
| | FR | 0810606 | 96830275.2 |
| 5751654 | US | | 08826223 |
| | GB | 0798742 | 96830166.3 |
| 6148413 | US | | 08835030 |
| | GB | 0798726 | 96830161.4 |
| 5854770 | US | | 08791746 |
| 5946237 | US | | 08826489 |
| 6212096 | US | | 09351603 |
| | IT | 0798727 | 96830162.2 |
| | GB | 0798727 | 96830162.2 |
| 5831891 | US | | 08812595 |
| | GB | 797208 | 96830128.3 |
| | FR | 797208 | 96830128.3 |
| 5859810 | US | | 08826009 |
| | GB | 0798730 | 96830169.7 |
| | FR | 0798730 | 96830169.7 |
| 5625603 | US | | 08477244 |
| 5793247 | US | | 08667481 |
| 5640122 | US | | 08464551 |
| | GB | 747800 | 96303214.9 |
| | FR | 747800 | 96303214.9 |
| 5576656 | US | | 08414103 |
| RE37876 | US | | 09568201 |
| 5768206 | US | | 08484491 |
| | GB | 747824 | 96303448.3 |
| | FR | 747824 | 96303448.3 |
| 5592422 | US | | 08476658 |
| 5619462 | US | | 08509158 |
| | JP | | 8200145 |
| 5745420 | US | | 08833582 |
| 5703512 | US | | 08712960 |
| 5608678 | US | | 08509351 |
| 5648933 | US | | 08509211 |
| 5629896 | US | | 08521800 |
| 5612918 | US | | 08582424 |
| 6144594 | US | | 08587709 |
| 6297996 | US | | 09457558 |
| 5701275 | US | | 08588730 |
| 5798980 | US | | 08878612 |
| 5801563 | US | | 08588988 |
| 5790462 | US | | 08580827 |
| 5657292 | US | | 08588662 |
| 5845059 | US | | 08588762 |
| 5745432 | US | | 08589141 |
| 5808960 | US | | 08858295 |
| | JP | | 96024 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 5825691 | US | | 08858788 |
| | JP | | 96236 |
| 5802004 | US | | 08587728 |
| 5828622 | US | | 08944649 |
| 5848018 | US | | 08926833 |
| 5864696 | US | | 08587711 |
| 6006339 | US | | 09020430 |
| | JP | | 96721 |
| 5619466 | US | | 08589024 |
| 5883838 | US | | 08929987 |
| 5896336 | US | | 08974747 |
| 5633828 | US | | 08519075 |
| | JP | | 8222288 |
| | GB | 760518 | 96305856.5 |
| | FR | 760518 | 96305856.5 |
| | DE | 69617336 | 96305856.5 |
| 5557573 | US | | 08484609 |
| | JP | | 8219954 |
| 5812446 | US | | 08623044 |
| | JP | 2727527 | 10419096 |
| 5760638 | US | | 08664083 |
| | FR | 762428 | 96460031.6 |
| 5801577 | US | | 08762677 |
| 5737266 | US | | 08738231 |
| 5950224 | US | | 08797948 |
| 5886549 | US | | 08792962 |
| 5850092 | US | | 08833925 |
| 6074916 | US | | 09164761 |
| | GB | 0802569 | 96830212.5 |
| 5881001 | US | | 08825098 |
| | GB | 0798741 | 96830165.5 |
| | FR | 0798741 | 96830165.5 |
| 5959935 | US | | 08865748 |
| 5929674 | US | | 08846757 |
| | IT | 0805556 | 96830247.1 |
| | GB | 0805556 | 96830247.1 |
| 5822259 | US | | 08846755 |
| | IT | 0806771 | 96830243.0 |
| | GB | 0806771 | 96830243.0 |
| 5859797 | US | | 08846753 |
| | IT | 805456 | 96830242.2 |
| | GB | 805456 | 96830242.2 |
| 6018255 | US | | 08862563 |
| 6094073 | US | | 09432642 |
| | GB | 809254 | 96830299.2 |
| 6128225 | US | | 08879017 |
| | JP | | 9161556 |
| | GB | 814480 | 96830344.6 |
| | FR | 814480 | 96830344.6 |
| 5903498 | US | | 08877927 |
| | GB | | 96830345.3 |
| | EP | | 96830345.3 |
| 5805500 | US | | 08877921 |
| | JP | | 9161557 |
| | GB | 814482 | 96830346.1 |
| | FR | 814482 | 96830346.1 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| | JP | | 9346027 |
| 5719445 | US | | 08780053 |
| 5959910 | US | | 08844696 |
| 6037799 | US | | 08758587 |
| 6059450 | US | | 08771643 |
| | US | | 10145606 |
| 5808947 | US | | 08710357 |
| 5923590 | US | | 08873502 |
| 6085280 | US | | 08853526 |
| 6049497 | US | | 08957715 |
| 5859798 | US | | 08934696 |
| 5787040 | US | | 08916054 |
| 5903141 | US | | 08791383 |
| 6119210 | US | | 08915855 |
| 5870336 | US | | 08957666 |
| 6281723 | US | | 08993071 |
| | FR | 2757712 | 9615671 |
| | FR | 2758022 | 9616355 |
| 6097631 | US | | 09275327 |
| | FR | 2776820 | 9803786 |
| 6138220 | US | | 08991693 |
| 6178490 | US | | 08991428 |
| 6002619 | US | | 08994889 |
| 5889702 | US | | 09031748 |
| 5969961 | US | | 09059088 |
| 6140876 | US | | 09188071 |
| | FR | 2770947 | 9714018 |
| 5966034 | US | | 09087478 |
| | FR | 2764135 | 9706703 |
| 6127898 | US | | 09005722 |
| 5959886 | US | | 09009088 |
| 5953253 | US | | 09035654 |
| 6011724 | US | | 08980195 |
| 5862075 | US | | 08970445 |
| 6104644 | US | | 09013966 |
| 6205512 | US | | 09056921 |
| 6279068 | US | | 09746472 |
| 6434056 | US | | 09746473 |
| | GB | 875899 | 98400661.9 |
| | FR | 875899 | 98400661.9 |
| 5991199 | US | | 09012938 |
| 6141254 | US | | 09355064 |
| | IT | 954865 | 98903102.6 |
| | GB | 954865 | 98903102.6 |
| | FR | 954865 | 98903102.6 |
| | DE | 954865 | 98903102.6 |
| 6060932 | US | | 09118953 |
| | FR | 0898356 | 98401807.7 |
| | DE | 0898356 | 98401807.7 |
| 6888225 | US | | 10323961 |
| 6061286 | US | | 09053720 |
| | IT | 0869506 | 97830160.4 |
| | GB | 0869506 | 97830160.4 |
| 6075718 | US | | 09039588 |
| | IT | 1291209 | TO97A00227 |
| 6212128 | US | | 09093382 |

Exhibit A

FMG with US Granted:

| US Pat No. | Country | Non-US Pat. number | Filing Number |
|------------|---------|--------------------|---------------|
| 6091642 | US | | 09234942 |
| | IT | 0932161 | 98830024.0 |
| 6266222 | US | | 09223621 |
| | IT | 0932202 | 97830741.1 |
| | FR | 0932202 | 97830741.1 |
| 6242793 | US | | 09231129 |
| 6372597 | US | | 09837137 |
| | JP | | 10370047 |
| | EP | | 97830742.9 |
| 6147902 | US | | 09320315 |
| | IT | 961287 | 98830324.4 |
| | GB | 961287 | 98830324.4 |
| | FR | 961287 | 98830324.4 |
| 6218265 | US | | 09336089 |
| | IT | 0971415 | 98830388.9 |
| | GB | 0971415 | 98830388.9 |
| | FR | 0971415 | 98830388.9 |
| | DE | 0971415 | 98830388.9 |
| 6111791 | US | | 09322644 |
| | IT | 1301398 | MI98A01193 |
| 6208705 | US | | 09262500 |
| | IT | 1298594 | MI98A00454 |
| 5995444 | US | | 08000547 |
| 6107865 | US | | 09429964 |
| 5995421 | US | | 09087399 |
| 6097633 | US | | 09182843 |
| | IT | 1295910 | MI97A02458 |
| 6867113 | US | | 09191743 |
| | EP | | 97830603.3 |
| 6133718 | US | | 09246029 |
| | IT | 1298560 | MI98A00219 |
| | IT | 1298938 | MI98A00351 |
| | IT | 1298939 | MI98A00352 |
| 6271571 | US | | 09276263 |
| | IT | 1298807 | MI98A00628 |
| 6466059 | US | | 09249834 |
| | IT | 936627 | 98830064.6 |
| | GB | 936627 | 98830064.6 |
| 6130844 | US | | 09257682 |
| | IT | 1302079 | TO98A00165 |
| 6064594 | US | | 09258224 |
| | IT | 1302080 | TO98A00166 |
| 6198672 | US | | 09257684 |
| | IT | 1302081 | TO98A00167 |
| 6034889 | US | | 09177899 |
| | IT | 918336 | 98402620.3 |
| | GB | 918336 | 98402620.3 |
| | FR | 918336 | 98402620.3 |
| | DE | 918336 | 98402620.3 |
| 6040994 | US | | 09179621 |
| 5995416 | US | | 09156945 |
| | IT | 903750 | 98460036.1 |
| | GB | 903750 | 98460036.1 |
| | FR | 903750 | 98460036.1 |
| | DE | 903750 | 98460036.1 |
| 6128222 | US | | 09173136 |

Exhibit A

| FMG Pending | | |
|-------------|---------------|---------------|
| Country | Filing Number | Patent number |
| US | 10816271 | |
| US | 10816271 | |
| US | 10698747 | |
| US | 10698747 | |
| US | 11348513 | |
| US | 11348513 | |
| EP | 05425052.7 | |
| EP | 05425052.7 | |
| US | 11323937 | |
| EP | 05425001.4 | |
| US | 11437405 | |
| EP | 05425347.1 | |
| US | 11437268 | |
| EP | 05425348.9 | |
| US | 11300145 | |
| IT | MI04A002374 | |
| EP | 05027286.3 | |
| US | | |
| EP | 05425814.0 | |
| US | 11411982 | |
| US | 11411982 | |
| EP | 05425261.4 | |
| EP | 05425261.4 | |
| US | 11334205 | |
| IT | VA05A000001 | |
| US | 11340414 | |
| JP | 06015176 | |
| EP | 05100551.0 | |
| CN | 0610059263.5 | |
| US | 11444892 | |
| EP | 05104656.3 | |
| US | 11411010 | |
| IT | MI05A000780 | |
| US | 11304488 | |
| EP | 04106609.3 | |
| US | 11368363 | |
| EP | 05101659.0 | |
| US | | |
| IT | VA05A000061 | |
| US | 11432301 | |
| IT | MI05A000838 | |
| US | 11495886 | |
| EP | 05106976.3 | |
| US | | |
| US | | |
| EP | 05425835.5 | |
| EP | 05425835.5 | |
| US | 11367707 | |
| EP | 05101660.8 | |
| EP | 06425223.2 | |
| US | | |
| EP | 05425564.1 | |
| US | 11381426 | |
| IT | VA05A000028 | |
| US | 11238137 | |
| EP | 04425724.4 | |

PATENT ASSIGNMENT AGREEMENT

WHEREAS, Numonyx B.V., a company organized under the laws of Netherlands, having a place of business at A-ONE Biz Center, Z.A. Vers la Piece, Rte. De l'Etraz, 1180 Rolle, Switzerland (hereinafter referred to as "Assignor") has rights in and to the following:

1. U.S. Letters Patents Listed on Exhibit A,
2. U.S. Patent Applications listed on Exhibit B,
3. Foreign patents and patent applications listed on Exhibit C.

(said patents and patent applications listed in Exhibits A, B, and C being hereinafter referred to as "SAID PATENT RIGHTS"); and

WHEREAS, Micron Technology, Inc. is a corporation having a principal place of business at 8000 S. Federal Way, Boise, Idaho 83707, United States (hereinafter referred to as "Assignee") is desirous of obtaining rights to SAID PATENT RIGHTS;

NOW, THEREFORE, for and in consideration of good and valuable consideration the receipt, sufficiency and adequacy of which are hereby acknowledged, Assignor does hereby sell, convey, transfer and assign to Assignee, its successors, assigns and legal representatives, subject to prior encumbrances, all right, title and interest in and to SAID PATENT RIGHTS, together with any and all continuations, continuation-in-part, continuing prosecution applications, requests for continuing examinations, divisions, reissues, reexaminations, extensions, registrations, and foreign counterparts of any item in any of the foregoing, together with the right to sue for and be entitled to any damages, injunctive relief, and any other remedies of any kind for past, current and future infringement thereof.

IN WITNESS WHEREOF, Assignor has caused this Assignment to be executed by its duly authorized officer effective as of the 23 day of May, 2012

Numonyx B.V.

By: Thomas L. Laws Jr.
Printed Name: Thomas L. Laws Jr.
Title: Director

Micron Technology, Inc.

By: Roderic W. Lewis
Printed Name: Roderic W. Lewis
Title: V.P. of Legal Affairs

Exhibit A - US Issued Patents

| WIPO/CLASS | MasterType | MasterStatus | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|------------------|----------------|--------------|---|------------|------------|------------|-----------|---------|
| NMXXS-0001.00/RE | Utility - REIS | Expired | METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINED THEREBY | 12/12/1988 | 08/198,208 | 3/20/1990 | RE35,578 | US |
| NMXXS-0001.00/US | Utility - ORG | Expired | METHOD TO INSTALL AN ELECTRONIC COMPONENT AND ITS ELECTRICAL CONNECTIONS ON A SUPPORT, AND PRODUCT OBTAINED THEREBY | 12/12/1988 | 07/283,214 | 3/20/1990 | 4,908,937 | US |
| NMXXS-0002.00/US | Utility - ORG | Abandoned | METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT | 12/12/1988 | 07/283,305 | 7/17/1990 | 4,941,257 | US |
| NMXXS-0002.01/RE | Utility - REIS | Expired | METHOD FOR FIXING AN ELECTRONIC COMPONENT AND ITS CONTACTS TO A SUPPORT | 11/9/1994 | 08/336,560 | 7/17/1990 | RE35,385 | US |
| NMXXS-0003.00/US | Utility - ORG | Abandoned | ELECTRICALLY PROGRAMMABLE MEMORY WITH SEVERAL INFORMATION BITS PER CELL | 4/24/1989 | 07/342,476 | 10/16/1990 | 4,964,079 | US |
| NMXXS-0004.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE | 7/23/1993 | 08/096,684 | 12/3/1996 | 5,581,511 | US |
| NMXXS-0004.03/US | Utility - CON | Issued | INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE | 6/7/1995 | 08/486,363 | 6/10/1997 | 5,638,332 | US |
| NMXXS-0004.02/US | Utility - DIV | Issued | INTEGRATED CIRCUIT MEMORY DEVICE WITH BALANCING CIRCUIT INCLUDING FOLLOWER AMPLIFIER COUPLED TO BIT LINE | 6/7/1995 | 08/478,463 | 8/6/1996 | 5,544,114 | US |
| NMXXS-0005.00/US | Utility - ORG | Issued | DEVICE FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST POWER SUPPLY CUTS | 8/12/1993 | 08/100,867 | 12/5/1995 | 5,473,496 | US |
| NMXXS-0006.00/US | Utility - ORG | Issued | VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH BOOTSTRAPPED OSCILLATOR | 9/29/1993 | 08/128,871 | 12/31/1996 | 5,589,793 | US |
| NMXXS-0006.01/US | Utility - DIV | Issued | VOLTAGE BOOSTER CIRCUIT OF THE CHARGE-PUMP TYPE WITH A BOOTSTRAPPED OSCILLATOR | 6/6/1995 | 08/467,297 | 1/7/1997 | 5,592,115 | US |
| NMXXS-0007.01/US | Utility - CON | Issued | POWER-ON-RESET CIRCUIT PROVIDING PROTECTION AGAINST POWER SUPPLY INTERRUPTIONS | 8/8/1997 | 08/908,583 | 9/12/2000 | 6,118,315 | US |
| NMXXS-0008.00/US | Utility - ORG | Expired | SAFETY DEVICE FOR ELECTRICALLY PROGRAMMABLE READ-ONLY MEMORY | 5/21/1987 | 07/052,068 | 3/7/1989 | 4,811,291 | US |
| NMXXS-0009.00/US | Utility - ORG | Expired | NON-VOLATILE SHADOW STORAGE CELL WITH REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY | 8/3/1987 | 07/081,032 | 1/31/1989 | 4,802,124 | US |
| NMXXS-0010.00/US | Utility - ORG | Expired | NON-VOLATILE SHADOW STORAGE CELL WITH IMPROVED LEVEL SHIFTING CIRCUIT AND REDUCED TUNNEL DEVICE COUNT FOR IMPROVED RELIABILITY | 8/3/1987 | 07/081,037 | 11/22/1988 | 4,787,066 | US |
| NMXXS-0011.03/US | Utility - CON | Issued | CONTENT ADDRESSABLE MEMORY | 6/7/1995 | 08/478,429 | 4/16/2002 | 6,373,737 | US |
| NMXXS-0012.00/US | Utility - ORG | Expired | REDUNDANCY FOR SERIAL MEMORY | 1/12/1990 | 07/464,219 | 4/2/1991 | 5,005,158 | US |
| NMXXS-0013.00/RE | Utility - REIS | Expired | METHODS FOR FABRICATING MEMORY CELLS AND LOAD ELEMENTS | 9/29/1994 | 08/316,035 | 9/29/1992 | RE37,769 | US |
| NMXXS-0013.00/US | Utility - ORG | Abandoned | POLYCRYSTALLINE SILICON CONTACT STRUCTURE | 4/30/1990 | 07/516,272 | 9/29/1992 | 5,151,387 | US |
| NMXXS-0013.01/US | Utility - DIV | Expired | POLYCRYSTALLINE SILICON CONTACT STRUCTURE | 2/28/1992 | 07/843,818 | 1/18/1994 | 5,279,887 | US |
| NMXXS-0014.00/US | Utility - CIP | Expired | DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE | 12/21/1989 | 07/454,408 | 6/9/1992 | 5,121,346 | US |
| NMXXS-0014.03/US | Utility - CON | Issued | DIFFERENCE COMPARISON BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE | 4/1/1994 | 08/221,986 | 3/26/1996 | 5,502,655 | US |
| NMXXS-0015.00/US | Utility - ORG | Expired | PIPELINED CIRCUITRY FOR ALLOWING THE COMPARISON OF THE RELATIVE DIFFERENCE BETWEEN TWO ASYNCHRONOUS POINTERS AND A PROGRAMMABLE VALUE | 10/18/1990 | 07/600,201 | 4/27/1993 | 5,206,817 | US |
| NMXXS-0016.00/US | Utility - ORG | Expired | TEST CIRCUIT FOR NON-VOLATILE STORAGE CELL | 9/29/1989 | 07/414,775 | 7/9/1991 | 5,031,152 | US |
| NMXXS-0017.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH A CLOCKED ACCESS CODE FOR TEST MODE ENTRY | 8/17/1990 | 07/569,009 | 12/10/1991 | 5,072,137 | US |
| NMXXS-0018.00/US | Utility - ORG | Expired | DUAL STATE MEMORY STORAGE CELL WITH IMPROVED DATA TRANSFER CIRCUITRY | 2/26/1991 | 07/661,555 | 10/1/1991 | 5,053,996 | US |
| NMXXS-0019.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE | 7/13/1990 | 07/552,567 | 11/23/1993 | 5,265,108 | US |
| NMXXS-0019.01/US | Utility - DIV | Expired | SEMICONDUCTOR MEMORY WITH IMPROVED TEST MODE | 6/2/1993 | 08/071,448 | 5/10/1994 | 5,311,473 | US |
| NMXXS-0020.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY | 8/17/1990 | 07/568,968 | 11/3/1992 | 5,161,159 | US |

PATENT

REEL: 029505 FRAME: 0037

Exhibit A - US Issued Patents

| WIPO No. | Market Type | Market Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|--|------------|------------|------------|------------|---------|
| NMKS-0021.01/US | Utility - CON | Issued | SEMICONDUCTOR MEMORY WITH INHIBITED TEST MODE ENTRY DURING POWER-UP | 11/20/1992 | 07/984,233 | 4/18/1995 | 5,408,435 | US |
| NMKS-0021.02/US | Utility - CON | Issued | SEMICONDUCTOR MEMORY WITH MULTIPLE CLOCKING FOR TEST MODE ENTRY | 4/18/1995 | 08/424,722 | 1/6/1998 | 5,706,232 | US |
| NMKS-0022.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY HAVING LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION | 9/26/1990 | 07/588,601 | 6/2/1992 | 5,119,340 | US |
| NMKS-0023.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY HAVING IMPROVED LATCHED REPEATERS FOR MEMORY ROW LINE SELECTION | 9/26/1990 | 07/588,577 | 7/7/1992 | 5,128,897 | US |
| NMKS-0024.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH SEQUENTIAL CLOCKED ACCESS CODES FOR TEST MODE ENTRY | 8/17/1990 | 07/570,203 | 12/10/1991 | 5,072,138 | US |
| NMKS-0025.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT HAVING MULTIPLE DATA OUTPUTS SHARING A RESISTOR NETWORK | 10/22/1990 | 07/601,288 | 3/24/1992 | 5,099,148 | US |
| NMKS-0026.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS | 9/26/1990 | 07/588,609 | 6/9/1992 | 5,121,358 | US |
| NMKS-0026.02/US | Utility - CON | Issued | SEMICONDUCTOR MEMORY WITH POWER-ON RESET CONTROLLED LATCHED ROW LINE REPEATERS | 1/19/1995 | 08/376,127 | 6/11/1996 | 5,526,318 | US |
| NMKS-0027.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH SEQUENCED LATCHED ROW LINE REPEATERS | 9/26/1990 | 07/588,600 | 6/23/1992 | 5,124,951 | US |
| NMKS-0028.00/US | Utility - ORG | Expired | ADDRESS BUFFER CIRCUIT WITH TRANSITION-BASED LATCHING | 10/22/1990 | 07/601,287 | 6/23/1992 | 5,124,584 | US |
| NMKS-0029.00/US | Utility - ORG | Expired | VEHICLE SEAT ASSEMBLY WITH INTEGRATED CHILD SEAT | 12/14/1990 | 07/827,403 | 11/23/1993 | 5,265,054 | US |
| NMKS-0030.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH COLUMN DECODED BIT LINE EQUILIBRATE | 12/13/1990 | 07/627,050 | 3/22/1994 | 5,297,090 | US |
| NMKS-0031.00/US | Utility - ORG | Expired | SEMICONDUCTOR MEMORY WITH SEPARATE TIME-OUT CONTROL FOR READ AND WRITE OPERATIONS | 12/14/1990 | 07/627,236 | 11/2/1993 | 5,258,952 | US |
| NMKS-0032.01/US | Utility - CON | Expired | SEMICONDUCTOR MEMORY WITH MULTIPLEXED REDUNDANCY | 8/2/1993 | 08/101,347 | 10/11/1994 | 5,355,340 | US |
| NMKS-0033.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT MEMORY DEVICE HAVING FLASH CLEAR | 7/17/1991 | 07/731,803 | 5/10/1994 | 5,311,477 | US |
| NMKS-0034.00/US | Utility - ORG | Expired | CONTROL CIRCUIT FOR RESETTNG A SNOOP VALID BIT IN A DUAL PORT CACHE TAG MEMORY | 5/1/1991 | 07/694,451 | 6/7/1994 | 5,319,768 | US |
| NMKS-0035.00/US | Utility - ORG | Expired | CONTROL CIRCUIT FOR DUAL PORT MEMORY | 4/30/1991 | 07/693,670 | 6/27/1995 | 5,428,632 | US |
| NMKS-0036.00/US | Utility - ORG | Expired | CACHE TAG PARITY DETECT CIRCUIT | 3/29/1991 | 07/677,313 | 8/16/1994 | 5,339,322 | US |
| NMKS-0037.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT MEMORY DEVICE WITH REDUNDANT ROWS | 7/17/1991 | 07/731,487 | 3/22/1994 | 5,297,094 | US |
| NMKS-0038.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT DUAL-PART MEMORY DEVICE HAVING REDUCED CAPACITANCE | 7/17/1991 | 07/731,802 | 2/15/1994 | 5,287,322 | US |
| NMKS-0039.01/US | Utility - CON | Expired | SIGNAL LINE PULSE ENHANCING CIRCUIT FOR INTEGRATED CIRCUITS | 8/20/1993 | 08/109,697 | 6/14/1994 | 5,321,314 | US |
| NMKS-0040.00/US | Utility - ORG | Issued | VIRTUAL GROUND READ ONLY MEMORY CIRCUIT | 11/30/1992 | 07/982,988 | 12/27/1994 | 5,377,153 | US |
| NMKS-0040.02/US | Utility - DIV | Issued | VIRTUAL GROUND READ ONLY MEMORY CIRCUIT | 5/22/1996 | 08/651,233 | 3/31/1998 | 5,734,602 | US |
| NMKS-0040.03/US | Utility - CON | Issued | VIRTUAL GROUND READ ONLY MEMORY CIRCUIT | 8/26/1996 | 08/697,482 | 4/22/1997 | 5,623,438 | US |
| NMKS-0041.00/US | Utility - ORG | Expired | READ/WRITE MEMORY WITH IMPROVED TEST MODE DATA COMPARE | 12/17/1991 | 07/809,393 | 2/8/1994 | 5,285,419 | US |
| NMKS-0042.01/US | Utility - CON | Issued | TRISTABLE DRIVER FOR INTERNAL DATA BUS LINES | 12/31/1996 | 08/777,836 | 5/5/1998 | 5,748,556 | US |
| NMKS-0043.00/US | Utility - ORG | Issued | MULTIPLEXING SENSE AMPLIFIER HAVING LEVEL SHIFTER CIRCUITS | 3/31/1993 | 08/040,916 | 12/27/1994 | 5,377,143 | US |
| NMKS-0043.01/US | Utility - DIV | Issued | MULTIPLEXING SENSE AMPLIFIER | 9/16/1994 | 08/307,332 | 1/9/1996 | 5,483,489 | US |
| NMKS-0044.00/US | Utility - ORG | Issued | MULTIPLEXING SENSE AMPLIFIER | 3/31/1993 | 08/041,321 | 1/23/1996 | 5,487,048 | US |
| NMKS-0045.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT WITH PRECHARGED INTERNAL DATA BUS | 12/17/1991 | 07/809,735 | 3/15/1994 | 5,295,104 | US |
| NMKS-0046.00/US | Utility - ORG | Issued | REDUNDANCY DECODER | 1/31/1992 | 07/830,315 | 11/28/1995 | 5,471,426 | US |
| NMKS-0047.00/US | Utility - ORG | Expired | COLUMN REDUNDANCY ARCHITECTURE FOR A READ/WRITE MEMORY | 1/31/1992 | 07/830,314 | 10/26/1993 | 5,257,229 | US |
| NMKS-0048.00/US | Utility - ORG | Issued | SELECTIVE BULK WRITE OPERATION | 4/17/1992 | 07/854,481 | 5/10/1994 | 5,311,467 | US |
| NMKS-0049.00/US | Utility - ORG | Issued | PARALLELIZED MAGNITUDE COMPARATOR | 4/30/1992 | 07/876,959 | 10/18/1994 | 5,357,235 | US |
| NMKS-0050.00/US | Utility - ORG | Issued | PARALLELIZED MAGNITUDE COMPARATOR FOR COMPARING A BINARY NUMBER TO A FIXED VALUE | 4/30/1992 | 07/876,851 | 6/7/1994 | 5,339,347 | US |
| NMKS-0051.01/US | Utility - CON | Issued | PARALLELIZED BORROW-LOOK AHEAD SUBTRACTOR | 9/16/1993 | 08/122,804 | 1/31/1995 | 5,386,377 | US |
| NMKS-0052.00/US | Utility - ORG | Issued | PARALLELIZED DIFFERENCE FLAG LOGIC | 5/29/1992 | 07/890,919 | 10/18/1994 | 5,357,236 | US |

PATENT

REEL: 029505 FRAME: 0038

Exhibit A - US Issued Patents

| MTI-DefNo | Mater-Type | Mater-Status | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|-----------------|---------------|--------------|---|------------|------------|------------|-----------|---------|
| NMMS-0053.00/US | Utility - ORG | Issued | SERIALIZED DIFFERENCE FLAG CIRCUIT | 6/22/1992 | 07/901,667 | 10/11/1994 | 5,355,113 | US |
| NMMS-0054.00/US | Utility - ORG | Issued | PROGRAMMABLE DIFFERENCE FLAG LOGIC | 7/31/1992 | 07/923,855 | 1/10/1995 | 5,381,126 | US |
| NMMS-0054.01/US | Utility - CON | Issued | FIFO WITH ADAPTABLE FLAG FOR CHANGING SYSTEM SPEED REQUIREMENTS | 9/8/1994 | 08/303,172 | 4/16/1996 | 5,508,679 | US |
| NMMS-0055.00/US | Utility - ORG | Expired | INTEGRATED CIRCUIT WITH SELF-BIASED DIFFERENTIAL DATA LINES | 12/17/1991 | 07/809,733 | 10/26/1993 | 5,257,226 | US |
| NMMS-0056.00/US | Utility - ORG | Issued | PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS | 7/28/1994 | 08/282,408 | 7/9/1996 | 5,534,448 | US |
| NMMS-0056.01/US | Utility - DIV | Issued | PROCESS FOR REALIZING P-CHANNEL MOS TRANSISTORS HAVING A LOW THRESHOLD VOLTAGE IN SEMICONDUCTOR INTEGRATED CIRCUITS FOR ANALOG APPLICATIONS | 6/7/1995 | 08/486,747 | 12/31/1996 | 5,589,701 | US |
| NMMS-0057.02/US | Utility - CON | Issued | INPUT BUFFER CIRCUIT IMMUNE TO COMMON MODE POWER SUPPLY FLUCTUATIONS | 6/7/1995 | 08/477,283 | 11/3/1998 | 5,831,457 | US |
| NMMS-0058.00/US | Utility - ORG | Issued | STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE | 11/13/1992 | 07/975,628 | 10/11/1994 | 5,355,344 | US |
| NMMS-0058.01/US | Utility - CON | Issued | STRUCTURE FOR USING A PORTION OF AN INTEGRATED CIRCUIT DIE | 6/21/1994 | 08/263,048 | 6/11/1996 | 5,526,317 | US |
| NMMS-0059.01/US | Utility - CON | Issued | INTEGRATED CIRCUIT OUTPUT DRIVER | 12/30/1994 | 08/367,681 | 7/17/2001 | 6,262,617 | US |
| NMMS-0060.00/US | Utility - ORG | Issued | OUTPUT DRIVER CIRCUIT WITH BODY BIAS CONTROL FOR MULTIPLE POWER SUPPLY OPERATION | 1/3/1994 | 08/176,960 | 6/6/1995 | 5,422,594 | US |
| NMMS-0061.01/US | Utility - CON | Issued | MULTIPLE CLOCKED DYNAMIC SENSE AMPLIFIER | 9/15/1994 | 08/306,527 | 1/16/1996 | 5,485,430 | US |
| NMMS-0062.00/US | Utility - ORG | Issued | DUAL DYNAMIC SENSE AMPLIFIERS FOR A MEMORY ARRAY | 12/22/1992 | 07/995,581 | 10/3/1995 | 5,455,802 | US |
| NMMS-0063.01/US | Utility - CON | Issued | LEADFRAME FOR INTEGRATED CIRCUITS | 1/13/1994 | 08/180,692 | 2/14/1995 | 5,389,577 | US |
| NMMS-0064.00/US | Utility - ORG | Issued | MULTIPLE LEVEL PARALLEL MAGNITUDE COMPARATOR | 2/19/1993 | 08/020,045 | 3/21/1995 | 5,400,007 | US |
| NMMS-0065.00/US | Utility - ORG | Issued | STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS | 9/30/1992 | 07/954,276 | 6/13/1995 | 5,424,988 | US |
| NMMS-0065.01/US | Utility - CON | Issued | STRESS TEST FOR MEMORY ARRAYS IN INTEGRATED CIRCUITS | 6/2/1995 | 08/460,409 | 7/1/1997 | 5,644,542 | US |
| NMMS-0066.00/US | Utility - ORG | Issued | SEW RATE LIMITED OUTPUT BUFFER WITH BYPASS CIRCUITRY | 8/31/1992 | 07/938,399 | 4/5/1994 | 5,300,828 | US |
| NMMS-0067.00/US | Utility - ORG | Issued | TEMPERATURE-COMPENSATED VOLTAGE LEVEL SENSE CIRCUIT | 4/29/1993 | 08/055,080 | 11/15/1994 | 5,365,129 | US |
| NMMS-0068.00/US | Utility - ORG | Issued | ADDRESS BUFFER | 4/30/1993 | 08/056,078 | 8/16/1994 | 5,389,277 | US |
| NMMS-0069.00/US | Utility - ORG | Issued | METHOD FOR STRESS TESTING DECODERS AND PERIPHERY CIRCUITS | 4/30/1993 | 08/056,376 | 8/23/1994 | 5,341,336 | US |
| NMMS-0070.00/US | Utility - ORG | Issued | INPUT BUFFER WITH HYSTERESIS CHARACTERISTICS | 12/21/1992 | 07/995,666 | 9/20/1994 | 5,349,246 | US |
| NMMS-0071.00/US | Utility - ORG | Issued | OUTPUT DRIVER CIRCUIT | 7/31/1992 | 07/923,135 | 7/19/1994 | 5,331,228 | US |
| NMMS-0072.00/US | Utility - ORG | Issued | REDUNDANCY ELEMENT CHECK IN IC MEMORY WITHOUT PROGRAMMING | 7/30/1993 | 08/099,606 | 4/4/1995 | 5,404,331 | US |
| NMMS-0073.00/US | Utility - ORG | Issued | TEMPERATURE-STABLE CURRENT SOURCE | 5/31/1995 | 08/454,926 | 7/1/1997 | 5,644,216 | US |
| NMMS-0074.01/US | Utility - DIV | Issued | PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE | 6/6/1995 | 08/473,552 | 5/6/1997 | 5,627,403 | US |
| NMMS-0074.02/US | Utility - CON | Issued | PROCESS FOR IMPROVING THE INTERFACE UNION AMONG DIELECTRIC MATERIALS IN AN INTEGRATED CIRCUIT MANUFACTURE | 11/18/1996 | 08/751,244 | 8/18/1998 | 5,795,821 | US |
| NMMS-0075.00/US | Utility - ORG | Issued | VOLTAGE GENERATOR CIRCUIT PROVIDING POTENTIALS OF OPPOSITE POLARITY | 9/26/1994 | 08/311,941 | 8/13/1996 | 5,546,044 | US |
| NMMS-0076.00/US | Utility - ORG | Abandoned | PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES | 9/7/1994 | 08/301,792 | 1/23/1996 | 5,486,486 | US |
| NMMS-0076.01/US | Utility - DIV | Issued | PROCESS FOR THE MANUFACTURE OF AN INTEGRATED VOLTAGE LIMITER AND STABILIZER IN FLASH EEPROM MEMORY DEVICES | 6/7/1995 | 08/477,302 | 2/4/1997 | 5,600,590 | US |
| NMMS-0077.00/US | Utility - ORG | Issued | MONOLITHICALLY INTEGRATED STORAGE DEVICE | 11/30/1994 | 08/347,653 | 7/9/1996 | 5,535,157 | US |
| NMMS-0078.00/US | Utility - ORG | Issued | CIRCUIT FOR COVERING INITIAL CONDITIONS WHEN STARTING-UP AN INTEGRATED CIRCUIT DEVICE | 1/30/1995 | 08/380,309 | 3/18/1997 | 5,612,641 | US |
| NMMS-0079.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE | 11/23/1994 | 08/344,232 | 6/18/1996 | 5,528,536 | US |
| NMMS-0079.01/US | Utility - DIV | Issued | METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE | 4/26/1995 | 08/639,931 | 8/19/1997 | 5,659,501 | US |

PATENT

REEL: 029505 FRAME: 0039

Exhibit A - US Issued Patents

| WIPO Class | Market Type | Market Status | Title | File Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|--|------------|------------|------------|------------|---------|
| NMXX-0079.02/US | Utility - CON | Issued | METHOD AND DEVICE FOR SUPPLYING NEGATIVE PROGRAMMING VOLTAGES TO NON-VOLATILE MEMORY CELLS IN A NON-VOLATILE MEMORY DEVICE | 6/9/1997 | 08/871,226 | 10/6/1998 | 5,818,760 | US |
| NMXX-0080.00/US | Utility - ORG | Issued | REDUNDANCY CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE | 12/6/1994 | 08/349,783 | 10/15/1996 | 5,566,114 | US |
| NMXX-0081.01/US | Utility - CON | Issued | INTEGRATED CIRCUIT FOR THE PROGRAMMING OF A MEMORY CELL IN A NON-VOLATILE MEMORY REGISTER | 4/18/1996 | 08/635,455 | 7/1/1997 | 5,644,529 | US |
| NMXX-0082.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A ROW REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE AND ROW REDUNDANCY INTEGRATED CIRCUITRY | 2/16/1995 | 08/391,999 | 8/19/1997 | 5,659,509 | US |
| NMXX-0083.00/US | Utility - ORG | Issued | INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE | 12/7/1994 | 08/350,961 | 2/20/1996 | 5,493,531 | US |
| NMXX-0083.01/US | Utility - CIP | Issued | INTEGRATED CIRCUITRY FOR CHECKING THE UTILIZATION RATE OF REDUNDANCY MEMORY ELEMENTS IN A SEMICONDUCTOR MEMORY DEVICE | 2/16/1996 | 08/602,237 | 1/13/1998 | 5,708,601 | US |
| NMXX-0084.00/US | Utility - ORG | Issued | REDUNDANCY CIRCUITRY LAYOUT FOR A SEMICONDUCTOR MEMORY DEVICE | 3/29/1995 | 08/412,550 | 9/24/1996 | 5,559,743 | US |
| NMXX-0085.00/US | Utility - ORG | Issued | CURRENT SOURCE HAVING VOLTAGE STABILIZING ELEMENT | 1/20/1995 | 08/377,524 | 8/13/1996 | 5,546,054 | US |
| NMXX-0086.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TIMING THE LOADING OF NONVOLATILE-MEMORY OUTPUT DATA | 2/23/1995 | 08/391,160 | 5/7/1996 | 5,515,332 | US |
| NMXX-0087.00/US | Utility - ORG | Issued | INTERNAL TIMING METHOD AND CIRCUIT FOR PROGRAMMABLE MEMORIES | 2/23/1995 | 08/391,159 | 9/2/1997 | 5,663,921 | US |
| NMXX-0088.01/US | Utility - CON | Issued | LOAD SIGNAL GENERATING METHOD AND CIRCUIT FOR NONVOLATILE MEMORIES | 2/25/1997 | 08/803,915 | 2/10/1998 | 5,717,642 | US |
| NMXX-0089.01/US | Utility - CON | Issued | COUNT UNIT FOR NONVOLATILE MEMORIES | 8/20/1996 | 08/700,126 | 11/11/1997 | 5,687,135 | US |
| NMXX-0090.00/US | Utility - ORG | Issued | END-OF-COUNT DETECTING DEVICE FOR NONVOLATILE MEMORIES | 12/28/1994 | 08/365,510 | 1/14/1997 | 5,596,703 | US |
| NMXX-0091.01/US | Utility - CON | Issued | VOLTAGE BOOSTER WITH AN ACCELERATION CIRCUIT | 5/14/1997 | 08/855,922 | 6/16/1998 | 5,768,115 | US |
| NMXX-0092.00/US | Utility - ORG | Issued | BIAS CIRCUIT FOR A MEMORY LINE DECODER DRIVER OF NONVOLATILE MEMORIES | 12/21/1994 | 08/348,461 | 3/12/1996 | 5,499,217 | US |
| NMXX-0093.00/US | Utility - ORG | Issued | READING CIRCUIT FOR AN INTEGRATED SEMICONDUCTOR MEMORY DEVICE | 3/22/1995 | 08/408,589 | 5/6/1997 | 5,627,790 | US |
| NMXX-0094.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR TESTING A NETWORK WITH A PROGRAMMABLE LOGIC MATRIX | 11/28/1994 | 08/345,530 | 2/10/1998 | 5,717,698 | US |
| NMXX-0095.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING AND TESTING A NONVOLATILE MEMORY | 1/31/1995 | 08/381,530 | 2/4/1997 | 5,600,600 | US |
| NMXX-0096.00/US | Utility - ORG | Issued | THRESHOLD VOLTAGE MEASURING DEVICE FOR MEMORY CELLS | 3/31/1995 | 08/412,326 | 2/4/1997 | 5,600,594 | US |
| NMXX-0097.00/US | Utility - ORG | Issued | CIRCUIT FOR IDENTIFYING A MEMORY CELL HAVING ERRONEOUS DATA STORED THEREIN | 8/30/1995 | 08/521,304 | 11/11/1997 | 5,687,124 | US |
| NMXX-0098.00/US | Utility - ORG | Issued | DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE | 12/29/1994 | 08/366,211 | 12/10/1996 | 5,583,820 | US |
| NMXX-0098.01/US | Utility - DIV | Issued | DEVICE FOR DETECTING A REDUCTION IN A SUPPLY VOLTAGE | 9/9/1996 | 08/711,132 | 5/5/1998 | 5,748,548 | US |
| NMXX-0099.00/US | Utility - ORG | Issued | STABLE REFERENCE VOLTAGE GENERATOR CIRCUIT | 11/30/1994 | 08/347,788 | 5/21/2002 | 6,392,469 | US |
| NMXX-0100.00/US | Utility - ORG | Issued | REGULATION CIRCUIT AND METHOD FOR THE ERASING PHASE OF NON-VOLATILE MEMORY CELLS | 2/23/1995 | 08/395,361 | 4/1/1997 | 5,617,356 | US |
| NMXX-0101.00/US | Utility - ORG | Issued | CIRCUIT DEVICE AND CORRESPONDING METHOD FOR RESETTNG NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY DEVICES | 12/29/1994 | 08/366,212 | 12/17/1996 | 5,586,077 | US |
| NMXX-0102.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR PROGRAMMING NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY CELLS | 12/29/1994 | 08/366,259 | 5/21/1996 | 5,519,656 | US |
| NMXX-0103.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES | 1/3/1995 | 08/368,211 | 8/19/1997 | 5,659,516 | US |
| NMXX-0103.01/US | Utility - DIV | Issued | VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR ELECTRICALLY PROGRAMMABLE MEMORY DEVICES | 4/1/1997 | 08/831,046 | 5/18/1999 | 5,905,677 | US |
| NMXX-0104.00/US | Utility - ORG | Issued | INTEGRATED PROGRAMMING CIRCUITRY FOR AN ELECTRICALLY PROGRAMMABLE SEMICONDUCTOR MEMORY DEVICE WITH REDUNDANCY | 12/28/1994 | 08/365,154 | 8/20/1996 | 5,548,554 | US |
| NMXX-0105.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR SUPPRESSING DATA LOADING NOISE IN NONVOLATILE MEMORIES | 2/21/1995 | 08/391,147 | 7/30/1996 | 5,541,884 | US |
| NMXX-0106.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TIMING THE READING OF NONVOLATILE MEMORIES | 2/21/1995 | 08/391,920 | 7/2/1996 | 5,532,972 | US |

PATENT

REEL: 029505 FRAME: 0040

Exhibit A - US Issued Patents

| WI#-Device | Material Type | Material Status | Title | Filed Date | Serial No | Issued Date | Patent No | Country |
|-----------------|----------------|-----------------|---|------------|------------|-------------|-----------|---------|
| NMMS-0107.00/US | Utility - ORG | Issued | MEMORY ARRAY CELL READING CIRCUIT WITH EXTRA CURRENT BRANCH | 4/17/1995 | 08/422,813 | 10/8/1996 | 5,565,826 | US |
| NMMS-0108.00/US | Utility - ORG | Issued | FLASH-EEPROM MEMORY ARRAY AND METHOD FOR BIASING THE SAME | 3/28/1995 | 08/412,162 | 6/10/1997 | 5,638,327 | US |
| NMMS-0109.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING REDUNDANCY REGISTERS IN A COLUMN REDUNDANCY INTEGRATED CIRCUITRY FOR A SEMICONDUCTOR MEMORY DEVICE, AND COLUMN REDUNDANCY INTEGRATED CIRCUITRY | 2/16/1995 | 08/389,599 | 2/11/1997 | 5,602,786 | US |
| NMMS-0110.00/US | Utility - ORG | Issued | REFERENCE SIGNAL GENERATING METHOD AND CIRCUIT FOR DIFFERENTIAL EVALUATION OF THE CONTENT OF NONVOLATILE MEMORY CELLS | 3/28/1995 | 08/411,904 | 7/30/1996 | 5,541,880 | US |
| NMMS-0111.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES | 1/3/1995 | 08/367,538 | 11/19/1996 | 5,576,990 | US |
| NMMS-0112.00/RE | Utility - REIS | Issued | DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR | 7/12/2000 | 09/616,821 | 7/14/1998 | RE39,918 | US |
| NMMS-0112.02/US | Utility - CON | Abandoned | DIRECT CURRENT SUM BANDGAP VOLTAGE COMPARATOR | 9/18/1997 | 08/932,930 | 7/14/1998 | 5,781,043 | US |
| NMMS-0113.00/US | Utility - ORG | Issued | STRUCTURE TO RECOVER A PORTION OF A PARTIALLY FUNCTIONAL EMBEDDED MEMORY | 4/22/1993 | 08/051,184 | 11/28/1995 | 5,471,431 | US |
| NMMS-0114.00/RE | Utility - REIS | Issued | STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS | 11/7/1997 | 08/966,042 | 11/7/1995 | RE36,319 | US |
| NMMS-0114.00/US | Utility - ORG | Abandoned | STRUCTURE FOR DESELECTIVE BROKEN SELECT LINES IN MEMORY ARRAYS | 5/28/1993 | 08/069,025 | 11/7/1995 | 5,465,233 | US |
| NMMS-0115.00/US | Utility - ORG | Issued | LATCH CONTROLLED OUTPUT DRIVER | 6/30/1993 | 08/085,760 | 9/20/1994 | 5,349,243 | US |
| NMMS-0116.00/US | Utility - ORG | Issued | FUSE CIRCUITRY TO CONTROL THE PROPAGATION DELAY OF AN IC | 6/30/1993 | 08/085,580 | 6/27/1995 | 5,428,311 | US |
| NMMS-0117.01/US | Utility - CON | Issued | METHOD AND APPARATUS FOR PARALLEL TESTING OF MEMORY | 3/27/1995 | 08/410,383 | 8/13/1996 | 5,546,537 | US |
| NMMS-0118.01/US | Utility - CON | Issued | CLOCK GENERATION CIRCUIT HAVING COMPENSATION FOR SEMICONDUCTOR MANUFACTURING PROCESS VARIATIONS | 3/30/1995 | 08/413,789 | 5/6/1997 | 5,627,793 | US |
| NMMS-0119.00/US | Utility - ORG | Issued | CLOCK GENERATOR CIRCUIT WITH LOW CURRENT FREQUENCY DIVIDER | 1/22/1994 | 08/188,153 | 11/21/1995 | 5,469,116 | US |
| NMMS-0120.00/US | Utility - CIP | Issued | DISABLING SENSE AMPLIFIER | 7/30/1993 | 08/099,947 | 12/27/1994 | 5,373,150 | US |
| NMMS-0120.01/US | Utility - DIV | Issued | DISABLING SENSE AMPLIFIER | 8/31/1994 | 08/298,766 | 12/5/1995 | 5,407,567 | US |
| NMMS-0121.00/US | Utility - ORG | Issued | PRECHARGE DEVICE FOR AN INTEGRATED CIRCUIT INTERNAL BUS | 8/31/1993 | 08/114,749 | 3/28/1995 | 5,402,379 | US |
| NMMS-0122.00/US | Utility - ORG | Issued | APPARATUS FOR TESTING SIGNAL TIMING AND PROGRAMMING DELAY | 1/31/1994 | 08/189,589 | 11/26/1996 | 5,579,326 | US |
| NMMS-0122.01/US | Utility - DIV | Lapsed | DISTRIBUTED NOR TAG MATCH APPARATUS | 5/9/1996 | 08/647,222 | 11/24/1998 | 5,841,789 | US |
| NMMS-0123.00/US | Utility - ORG | Issued | APPARATUS FOR TESTING SIGNAL TIMING AND PROGRAMMING DELAY | 8/31/1993 | 08/114,747 | 11/5/1996 | 5,572,456 | US |
| NMMS-0124.02/US | Utility - CON | Issued | VARIABLE IMPEDANCE DELAY ELEMENTS | 2/18/1997 | 08/801,452 | 1/11/2000 | 6,014,050 | US |
| NMMS-0124.03/US | Utility - DIV | Issued | VARIABLE IMPEDANCE DELAY ELEMENTS | 8/25/1998 | 09/139,225 | 6/28/2001 | 6,252,447 | US |
| NMMS-0125.00/US | Utility - ORG | Issued | TESTING CIRCUITRY OF INTERNAL PERIPHERAL BLOCKS IN A SEMICONDUCTOR MEMORY DEVICE AND METHOD OF TESTING THE SAME | 1/27/1994 | 08/188,158 | 8/8/1995 | 5,440,516 | US |
| NMMS-0126.00/US | Utility - ORG | Issued | STRESS TEST MODE | 12/22/1993 | 08/172,854 | 11/10/1998 | 5,835,427 | US |
| NMMS-0127.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR ACQUIRING REDUNDANCY INFORMATION FROM A PACKAGED MEMORY CHIP | 12/22/1993 | 08/172,848 | 8/8/2000 | 6,101,618 | US |
| NMMS-0128.01/US | Utility - CON | Issued | REDUNDANT LINE DECODER MASTER ENABLE | 6/19/1995 | 08/492,219 | 10/22/1996 | 5,568,061 | US |
| NMMS-0129.01/US | Utility - CON | Issued | STRUCTURE TO UTILIZE A PARTIALLY FUNCTIONAL CACHE MEMORY BY INVALIDATION OF FAULTY CACHE MEMORY LOCATIONS | 9/20/1996 | 08/717,139 | 1/13/1998 | 5,708,789 | US |
| NMMS-0130.00/US | Utility - ORG | Issued | LATCH CONTROLLED OUTPUT DRIVER | 9/30/1993 | 08/129,257 | 3/7/1995 | 5,396,108 | US |
| NMMS-0131.00/US | Utility - ORG | Issued | EDGE TRANSITION DETECTION DISABLE CIRCUIT TO ALTER MEMORY DEVICE OPERATING CHARACTERISTICS | 9/30/1993 | 08/129,763 | 5/23/1995 | 5,448,756 | US |
| NMMS-0132.00/US | Utility - ORG | Issued | DATA COMPARING SENSE AMPLIFIER | 12/22/1993 | 08/172,853 | 10/22/1996 | 5,568,073 | US |
| NMMS-0133.00/US | Utility - ORG | Issued | STATIC TEST MODE NOISE FILTER | 11/30/1993 | 08/160,608 | 8/8/1995 | 5,460,178 | US |
| NMMS-0134.00/US | Utility - ORG | Issued | FUSE CIRCUIT WITH FEEDBACK DISCONNECT | 12/28/1993 | 08/174,139 | 2/13/1996 | 5,491,444 | US |
| NMMS-0135.00/US | Utility - ORG | Issued | STATIC MEMORY LONG WRITE TEST | 12/22/1993 | 08/173,197 | 11/19/1996 | 5,577,051 | US |
| NMMS-0136.00/US | Utility - CIP | Issued | COMPENSATING DELAY ELEMENT FOR CLOCK GENERATION IN A MEMORY DEVICE | 12/20/1993 | 08/170,612 | 6/13/1995 | 5,424,985 | US |
| NMMS-0137.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY WITH EDGE TRANSITION DETECTION PULSE DISABLE | 2/28/1994 | 08/202,830 | 2/20/1996 | 5,493,537 | US |
| NMMS-0138.00/US | Utility - ORG | Issued | ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY WITH WRITE CHECKING | 11/17/1994 | 08/340,940 | 4/21/1998 | 5,742,548 | US |

PATENT

REEL: 029505 FRAME: 0041

Exhibit A - US Issued Patents

| WIPO No. | Matr/Type | Matr/Status | Title | Filed Date | Serial No. | Issued Date | Patent No. | Country |
|------------------|---------------|-------------|--|------------|------------|-------------|------------|---------|
| NMXXS-0139.00/US | Utility - ORG | Issued | RESISTOR-CAPACITOR-TRANSISTOR TYPE INTEGRATED CIRCUIT, METHOD FOR THE MANUFACTURE OF SUCH A CIRCUIT AND APPLICATION TO AN OSCILLATOR | 5/19/1994 | 08/246,070 | 7/4/1995 | 5,430,319 | US |
| NMXXS-0139.01/US | Utility - CON | Issued | RELAXATION OSCILLATOR USING INTEGRATED RTC STRUCTURE | 3/8/1995 | 08/399,900 | 8/26/1997 | 5,661,324 | US |
| NMXXS-0140.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT CONTAINING A PROTECTED MEMORY AND SECURED SYSTEM USING SAID INTEGRATED CIRCUIT | 10/27/1994 | 08/329,975 | 1/14/1997 | 5,594,793 | US |
| NMXXS-0141.00/US | Utility - ORG | Issued | LINE DECODER CIRCUIT FOR A MEMORY WORKING AT LOW SUPPLY VOLTAGES | 12/21/1994 | 08/361,313 | 9/10/1996 | 5,555,216 | US |
| NMXXS-0142.00/US | Utility - ORG | Issued | MEMORY IN INTEGRATED CIRCUIT FORM WITH IMPROVED READING TIME | 12/21/1994 | 08/361,996 | 7/16/1996 | 5,537,349 | US |
| NMXXS-0143.00/US | Utility - ORG | Issued | METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES | 1/27/1995 | 08/379,337 | 3/23/1999 | 5,886,386 | US |
| NMXXS-0143.01/US | Utility - DIV | Issued | METHOD FOR MAKING A BIPOLAR TRANSISTOR FOR THE PROTECTION OF AN INTEGRATED CIRCUIT AGAINST ELECTROSTATIC DISCHARGES | 12/24/1998 | 09/220,635 | 7/24/2001 | 6,265,277 | US |
| NMXXS-0144.02/US | Utility - CON | Issued | BIAS CIRCUIT FOR TRANSISTOR OF A STORAGE CELL | 12/16/1996 | 08/767,521 | 5/4/1999 | 5,900,756 | US |
| NMXXS-0145.00/US | Utility - ORG | Issued | MEMORY REDUNDANCY CIRCUIT | 2/27/1995 | 08/393,464 | 11/26/1996 | 5,579,265 | US |
| NMXXS-0146.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT | 3/10/1995 | 08/402,519 | 3/11/1997 | 5,610,860 | US |
| NMXXS-0146.01/US | Utility - DIV | Issued | INTEGRATED CIRCUIT MEMORY WITH COLUMN VOLTAGE HOLDING CIRCUIT | 3/4/1997 | 08/811,358 | 3/17/1998 | 5,729,162 | US |
| NMXXS-0147.00/US | Utility - ORG | Issued | NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR IN PREDEFINED INITIAL STATE FOR MEMORY REDUNDANCY CIRCUIT | 1/30/1995 | 08/380,737 | 2/25/1997 | 5,606,523 | US |
| NMXXS-0148.00/US | Utility - ORG | Issued | NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT | 1/30/1995 | 08/380,738 | 1/7/1997 | 5,592,417 | US |
| NMXXS-0148.01/US | Utility - DIV | Issued | NON-VOLATILE-PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT | 11/21/1996 | 08/752,814 | 10/14/1997 | 5,677,870 | US |
| NMXXS-0148.02/US | Utility - DIV | Issued | NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR, PROGRAMMABLE BY THE SOURCE, FOR MEMORY REDUNDANCY CIRCUIT | 11/21/1996 | 08/754,432 | 2/24/1998 | 5,721,706 | US |
| NMXXS-0149.00/US | Utility - ORG | Issued | NON-VOLATILE PROGRAMMABLE BISTABLE MULTIVIBRATOR WITH REDUCED PARASITICS IN READING MODE NOTABLY FOR MEMORY REDUNDANCY CIRCUIT | 1/31/1995 | 08/381,529 | 10/1/1996 | 5,561,621 | US |
| NMXXS-0150.00/US | Utility - ORG | Issued | SWITCHING REGULATOR WITH DYSYMMETRICAL DIFFERENTIAL INPUT STAGE | 4/19/1995 | 08/423,398 | 3/18/1997 | 5,612,611 | US |
| NMXXS-0151.00/US | Utility - ORG | Issued | VOLTAGE BOOSTER CIRCUIT | 4/19/1995 | 08/423,396 | 6/3/1997 | 5,636,115 | US |
| NMXXS-0152.00/US | Utility - ORG | Abandoned | METHOD FOR THE ERASURE OF A MEMORY, AND CIRCUITS FOR THE IMPLEMENTATION THEREOF | 4/12/1995 | 08/421,671 | 4/8/1997 | 5,619,451 | US |
| NMXXS-0153.00/US | Utility - ORG | Issued | CIRCUIT FOR THE SELECTION OF REDUNDANT MEMORY ELEMENTS AND FLASH EEPROM MEMORY COMPRISING SAID CIRCUIT | 2/22/1995 | 08/394,314 | 8/18/1998 | 5,796,633 | US |
| NMXXS-0154.00/US | Utility - ORG | Issued | ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY INCORPORATING TEST FUNCTIONS | 4/7/1995 | 08/418,636 | 7/1/1997 | 5,644,530 | US |
| NMXXS-0155.00/US | Utility - ORG | Issued | PROGRAMMABLE INTEGRATED CIRCUIT MEMORY COMPRISING EMULATION MEANS | 6/7/1995 | 08/484,873 | 7/22/1997 | 5,651,128 | US |
| NMXXS-0156.00/US | Utility - ORG | Issued | MATRIX DEVICE WITH REDUNDANCY FUSES FOR INTEGRATED MEMORY | 3/21/1995 | 08/408,016 | 1/14/1997 | 5,594,693 | US |
| NMXXS-0157.00/US | Utility - ORG | Issued | METHOD FOR TESTING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY DEVICE | 6/7/1995 | 08/479,081 | 12/31/1996 | 5,590,075 | US |
| NMXXS-0158.01/US | Utility - CON | Issued | PROGRAMMABLE MEMORY ELEMENT | 2/4/1997 | 08/794,965 | 12/9/1997 | 5,696,716 | US |
| NMXXS-0159.00/US | Utility - ORG | Issued | SENSE AMPLIFIER WITH HYSTERESIS | 5/2/1995 | 08/432,838 | 2/3/1998 | 5,715,204 | US |
| NMXXS-0160.01/US | Utility - DIV | Issued | HIGHLY-PLANAR INTERLAYER DIELECTRIC THIN FILMS IN INTEGRATED CIRCUITS | 6/6/1995 | 08/468,282 | 1/28/1997 | 5,598,028 | US |
| NMXXS-0161.00/US | Utility - ORG | Issued | PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS | 12/22/1995 | 08/577,125 | 11/28/2000 | 6,153,537 | US |
| NMXXS-0161.01/US | Utility - DIV | Issued | PROCESS FOR THE PRODUCTION OF A SEMICONDUCTOR DEVICE HAVING BETTER INTERFACE ADHESION BETWEEN DIELECTRIC LAYERS | 12/14/1998 | 09/211,065 | 3/11/2003 | 6,531,714 | US |
| NMXXS-0162.00/US | Utility - ORG | Issued | FAILURE TOLERANT MEMORY DEVICE, IN PARTICULAR OF THE FLASH EEPROM TYPE | 5/31/1995 | 08/454,650 | 10/28/1997 | 5,682,349 | US |

PATENT

REEL: 029505 FRAME: 0042

Exhibit A - US Issued Patents

| Patent No. | Patent Title | Issue Date | Patent No. | Country |
|-----------------|---------------|------------|---|---------|
| NMMS-0163.00/US | UTILITY - ORG | Issued | NONVOLATILE MEMORY CELL AND A METHOD FOR FORMING THE SAME | US |
| NMMS-0163.01/US | Utility - DIV | Issued | METHOD OF MAKING ASYMMETRIC NONVOLATILE MEMORY CELL | US |
| NMMS-0164.00/US | Utility - ORG | Issued | MEMORY DEVICE HAVING ERROR DETECTION AND CORRECTION FUNCTION, AND METHODS FOR READING, WRITING AND ERASING THE MEMORY DEVICE | US |
| NMMS-0165.00/US | Utility - ORG | Issued | SENSE AMPLIFIER HAVING CAPACITIVELY COUPLED INPUT FOR OFFSET COMPENSATION | US |
| NMMS-0165.01/US | Utility - CON | Issued | SENSE AMPLIFIER CIRCUIT FOR SEMICONDUCTOR MEMORY DEVICES | US |
| NMMS-0166.01/US | Utility - CON | Issued | MONOLITHICALLY INTEGRATED GENERATOR OF A PLURALITY OF VOLTAGE VALUES | US |
| NMMS-0167.00/US | Utility - ORG | Issued | HIGH-VOLTAGE N-CHANNEL MOS TRANSISTOR AND ASSOCIATED MANUFACTURING PROCESS | US |
| NMMS-0168.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT WITH IMPROVED IMMUNITY TO LARGE METALLIZATION DEFECTS | US |
| NMMS-0169.00/US | Utility - ORG | Issued | READING CIRCUIT FOR MEMORY CELLS | US |
| NMMS-0170.00/US | Utility - ORG | Issued | SYNCHRONIZATION DEVICE FOR OUTPUT STAGES, PARTICULARLY FOR ELECTRONIC MEMORIES | US |
| NMMS-0171.00/US | Utility - ORG | Issued | PROGRAMMABLE MEMORY WITH SINGLE BIT ENCODING | US |
| NMMS-0172.00/US | Utility - ORG | Issued | DECODER WITH REDUCED ARCHITECTURE | US |
| NMMS-0173.00/US | Utility - ORG | Issued | OUTPUT STAGE FOR INTEGRATED CIRCUITS, PARTICULARLY FOR ELECTRONIC MEMORIES | US |
| NMMS-0174.00/US | Utility - ORG | Issued | PROGRAMMABLE MULTIBIT REGISTER FOR COINCIDENCE AND JUMP OPERATIONS AND COINCIDENCE FUSE CELL | US |
| NMMS-0176.00/US | Utility - ORG | Issued | EEPROM MEMORY WITH CONTACTLESS MEMORY CELLS | US |
| NMMS-0177.00/US | Utility - ORG | Issued | BYTE ERASABLE EEPROM FULLY COMPATIBLE WITH A SINGLE POWER SUPPLY FLASH-EPROM PROCESS | US |
| NMMS-0178.00/US | Utility - ORG | Issued | POWER-ON RESET CIRCUIT | US |
| NMMS-0179.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER | US |
| NMMS-0179.01/US | Utility - CON | Issued | NONVOLATILE MEMORY DEVICE HAVING SECTORS OF SELECTABLE SIZE AND NUMBER | US |
| NMMS-0180.00/US | Utility - ORG | Issued | PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC | US |
| NMMS-0180.01/US | Utility - CON | Issued | PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS AND CORRESPONDING IC | US |
| NMMS-0181.00/US | Utility - ORG | Issued | PROCESS FOR FORMING AN INTEGRATED CIRCUIT COMPRISING NON-VOLATILE MEMORY CELLS AND SIDE TRANSISTORS OF AT LEAST TWO DIFFERENT TYPES, AND CORRESPONDING IC | US |
| NMMS-0182.00/US | Utility - ORG | Issued | METHOD OF MANUFACTURING A MOS INTEGRATED CIRCUIT HAVING COMPONENTS WITH DIFFERENT DIELECTRICS | US |
| NMMS-0183.00/US | Utility - ORG | Issued | METHOD FOR IMPROVING THE PROFILE OF THE INTERMEDIATE DIELECTRIC, PARTICULARLY FOR NON-VOLATILE MEMORIES | US |
| NMMS-0183.01/US | Utility - DIV | Issued | METHOD FOR IMPROVING THE INTERMEDIATE DIELECTRIC PROFILE, PARTICULARLY FOR NON-VOLATILE MEMORIES | US |
| NMMS-0184.00/US | Utility - ORG | Issued | CHARGE PUMP VOLTAGE MULTIPLIER CIRCUIT | US |
| NMMS-0185.00/US | Utility - ORG | Issued | VOLTAGE GENERATOR-BOOSTER FOR SUPPLYING A PULSATING VOLTAGE HAVING APPROXIMATELY CONSTANT VOLTAGE LEVELS | US |
| NMMS-0186.00/US | Utility - ORG | Issued | CURRENT DETECTING CIRCUIT | US |
| NMMS-0187.00/US | Utility - ORG | Issued | HIERARCHIC MEMORY DEVICE HAVING AUXILIARY LINES CONNECTED TO WORD LINES | US |

PATENT

REEL: 029505 FRAME: 0043

Exhibit A - US Issued Patents

| WIPO-No. | Matr-Type | Matr-Status | Title | Filed | Ser.No. | Issue Date | Patent No. | Country |
|-----------------|---------------|-------------|--|------------|------------|------------|------------|---------|
| NMKS-0188.04/US | Utility - CON | Issued | METHOD AND STRUCTURE FOR RECOVERING SMALLER DENSITY MEMORIES FROM LARGER DENSITY MEMORIES | 5/15/1997 | 08/940,045 | 5/18/1999 | 5,905,683 | US |
| NMKS-0189.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT WITH FUSE CIRCUITRY SIMULATING FUSE BLOWING | 3/31/1994 | 08/220,976 | 5/14/1996 | 5,517,455 | US |
| NMKS-0190.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT WITH CENTRALIZED CONTROL OF EDGE TRANSITION DETECTION PULSE GENERATION | 3/31/1994 | 08/220,834 | 11/28/1995 | 5,471,157 | US |
| NMKS-0191.00/US | Utility - ORG | Issued | STRUCTURE CAPABLE OF SIMULTANEOUSLY TESTING REDUNDANT AND NON-REDUNDANT MEMORY ELEMENTS DURING STRESS TESTING OF AN INTEGRATED CIRCUIT MEMORY DEVICE | 4/29/1994 | 08/235,161 | 6/25/1996 | 5,530,674 | US |
| NMKS-0192.00/US | Utility - ORG | Issued | LONG WRITE TEST | 6/29/1994 | 08/267,667 | 12/10/1996 | 5,583,816 | US |
| NMKS-0193.00/US | Utility - ORG | Issued | CIRCUIT WHICH PROVIDES POWER ON RESET DISABLE DURING A TEST MODE | 6/29/1994 | 08/267,666 | 10/3/1995 | 5,455,799 | US |
| NMKS-0194.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT MEMORY HAVING CONTROL CIRCUITRY FOR SHARED DATA BUS | 5/31/1994 | 08/254,718 | 5/28/1996 | 5,521,880 | US |
| NMKS-0195.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT MEMORY WITH DISABLED EDGE TRANSITION PULSE GENERATION DURING SPECIAL TEST MODE | 5/31/1994 | 08/251,337 | 2/20/1996 | 5,493,532 | US |
| NMKS-0196.00/US | Utility - ORG | Issued | VARIABLE INPUT THRESHOLD ADJUSTMENT | 7/29/1994 | 08/282,177 | 12/31/1996 | 5,589,783 | US |
| NMKS-0197.00/US | Utility - ORG | Issued | TEST MODE CONTROL CIRCUIT OF AN INTEGRATED CIRCUIT DEVICE | 7/29/1994 | 08/282,047 | 11/9/1999 | 5,982,188 | US |
| NMKS-0198.00/US | Utility - ORG | Issued | APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID | 8/10/1994 | 08/288,334 | 10/15/1996 | 5,566,112 | US |
| NMKS-0198.01/US | Utility - DIV | Issued | APPARATUS AND METHOD FOR ENABLING A BUS DRIVER WHEN A DATA SIGNAL IS VALID | 5/10/1995 | 08/438,276 | 10/29/1996 | 5,570,316 | US |
| NMKS-0199.00/US | Utility - ORG | Issued | PRE-CHARGED EXCLUSIONARY WIRED-CONNECTED PROGRAMMED REDUNDANT SELECT | 9/30/1994 | 08/316,087 | 2/27/1996 | 5,495,446 | US |
| NMKS-0200.00/US | Utility - ORG | Issued | FULL MEMORY CHIP LONG WRITE TEST MODE | 9/30/1994 | 08/315,337 | 3/26/1996 | 5,502,678 | US |
| NMKS-0201.00/US | Utility - ORG | Issued | LOW CURRENT DIFFERENTIAL LEVEL SHIFTER | 10/31/1994 | 08/331,892 | 5/14/1996 | 5,517,148 | US |
| NMKS-0202.00/US | Utility - ORG | Issued | CIRCUIT STRUCTURE AND METHOD FOR STRESS TESTING OF BIT LINES | 10/31/1994 | 08/331,699 | 3/11/1997 | 5,610,866 | US |
| NMKS-0203.00/US | Utility - ORG | Issued | APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN | 5/10/1995 | 08/438,903 | 11/12/1996 | 5,574,688 | US |
| NMKS-0204.00/US | Utility - ORG | Issued | POST-FABRICATION SELECTABLE REGISTERED AND NON-REGISTERED MEMORY | 12/22/1994 | 08/362,187 | 11/26/1996 | 5,579,263 | US |
| NMKS-0205.00/US | Utility - ORG | Issued | CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE | 12/16/1994 | 08/357,864 | 10/7/1996 | 5,568,084 | US |
| NMKS-0205.01/US | Utility - CON | Issued | CIRCUIT FOR PROVIDING A COMPENSATED BIAS VOLTAGE | 4/12/1996 | 08/631,063 | 8/5/1997 | 5,654,663 | US |
| NMKS-0206.00/US | Utility - ORG | Issued | OUTPUT DRIVER CIRCUITRY WITH LIMITED OUTPUT HIGH VOLTAGE | 12/20/1994 | 08/360,228 | 1/21/1997 | 5,536,297 | US |
| NMKS-0207.00/US | Utility - ORG | Issued | VOLTAGE REFERENCE CIRCUIT USING AN OFFSET COMPENSATING CURRENT SOURCE | 12/20/1994 | 08/360,229 | 8/20/1996 | 5,548,241 | US |
| NMKS-0208.00/US | Utility - ORG | Issued | OUTPUT DRIVER CIRCUITRY WITH SELECTIVE LIMITED OUTPUT HIGH VOLTAGE | 12/20/1994 | 08/359,397 | 1/14/1997 | 5,594,373 | US |
| NMKS-0209.00/US | Utility - ORG | Issued | ADJUSTABLE CURRENT SOURCE | 12/20/1994 | 08/359,927 | 12/3/1996 | 5,581,209 | US |
| NMKS-0210.00/US | Utility - ORG | Issued | VOLTAGE REFERENCE CIRCUIT HAVING A THRESHOLD VOLTAGE SHIFT | 12/20/1994 | 08/359,926 | 1/28/1997 | 5,598,122 | US |
| NMKS-0211.00/US | Utility - ORG | Issued | DYNAMICALLY CONTROLLED VOLTAGE REFERENCE CIRCUIT | 12/20/1994 | 08/360,227 | 12/31/1996 | 5,589,794 | US |
| NMKS-0212.01/US | Utility - CON | Issued | CLOCK PULSE EXTENDER MODE FOR CLOCKED MEMORY DEVICES HAVING PRECHARGED DATA PATHS | 4/30/1997 | 08/848,342 | 6/29/1999 | 5,917,353 | US |
| NMKS-0213.00/US | Utility - ORG | Issued | APPARATUS AND METHOD FOR MAPPING A REDUNDANT MEMORY COLUMN TO A DEFECTIVE MEMORY COLUMN | 5/10/1995 | 08/438,349 | 11/5/1996 | 5,572,470 | US |
| NMKS-0214.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR TESTING AN INTEGRATED CIRCUIT DEVICE | 8/25/1995 | 08/519,192 | 4/18/2000 | 6,052,806 | US |
| NMKS-0215.00/US | Utility - ORG | Issued | RESIDUAL CHARGE ELIMINATION FOR A MEMORY DEVICE | 12/29/1995 | 08/580,549 | 3/31/1998 | 5,734,608 | US |
| NMKS-0216.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TESTING MEMORIES IN INTEGRATED CIRCUIT FORM | 12/21/1995 | 08/575,953 | 10/7/1997 | 5,675,539 | US |
| NMKS-0217.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR ADDRESS DECODING IN AN INTEGRATED CIRCUIT MEMORY | 9/11/1995 | 08/526,500 | 4/21/1998 | 5,742,546 | US |
| NMKS-0218.00/US | Utility - ORG | Issued | CURRENT DETECTION CIRCUIT FOR READING A MEMORY IN INTEGRATED CIRCUIT FORM | 5/17/1996 | 08/649,282 | 12/16/1997 | 5,699,295 | US |

PATENT

REEL: 029505 FRAME: 0044

Exhibit A - US Issued Patents

| MTI-DRGNO | MatterType | MatterStatus | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|-----------------|----------------|--------------|---|------------|------------|------------|-----------|---------|
| NMMS-0219.00/US | Utility - ORG | Issued | AN ELECTRICALLY PROGRAMMABLE MEMORY WITH IMPROVED RETENTION OF DATA AND A METHOD OF WRITING DATA IN SAID MEMORY | 12/18/1995 | 08/573,897 | 7/29/1997 | 5,652,720 | US |
| NMMS-0220.00/US | Utility - ORG | Issued | CHARGE PUMP TYPE OF NEGATIVE VOLTAGE GENERATOR CIRCUIT AND METHOD | 6/13/1996 | 08/663,524 | 11/24/1998 | 5,841,314 | US |
| NMMS-0221.00/US | Utility - ORG | Issued | RESISTANCE REFERENCE CIRCUIT | 12/21/1995 | 08/576,881 | 2/10/1998 | 5,717,323 | US |
| NMMS-0222.00/US | Utility - ORG | Issued | DIGITAL RAMP GENERATOR | 5/30/1996 | 08/652,710 | 6/30/1998 | 5,774,390 | US |
| NMMS-0223.00/US | Utility - ORG | Issued | SENAL DICHOTOMIC METHOD FOR SENSING MULTIPLE-LEVEL NON-VOLATILE MEMORY CELLS, AND SENSING CIRCUIT IMPLEMENTING SUCH METHOD | 1/29/1996 | 08/593,650 | 12/23/1997 | 5,701,265 | US |
| NMMS-0224.01/US | Utility - CON | Issued | READING CIRCUIT FOR MULTILEVEL NON VOLATILE MEMORY CELL DEVICES | 6/4/1997 | 08/669,072 | 11/17/1998 | 5,838,612 | US |
| NMMS-0225.00/US | Utility - ORG | Issued | CIRCUIT FOR READING NON-VOLATILE MEMORIES | 7/31/1996 | 08/690,530 | 3/31/1998 | 5,734,610 | US |
| NMMS-0226.00/RE | Utility - REIS | Issued | CIRCUIT AND METHOD FOR READING A MEMORY CELL THAT CAN STORE MULTIPLE BITS OF DATA | 9/30/1999 | 09/410,164 | 9/30/1997 | RE38,166 | US |
| NMMS-0226.00/US | Utility - ORG | Abandoned | SENSE CIRCUIT FOR SERIES BINARY SENSING OF MULTILEVEL NONVOLATILE STORAGE ELEMENT | 1/29/1996 | 08/592,939 | 9/30/1997 | 5,673,221 | US |
| NMMS-0227.00/US | Utility - ORG | Issued | READING CIRCUIT FOR MEMORY CELL DEVICES HAVING A LOW SUPPLY VOLTAGE | 4/25/1996 | 08/638,976 | 12/2/1997 | 5,694,363 | US |
| NMMS-0228.00/US | Utility - ORG | Issued | MODULATED SLOPE SIGNAL GENERATION CIRCUIT, PARTICULARLY FOR LATCH DATA SENSING ARRANGEMENTS | 7/19/1996 | 08/684,431 | 4/7/1998 | 5,737,268 | US |
| NMMS-0229.00/US | Utility - ORG | Issued | THRESHOLD DETECTING DEVICE | 7/31/1996 | 08/688,956 | 12/8/1998 | 5,847,584 | US |
| NMMS-0230.00/US | Utility - ORG | Issued | CHARGE PUMP CIRCUIT WITH MULTIPLE BOOST STAGES | 7/19/1996 | 08/684,192 | 6/2/1998 | 5,760,497 | US |
| NMMS-0231.00/US | Utility - ORG | Issued | FLASH EEPROM WITH INTEGRATED DEVICE FOR LIMITING THE ERASE SOURCE VOLTAGE | 7/31/1996 | 08/692,936 | 1/14/2003 | 6,507,067 | US |
| NMMS-0232.00/US | Utility - ORG | Issued | NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES | 6/19/1996 | 08/665,862 | 8/19/1997 | 5,659,502 | US |
| NMMS-0232.01/US | Utility - CON | Issued | NEGATIVE WORD LINE VOLTAGE REGULATION CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES | 6/23/1997 | 08/881,713 | 7/6/1999 | 5,920,505 | US |
| NMMS-0233.00/US | Utility - ORG | Issued | PARALLEL PROGRAMMING METHOD OF MEMORY WORDS AND CORRESPONDING CIRCUIT | 9/30/1996 | 08/722,378 | 7/14/1998 | 5,781,474 | US |
| NMMS-0234.00/US | Utility - ORG | Issued | METHOD FOR SETTING THE THRESHOLD VOLTAGE OF A REFERENCE MEMORY CELL | 7/12/1996 | 08/679,656 | 7/21/1998 | 5,784,314 | US |
| NMMS-0235.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY DEVICE | 9/30/1996 | 08/720,491 | 12/1/1998 | 5,844,404 | US |
| NMMS-0236.00/US | Utility - ORG | Issued | ROW DECODING CIRCUIT FOR SEMICONDUCTOR NON-VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD | 3/27/1997 | 08/824,616 | 12/8/1998 | 5,848,013 | US |
| NMMS-0236.01/US | Utility - DIV | Issued | ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD | 12/2/1998 | 09/203,937 | 10/24/2000 | 6,137,725 | US |
| NMMS-0236.02/US | Utility - DIV | Issued | ROW DECODING CIRCUIT FOR A SEMICONDUCTOR NON VOLATILE ELECTRICALLY PROGRAMMABLE MEMORY AND CORRESPONDING METHOD | 8/7/2000 | 09/633,334 | 11/20/2001 | 6,320,792 | US |
| NMMS-0237.00/US | Utility - ORG | Issued | DEVICE FOR GENERATING AND REGULATING A GATE VOLTAGE IN A NON-VOLATILE MEMORY | 12/30/1996 | 08/775,111 | 10/13/1998 | 5,822,247 | US |
| NMMS-0238.00/US | Utility - ORG | Issued | SYSTEM FOR DETERMINING THE PROGRAMMED/NON PROGRAMMED STATUS OF A MEMORY CELL | 3/27/1997 | 08/827,409 | 1/26/1999 | 5,864,513 | US |
| NMMS-0239.00/US | Utility - ORG | Issued | BOOST REGULATOR | 1/21/1997 | 08/787,494 | 10/13/1998 | 5,821,806 | US |
| NMMS-0240.00/US | Utility - ORG | Issued | UNBALANCED LATCH AND FUSE CIRCUIT INCLUDING THE SAME | 7/19/1996 | 08/684,406 | 8/19/1997 | 5,659,498 | US |
| NMMS-0241.00/US | Utility - ORG | Issued | REFERENCE WORD LINE AND DATA PROPAGATION REPRODUCTION CIRCUIT FOR MEMORIES PROVIDED WITH HIERARCHICAL DECODERS | 3/27/1997 | 08/835,033 | 5/19/1998 | 5,754,483 | US |
| NMMS-0242.00/US | Utility - ORG | Issued | TIMESHARING INTERNAL BUS, PARTICULARLY FOR NON-VOLATILE MEMORIES | 3/7/1997 | 08/813,687 | 8/20/2002 | 6,438,669 | US |
| NMMS-0243.00/US | Utility - ORG | Issued | PARALLEL-DICHOTOMIC SERIAL SENSING METHOD FOR SENSING MULTIPLE-LEVEL NON VOLATILE MEMORY CELLS, AND SENSING CIRCUIT FOR ACTUATING SUCH METHOD | 7/31/1996 | 08/690,059 | 3/17/1998 | 5,729,490 | US |

PATENT

REEL: 029505 FRAME: 0045

Exhibit A - US Issued Patents

| NMKS-0244.01/US | Utility - CON | Issued | SUPPLY VOLTAGES SWITCHES CIRCUIT | 7/2/1998 | 09/109,630 | 3/21/2000 | 6,040,734 | US |
|-----------------|-----------------|-----------|---|------------|------------|------------|-----------|----|
| NMKS-0245.00/US | Utility - ORG | Abandoned | METHOD AND PROGRAMMING DEVICE FOR DETECTING AN ERROR IN A MEMORY | 12/24/1996 | 08/774,110 | 3/3/1998 | 5,724,290 | US |
| NMKS-0246.00/US | Utility - ORG | Issued | VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS | 10/23/1996 | 08/735,709 | 8/11/1998 | 5,793,679 | US |
| NMKS-0246.01/US | Utility - DIV | Issued | VOLTAGE GENERATOR FOR ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS | 2/27/1998 | 09/032,179 | 12/5/2000 | 6,157,054 | US |
| NMKS-0247.00/US | Utility - ORG | Issued | FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR | 7/24/1996 | 08/687,145 | 2/27/2001 | 6,195,291 | US |
| NMKS-0247.01/US | Utility - DIV | Issued | FLASH EEPROM WITH ON-CHIP ERASE SOURCE VOLTAGE GENERATOR | 1/23/2001 | 09/768,744 | 11/19/2002 | 6,483,750 | US |
| NMKS-0248.00/US | Utility - ORG | Issued | NEGATIVE CHARGE PUMP CIRCUIT FOR ELECTRICALLY ERASABLE SEMICONDUCTOR MEMORY DEVICES | 10/31/1996 | 08/751,299 | 5/19/1998 | 5,754,476 | US |
| NMKS-0249.00/US | Utility - ORG | Issued | ANALOG VOLTAGE-SIGNAL SELECTOR DEVICE | 11/1/1996 | 08/742,978 | 5/18/1999 | 5,905,387 | US |
| NMKS-0250.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH IMPROVED YIELD AND RELIABILITY | 6/28/1996 | 08/674,848 | 7/7/1998 | 5,778,012 | US |
| NMKS-0251.00/US | Utility - ORG | Issued | CIRCUIT FOR THE GENERATION OF A VOLTAGE AS A FUNCTION OF THE CONDUCTIVITY OF AN ELEMENTARY CELL OF A NON-VOLATILE MEMORY | 3/27/1997 | 08/835,031 | 9/1/1998 | 5,801,988 | US |
| NMKS-0252.00/US | Utility - ORG | Issued | ZERO CONSUMPTION POWER-ON-RESET | 1/30/1997 | 08/790,832 | 10/13/1998 | 5,821,788 | US |
| NMKS-0253.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR REDUNDANCY MANAGEMENT OF NON-VOLATILE MEMORIES | 3/27/1997 | 08/828,039 | 11/17/1998 | 5,838,619 | US |
| NMKS-0254.00/US | Utility - ORG | Issued | PROCESS FOR FABRICATING A MICROTIP CATHODE ASSEMBLY FOR A FIELD EMISSION DISPLAY PANEL | 12/13/1996 | 08/807,113 | 12/14/1999 | 6,000,980 | US |
| NMKS-0255.00/US | Utility - ORG | Issued | HIGH-VOLTAGE-RESISTANT MOS TRANSISTOR, AND CORRESPONDING MANUFACTURING PROCESS | 3/18/1997 | 08/824,888 | 11/2/1999 | 5,977,591 | US |
| NMKS-0256.01/US | Utility - CON | Issued | NONVOLATILE FLOATING-GATE MEMORY DEVICES, AND PROCESS OF FABRICATION | 4/13/2000 | 09/548,782 | 9/10/2002 | 6,448,138 | US |
| NMKS-0257.00/US | Utility - ORG | Issued | HIGH CAPACITY CAPACITOR AND CORRESPONDING MANUFACTURING PROCESS | 10/30/1996 | 08/739,997 | 4/24/2001 | 6,222,245 | US |
| NMKS-0258.00/US | Utility - ORG | Issued | ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS DEVICE FOR A REDUCED NUMBER OF PROGRAMMING CYCLES | 2/27/1997 | 08/807,574 | 7/20/1999 | 5,926,416 | US |
| NMKS-0259.00/US | Utility - ORG | Issued | PROCESS OF FABRICATING TUNNEL-OXIDE NONVOLATILE MEMORY DEVICES | 1/31/1997 | 08/792,893 | 10/6/1998 | 5,817,557 | US |
| NMKS-0260.00/US | Utility - ORG | Issued | FABRICATION OF NATURAL TRANSISTORS IN A NONVOLATILE MEMORY PROCESS | 1/16/1997 | 08/784,967 | 7/13/1999 | 5,923,975 | US |
| NMKS-0261.00/US | Utility - ORG | Issued | MULTI-LEVEL MEMORY CIRCUITS AND CORRESPONDING READING AND WRITING METHODS | 1/30/1997 | 08/791,348 | 1/12/1999 | 5,859,795 | US |
| NMKS-0262.00/US | Utility - NSPCT | Issued | MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED READING VOLTAGE | 10/30/1996 | 09/202,657 | 8/8/2000 | 6,101,121 | US |
| NMKS-0263.00/US | Utility - ORG | Issued | CLOCK CIRCUIT FOR READING A MULTILEVEL NON VOLATILE MEMORY CELLS DEVICE | 6/27/1997 | 08/883,822 | 11/16/1999 | 5,986,921 | US |
| NMKS-0264.00/US | Utility - NSPCT | Issued | MULTI-LEVEL MEMORY CIRCUIT WITH REGULATED WRITING VOLTAGE | 10/30/1996 | 09/202,656 | 8/1/2000 | 6,097,628 | US |
| NMKS-0265.00/US | Utility - ORG | Issued | SECTORIZED ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH REDUNDANCY | 3/21/1997 | 08/821,804 | 12/29/1998 | 5,854,764 | US |
| NMKS-0266.00/US | Utility - ORG | Issued | ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY DEVICE WITH TESTABLE REDUNDANCY CIRCUITS | 5/8/1997 | 08/853,756 | 12/7/1999 | 5,999,450 | US |
| NMKS-0267.00/US | Utility - ORG | Issued | SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS | 4/29/1997 | 08/845,916 | 6/29/1999 | 5,917,753 | US |
| NMKS-0267.01/US | Utility - CON | Issued | SENSING CIRCUITRY FOR READING AND VERIFYING THE CONTENTS OF ELECTRICALLY PROGRAMMABLE/ERASABLE NON-VOLATILE MEMORY CELLS | 12/9/1998 | 09/209,319 | 4/25/2000 | 6,055,187 | US |
| NMKS-0268.00/US | Utility - ORG | Issued | ERASING METHOD FOR A NON-VOLATILE MEMORY | 12/24/1996 | 08/774,860 | 10/6/1998 | 5,818,763 | US |
| NMKS-0269.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR GENERATING A SYNCHRONIZING AND SIGNAL | 11/26/1997 | 08/978,665 | 3/23/1999 | 5,886,949 | US |
| NMKS-0270.01/US | Utility - DIV | Issued | METHOD OF AVOIDING DISTURBANCE DURING THE STEP OF PROGRAMMING AND ERASING AN ELECTRICALLY PROGRAMMABLE, SEMICONDUCTOR NON-VOLATILE STORAGE DEVICE | 9/27/1999 | 09/407,135 | 2/27/2001 | 6,195,290 | US |

PATENT

REEL: 029505 FRAME: 0046

Exhibit A - US Issued Patents

| NIM-DataNo | MarketType | MarketStatus | Title | FileDate | SerialNo | IssueDate | PatentNo | Country |
|-----------------|----------------|--------------|--|------------|------------|------------|-----------|---------|
| NMKS-0271.00/US | Utility - ORG | Issued | ERASE VOLTAGE CONTROL CIRCUIT FOR AN ELECTRICALLY ERASABLE NON-VOLATILE MEMORY CELL | 1/23/1997 | 08/787,907 | 2/24/1998 | 5,721,707 | US |
| NMKS-0272.00/US | Utility - ORG | Issued | METHOD FOR ERASING AN ELECTRICALLY PROGRAMMABLE AND ERASABLE NON-VOLATILE MEMORY CELL | 1/24/1997 | 08/788,530 | 7/21/1998 | 5,784,319 | US |
| NMKS-0273.00/US | Utility - ORG | Issued | MONOLITHICALLY INTEGRATED PROGRAMMABLE DEVICE HAVING ELEMENTARY MODULES CONNECTED ELECTRICALLY BY MEANS OF MEMORY CELLS OF THE FLASH TYPE | 12/27/1996 | 08/777,296 | 12/21/1999 | 6,005,411 | US |
| NMKS-0274.00/US | Utility - ORG | Issued | PAGE-MODE MEMORY DEVICE WITH MULTIPLE-LEVEL MEMORY CELLS | 6/5/1997 | 08/869,208 | 5/26/1998 | 5,757,719 | US |
| NMKS-0275.00/US | Utility - ORG | Issued | HIGH VOLTAGES DETECTOR CIRCUIT AND INTEGRATED CIRCUIT USING SAME | 1/30/1997 | 08/791,700 | 8/18/1998 | 5,796,275 | US |
| NMKS-0276.00/US | Utility - ORG | Issued | PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES, AND CORRESPONDING DEVICE | 1/27/1998 | 09/014,437 | 5/2/2000 | 6,057,591 | US |
| NMKS-0276.01/US | Utility - DIV | Issued | PROCESS FOR FORMING AN EDGE STRUCTURE TO SEAL INTEGRATED ELECTRONIC DEVICES | 3/24/2000 | 09/534,675 | 4/3/2001 | 6,210,994 | US |
| NMKS-0277.00/US | Utility - ORG | Issued | MEMORY ARCHITECTURE FOR FLEXIBLE READING MANAGEMENT, PARTICULARLY FOR NON-VOLATILE MEMORIES, HAVING NOISE-IMMUNITY FEATURES, MATCHING DEVICE PERFORMANCE, AND HAVING OPTIMIZED THROUGHOUT | 4/24/1997 | 08/847,385 | 6/29/1999 | 5,917,768 | US |
| NMKS-0278.00/US | Utility - ORG | Issued | CIRCUITS AND METHODS FOR READ-ENABLING MEMORY DEVICES SYNCHRONOUSLY WITH THE REACHING OF THE MINIMUM FUNCTIONALITY CONDITIONS OF THE MEMORY CELLS AND READING CIRCUITS, PARTICULARLY FOR NON-VOLATILE MEMORIES | 4/24/1997 | 08/840,056 | 3/2/1999 | 5,878,049 | US |
| NMKS-0279.00/US | Utility - ORG | Issued | COLUMN MULTIPLEXER | 5/9/1997 | 08/853,732 | 7/7/1998 | 5,777,941 | US |
| NMKS-0280.00/US | Utility - ORG | Issued | DRIVER DEVICE FOR SELECTION LINES FOR A MULTIPLEXER, TO BE USED IN A WIDE RANGE OF SUPPLY VOLTAGES, PARTICULARLY FOR NON-VOLATILE MEMORIES | 3/27/1997 | 08/826,223 | 5/12/1998 | 5,751,654 | US |
| NMKS-0281.00/US | Utility - ORG | Issued | A MEMORY UNDER TEST PROGRAMMING AND READING DEVICE | 3/28/1997 | 08/835,030 | 11/14/2000 | 6,148,413 | US |
| NMKS-0282.00/US | Utility - ORG | Issued | DECODING HIERARCHICAL ARCHITECTURE FOR HIGH INTEGRATION MEMORIES | 1/30/1997 | 08/791,746 | 12/29/1998 | 5,854,770 | US |
| NMKS-0283.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY DEVICE CAPABLE OF READING DATA WITH AN APPROPRIATE SELF-TIMING AND A REDUCED NUMBER OF REFERENCE LINES | 3/27/1997 | 08/826,489 | 8/31/1999 | 5,946,237 | US |
| NMKS-0283.01/US | Utility - DIV | Issued | DATA READING PATH MANAGEMENT ARCHITECTURE FOR A MEMORY DEVICE, PARTICULARLY FOR NON-VOLATILE MEMORIES | 7/12/1999 | 09/351,603 | 4/3/2001 | 6,212,096 | US |
| NMKS-0284.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE HAVING OPTIMIZED MANAGEMENT OF DATA TRANSMISSION LINES | 3/7/1997 | 08/812,595 | 11/3/1998 | 5,831,891 | US |
| NMKS-0285.00/US | Utility - ORG | Issued | PULSE GENERATION CIRCUIT AND METHOD FOR SYNCHRONIZED DATA LOADING IN AN OUTPUT PRE-BUFFER | 3/27/1997 | 08/826,009 | 1/12/1999 | 5,859,810 | US |
| NMKS-0286.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT WITH UNEQUALLY-SIZED, PAIRED MEMORY COUPLED TO ODD NUMBER OF INPUT/OUTPUT PADS | 6/7/1995 | 08/477,244 | 4/29/1997 | 5,625,605 | US |
| NMKS-0287.01/US | Utility - CON | Issued | CONSTANT CURRENT SOURCE WITH REDUCED SENSITIVITY TO SUPPLY VOLTAGE AND PROCESS VARIATION | 6/24/1996 | 08/667,481 | 8/11/1998 | 5,793,247 | US |
| NMKS-0288.00/US | Utility - ORG | Issued | CIRCUIT FOR PROVIDING A BIAS VOLTAGE COMPENSATED FOR P-CHANNEL TRANSISTOR VARIATIONS | 6/5/1995 | 08/464,551 | 6/17/1997 | 5,640,122 | US |
| NMKS-0289.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR AN OUTPUT DRIVER WITH REDUCED OUTPUT IMPEDANCE | 3/31/1995 | 08/414,103 | 11/19/1996 | 5,576,656 | US |
| NMKS-0290.00/RE | Utility - REIS | Issued | POWER SUPPLY SWITCH REFERENCE CIRCUITRY | 5/5/2000 | 09/568,201 | 5/5/1998 | RE57,876 | US |
| NMKS-0290.00/US | Utility - ORG | Abandoned | POWER SUPPLY SWITCH REFERENCE CIRCUITRY | 6/5/1995 | 08/464,082 | 5/5/1998 | 5,747,890 | US |
| NMKS-0291.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR BIASING BIT LINES | 6/7/1995 | 08/484,491 | 6/16/1998 | 5,768,206 | US |
| NMKS-0292.00/US | Utility - ORG | Issued | REDUCED PIN COUNT STRESS TEST CIRCUIT FOR INTEGRATED MEMORY DEVICES AND METHOD THEREFOR | 6/7/1995 | 08/476,658 | 1/7/1997 | 5,592,422 | US |
| NMKS-0293.00/US | Utility - ORG | Issued | FAULT DETECTION FOR ENTIRE WAFER STRESS TEST | 7/31/1995 | 08/509,158 | 4/8/1997 | 5,619,462 | US |

PATENT

REEL: 029505 FRAME: 0047

Exhibit A - US Issued Patents

| Patent No. | Matter Type | Matter Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|--|------------|------------|------------|------------|---------|
| NMMS-0294.01/US | Utility - CON | Issued | INTEGRATED MEMORY CIRCUIT WITH SEQUENCED BITLINES FOR STRESS TEST | 4/7/1997 | 08/833,582 | 4/28/1998 | 5,745,420 | US |
| NMMS-0295.01/US | Utility - CON | Issued | INTEGRATED MEMORY CIRCUIT FOR TEST MODE ENTRY DURING POWER UP | 9/12/1996 | 08/712,960 | 12/30/1997 | 5,703,512 | US |
| NMMS-0296.00/US | Utility - ORG | Issued | COLLAPSE REDUNDANCY OF A MULTIPLE BLOCK MEMORY ARCHITECTURE | 7/31/1995 | 08/509,351 | 3/4/1997 | 5,608,678 | US |
| NMMS-0297.00/US | Utility - ORG | Issued | STRUCTURE FOR Deselecting Broken Select Lines In Memory Arrays | 7/31/1995 | 08/509,211 | 7/15/1997 | 5,648,933 | US |
| NMMS-0298.00/US | Utility - ORG | Issued | WRITE CONTROLLED ADDRESS BUFFER | 8/31/1995 | 08/521,800 | 5/13/1997 | 5,629,996 | US |
| NMMS-0299.00/US | Utility - ORG | Issued | REDUNDANCY ARCHITECTURE | 12/29/1995 | 08/582,424 | 3/18/1997 | 5,612,918 | US |
| NMMS-0300.00/US | Utility - ORG | Issued | TEST MODE ACTIVATION AND DATA OVERRIDE | 1/19/1996 | 08/587,709 | 11/7/2000 | 6,144,594 | US |
| NMMS-0301.02/US | Utility - CON | Issued | TEST MODE ACTIVATION AND DATA OVERRIDE | 12/29/1995 | 09/457,558 | 10/2/2001 | 6,297,996 | US |
| NMMS-0301.00/US | Utility - ORG | Issued | PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY | 1/19/1996 | 08/588,730 | 12/23/1997 | 5,701,275 | US |
| NMMS-0301.01/US | Utility - DIV | Issued | PIPELINED CHIP ENABLE CONTROL CIRCUITRY AND METHODOLOGY | 6/19/1997 | 08/878,612 | 8/25/1998 | 5,798,980 | US |
| NMMS-0302.00/US | Utility - ORG | Issued | OUTPUT DRIVER CIRCUITRY HAVING A SINGLE SLEW RATE RESISTOR | 1/19/1996 | 08/588,988 | 9/1/1998 | 5,801,563 | US |
| NMMS-0303.00/US | Utility - ORG | Issued | REDUNDANCY CONTROL | 12/29/1995 | 08/580,827 | 8/4/1998 | 5,790,462 | US |
| NMMS-0304.00/US | Utility - ORG | Issued | WRITE PASS THROUGH CIRCUIT | 1/19/1996 | 08/588,662 | 8/12/1997 | 5,657,292 | US |
| NMMS-0305.00/US | Utility - ORG | Issued | DATA-INPUT DEVICE FOR GENERATING TEST SIGNALS ON BIT AND BIT-COMPLEMENT LINES | 1/19/1996 | 08/588,762 | 12/1/1998 | 5,845,059 | US |
| NMMS-0306.00/US | Utility - ORG | Issued | WRITE DRIVER HAVING A TEST FUNCTION | 1/19/1996 | 08/589,141 | 4/28/1998 | 5,745,432 | US |
| NMMS-0307.01/US | Utility - CON | Issued | CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL | 5/19/1997 | 08/858,295 | 9/15/1998 | 5,808,960 | US |
| NMMS-0308.01/US | Utility - CON | Issued | CIRCUIT AND METHOD FOR TRACKING THE START OF A WRITE TO A MEMORY CELL | 5/19/1997 | 08/858,295 | 9/15/1998 | 5,808,960 | US |
| NMMS-0308.01/US | Utility - CON | Issued | CIRCUIT AND METHOD FOR TERMINATING A WRITE TO A MEMORY CELL | 5/19/1997 | 08/858,788 | 10/20/1998 | 5,825,691 | US |
| NMMS-0309.00/US | Utility - ORG | Issued | CLOCKED SENSE AMPLIFIER WITH WORDLINE TRACKING | 1/19/1996 | 08/587,728 | 9/1/1998 | 5,802,004 | US |
| NMMS-0309.01/US | Utility - DIV | Issued | CLOCKED SENSE AMPLIFIER WITH WORDLINE TRACKING | 10/6/1997 | 08/944,649 | 10/27/1998 | 5,828,622 | US |
| NMMS-0310.01/US | Utility - CON | Lapsed | MEMORY-ROW SELECTOR HAVING A TEST FUNCTION | 9/10/1997 | 08/926,883 | 12/8/1998 | 5,848,018 | US |
| NMMS-0311.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL | 1/19/1996 | 08/587,711 | 1/26/1999 | 5,864,696 | US |
| NMMS-0311.01/US | Utility - DIV | Issued | CIRCUIT AND METHOD FOR SETTING THE TIME DURATION OF A WRITE TO A MEMORY CELL | 2/9/1998 | 09/020,430 | 12/21/1999 | 6,006,339 | US |
| NMMS-0312.00/US | Utility - ORG | Issued | LOW-POWER READ CIRCUIT AND METHOD FOR CONTROLLING A SENSE AMPLIFIER | 1/19/1996 | 08/589,024 | 4/8/1997 | 5,619,466 | US |
| NMMS-0313.01/US | Utility - DIV | Issued | DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL | 9/15/1997 | 08/929,987 | 3/16/1999 | 5,883,838 | US |
| NMMS-0313.02/US | Utility - CON | Issued | DEVICE AND METHOD FOR DRIVING A CONDUCTIVE PATH WITH A SIGNAL | 11/19/1997 | 08/974,747 | 4/20/1999 | 5,896,336 | US |
| NMMS-0314.00/US | Utility - ORG | Issued | CIRCUITRY AND METHODOLOGY TO TEST SINGLE BIT FAILURES OF INTEGRATED CIRCUIT MEMORY DEVICES | 8/24/1995 | 08/519,075 | 5/27/1997 | 5,633,828 | US |
| NMMS-0315.00/US | Utility - ORG | Issued | ENTIRE WAFER STRESS TEST METHOD FOR INTEGRATED MEMORY DEVICES AND CIRCUIT THEREFOR | 8/21/1995 | 08/484,609 | 9/17/1996 | 5,557,573 | US |
| NMMS-0316.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR THE PROTECTION OF NON-VOLATILE MEMORY ZONES | 3/29/1996 | 08/623,044 | 9/22/1998 | 5,812,446 | US |
| NMMS-0317.00/US | Utility - ORG | Issued | PHASE GENERATOR CIRCUIT FOR CHARGE PUMP TYPE OF NEGATIVE SUPPLY CIRCUIT | 6/13/1996 | 08/664,083 | 6/2/1998 | 5,760,638 | US |
| NMMS-0318.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY | 8/27/1996 | 08/703,811 | 3/16/1999 | 5,883,833 | US |
| NMMS-0318.01/US | Utility - DIV | Issued | METHOD AND CIRCUIT FOR THE PROGRAMMING AND ERASURE OF A MEMORY | 11/24/1998 | 09/198,431 | 3/7/2000 | 6,034,895 | US |
| NMMS-0319.00/US | Utility - ORG | Issued | HIGH VOLTAGE GENERATOR | 12/11/1996 | 08/762,677 | 9/1/1998 | 5,801,577 | US |
| NMMS-0320.00/US | Utility - ORG | Issued | METHODS AND APPARATUS FOR PROGRAMMING CONTENT-ADDRESSABLE MEMORIES USING FLOATING-GATE MEMORY CELLS | 10/25/1996 | 08/738,231 | 4/7/1998 | 5,737,266 | US |
| NMMS-0321.00/US | Utility - ORG | Issued | ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY CIRCUIT HAVING MEANS FOR AUTONOMOUS REFRESHING DEPENDENT UPON ON PERIODIC CLOCK PULSES | 2/12/1997 | 08/797,948 | 9/7/1999 | 5,950,224 | US |
| NMMS-0322.00/US | Utility - ORG | Issued | DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED | 1/24/1997 | 08/792,962 | 3/23/1999 | 5,886,549 | US |

PATENT

REEL: 029505 FRAME: 0048

Exhibit A - US Issued Patents

| Pub No. | Matter Type | Matter Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|------------------|---------------|---------------|--|------------|------------|------------|------------|---------|
| NMXXS-0322.00/US | Utility - CON | Issued | DEVICE TO NEUTRALIZE AN ELECTRONIC CIRCUIT WHEN IT IS BEING POWERED OR DISCONNECTED | 11/17/1998 | 09/199,735 | 9/26/2000 | 6,125,022 | US |
| NMXXS-0323.00/US | Utility - ORG | Issued | FLASH-EEPROM WITH EMBEDDED EEPROM | 4/10/1997 | 08/833,925 | 12/15/1998 | 5,850,092 | US |
| NMXXS-0323.01/US | Utility - DIV | Issued | FLASH-EEPROM WITH EMBEDDED EEPROM | 10/1/1998 | 09/156,761 | 6/13/2000 | 6,074,916 | US |
| NMXXS-0324.00/US | Utility - ORG | Issued | DATA SENSING TIMING MODULATING CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES | 3/27/1997 | 08/825,098 | 3/9/1999 | 5,881,001 | US |
| NMXXS-0325.00/US | Utility - ORG | Issued | SYNCHRONIZATION SIGNAL GENERATION CIRCUIT AND METHOD | 5/30/1997 | 08/855,748 | 9/28/1999 | 5,959,935 | US |
| NMXXS-0326.00/US | Utility - ORG | Issued | POWER ON RESET CIRCUIT WITH AUTO TURN OFF | 4/30/1997 | 08/846,757 | 7/27/1999 | 5,929,674 | US |
| NMXXS-0327.00/US | Utility - ORG | Issued | UPROM CELL FOR LOW VOLTAGE SUPPLY | 4/30/1997 | 08/846,755 | 10/13/1998 | 5,822,259 | US |
| NMXXS-0328.00/US | Utility - ORG | Issued | BIASING CIRCUIT FOR UPROM CELLS WITH LOW VOLTAGE SUPPLY | 4/30/1997 | 08/846,753 | 1/12/1999 | 5,859,797 | US |
| NMXXS-0329.00/US | Utility - ORG | Issued | LINE DECODER FOR MEMORY DEVICES | 5/23/1997 | 08/862,563 | 1/25/2000 | 6,018,255 | US |
| NMXXS-0329.01/US | Utility - DIV | Issued | LINE DECODER FOR MEMORY DEVICES | 11/2/1999 | 09/432,642 | 7/25/2000 | 6,094,073 | US |
| NMXXS-0330.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR READING LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS | 6/18/1997 | 08/879,017 | 10/3/2000 | 6,128,225 | US |
| NMXXS-0331.00/US | Utility - ORG | Issued | LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY DEVICE WITH VOLTAGE BOOSTING | 6/18/1997 | 08/877,927 | 5/11/1999 | 5,903,498 | US |
| NMXXS-0332.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR GENERATING A READ REFERENCE SIGNAL FOR NONVOLATILE MEMORY CELLS | 6/18/1997 | 08/877,921 | 9/8/1998 | 5,805,500 | US |
| NMXXS-0333.01/US | Utility - CON | Issued | NONVOLATILE MEMORY CELLS | 7/27/2001 | 09/916,954 | 7/8/2003 | 6,590,247 | US |
| NMXXS-0334.00/US | Utility - ORG | Issued | BIDIRECTIONAL CHARGE PUMP GENERATING EITHER A POSITIVE OR NEGATIVE VOLTAGE | 7/28/1997 | 08/900,165 | 2/6/2001 | 6,184,741 | US |
| NMXXS-0335.00/US | Utility - ORG | Issued | BICMOS NEGATIVE CHARGE PUMP | 11/5/1997 | 08/965,068 | 1/18/2000 | 6,016,073 | US |
| NMXXS-0336.00/US | Utility - ORG | Issued | POSITIVE CHARGE PUMP | 10/8/1997 | 08/946,727 | 6/13/2000 | 6,075,402 | US |
| NMXXS-0337.00/US | Utility - ORG | Issued | OUTPUT STAGE FOR A MEMORY DEVICE AND FOR LOW VOLTAGE APPLICATIONS | 7/23/1997 | 08/899,228 | 4/10/2001 | 6,215,329 | US |
| NMXXS-0338.00/US | Utility - ORG | Issued | LOW NOISE OUTPUT BUFFER FOR SEMICONDUCTOR ELECTRONIC CIRCUITS | 7/8/1997 | 08/889,653 | 5/9/2000 | 6,060,753 | US |
| NMXXS-0339.00/US | Utility - ORG | Issued | HIGH VOLTAGE TOLERANCE OUTPUT STAGE | 7/23/1997 | 08/898,811 | 11/21/2000 | 6,150,844 | US |
| NMXXS-0340.00/US | Utility - CON | Issued | SINGLE-CELL REFERENCE SIGNAL GENERATING CIRCUIT FOR READING NONVOLATILE MEMORY | 6/17/1997 | 08/877,066 | 8/31/1999 | 5,946,238 | US |
| NMXXS-0341.00/US | Utility - ORG | Issued | INTEGRATED DEVICE WITH PADS | 3/5/1997 | 08/811,577 | 7/13/1999 | 5,923,076 | US |
| NMXXS-0342.00/US | Utility - ORG | Issued | NMOS NEGATIVE CHARGE PUMP | 1/23/1998 | 09/012,331 | 10/10/2000 | 6,130,572 | US |
| NMXXS-0343.00/US | Utility - ORG | Issued | ADDRESS TRANSITION DETECTION CIRCUIT | 3/5/1997 | 08/811,869 | 9/29/1998 | 5,815,464 | US |
| NMXXS-0344.00/US | Utility - ORG | Issued | METHOD FOR RECOVERING FAILED MEMORY DEVICES | 3/18/1997 | 08/816,766 | 4/25/2000 | 6,055,655 | US |
| NMXXS-0345.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR GENERATING A POWER-ON RESET SIGNAL | 3/27/1997 | 08/828,791 | 9/28/1999 | 5,959,476 | US |
| NMXXS-0346.01/US | Utility - ORG | Issued | GAIN MODULATED SENSE AMPLIFIER | 3/27/1997 | 08/828,790 | 5/4/1999 | 5,901,087 | US |
| NMXXS-0346.00/US | Utility - DIV | Issued | GAIN MODULATED SENSE AMPLIFIER, PARTICULARLY FOR MEMORY DEVICES | 3/26/1998 | 09/048,941 | 6/20/2000 | 6,078,523 | US |
| NMXXS-0347.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD TO ADJUST MEMORY TIMING | 3/28/1997 | 08/825,138 | 3/23/1999 | 5,886,945 | US |
| NMXXS-0348.00/US | Utility - ORG | Issued | STANDBY VOLTAGE BOOSTING STAGE AND METHOD FOR A MEMORY DEVICE | 3/27/1997 | 08/826,008 | 3/30/1999 | 5,899,723 | US |
| NMXXS-0349.00/US | Utility - ORG | Issued | VOLTAGE BOOSTER FOR MEMORY DEVICES | 3/27/1997 | 08/824,958 | 9/8/1998 | 5,805,435 | US |
| NMXXS-0350.00/US | Utility - ORG | Issued | CIRCUIT FOR THE SWITCHING OF SUPPLY VOLTAGES IN ELECTRICALLY PROGRAMMABLE AND CANCELABLE NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES | 4/7/1997 | 08/835,294 | 5/19/1998 | 5,754,473 | US |
| NMXXS-0351.00/US | Utility - ORG | Issued | AUTO-SAVING CIRCUIT FOR PROGRAMMING CONFIGURATION ELEMENTS IN NON-VOLATILE MEMORY DEVICES | 4/7/1997 | 08/835,296 | 1/26/1999 | 5,864,500 | US |
| NMXXS-0352.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR PROGRAMMING ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS IN A CELL MATRIX | 4/4/1997 | 08/833,336 | 1/16/2001 | 6,175,521 | US |
| NMXXS-0353.00/US | Utility - ORG | Issued | CIRCUIT FOR DETECTING THE COINCIDENCE BETWEEN A BINARY INFORMATION UNIT STORED THEREIN AND AN EXTERNAL DATUM | 3/17/1997 | 08/819,519 | 9/28/1999 | 5,959,917 | US |
| NMXXS-0354.00/US | Utility - ORG | Issued | METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY | 4/17/1997 | 08/841,904 | 11/17/1998 | 5,838,623 | US |

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REEL: 029505 FRAME: 0049

Exhibit A - US Issued Patents

| App No | Matter Type | Matter Status | Title | Filed Date | Serial No | Issue Date | Patent No | Country |
|------------------|---------------|---------------|--|------------|------------|------------|-----------|---------|
| NMXXS-0364.01/US | Utility - CON | Issued | METHOD FOR DETECTING REDUNDED DEFECTIVE ADDRESSES IN A MEMORY DEVICE WITH REDUNDANCY | 10/30/1998 | 09/183,469 | 8/10/1999 | 5,936,907 | US |
| NMXXS-0355.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY DEVICE WITH ROW REDUNDANCY | 4/17/1997 | 08/842,835 | 3/30/1999 | 5,889,710 | US |
| NMXXS-0356.00/US | Utility - ORG | Issued | REDUNDANCY MEMORY REGISTER | 4/17/1997 | 08/844,903 | 9/22/1998 | 5,812,467 | US |
| NMXXS-0357.00/US | Utility - ORG | Issued | CIRCUIT FOR TRANSFERRING REDUNDANCY DATA OF A REDUNDANCY CIRCUIT INSIDE A MEMORY DEVICE BY MEANS OF A TIME-SHARED APPROACH | 6/5/1997 | 08/869,859 | 1/26/1999 | 5,864,562 | US |
| NMXXS-0358.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY DEVICE WITH ROW AND COLUMN REDUNDANCY CIRCUITS AND A TIME-SHARED REDUNDANCY CIRCUIT TEST ARCHITECTURE | 6/5/1997 | 08/869,367 | 2/2/1999 | 5,867,504 | US |
| NMXXS-0359.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY AND TIME-SHARED REDUNDANCY DATA TRANSFER APPROACH | 6/3/1997 | 08/868,214 | 10/19/1999 | 5,968,183 | US |
| NMXXS-0360.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH CLOCKED COLUMN REDUNDANCY | 6/3/1997 | 08/868,213 | 11/3/1998 | 5,851,915 | US |
| NMXXS-0361.00/US | Utility - ORG | Issued | PRE-CHARGE STEP DETERMINING CIRCUIT OF A GENERIC BIT LINE PARTICULARLY FOR NON-VOLATILE MEMORIES | 4/7/1997 | 08/835,347 | 5/9/2000 | 6,061,273 | US |
| NMXXS-0362.00/US | Utility - ORG | Issued | READ CIRCUIT AND METHOD FOR NONVOLATILE MEMORY CELLS WITH AN EQUALIZING STRUCTURE | 6/18/1997 | 08/877,922 | 3/23/1999 | 5,886,925 | US |
| NMXXS-0363.00/US | Utility - ORG | Issued | MULTILEVEL NON VOLATILE MEMORY DEVICE | 8/22/1997 | 08/916,874 | 12/7/1999 | 5,999,445 | US |
| NMXXS-0364.00/US | Utility - ORG | Issued | FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT | 9/30/1997 | 08/940,278 | 8/31/1999 | 5,946,235 | US |
| NMXXS-0364.01/US | Utility - CON | Issued | FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT | 8/13/1999 | 09/373,813 | 5/22/2001 | 6,236,592 | US |
| NMXXS-0364.02/US | Utility - CON | Issued | FLOATING GATE MOS TRANSISTOR CHARGE INJECTION CIRCUIT AND COMPUTATION DEVICES INCORPORATING IT | 8/9/2000 | 09/636,397 | 6/26/2001 | 6,252,802 | US |
| NMXXS-0365.00/US | Utility - ORG | Issued | ASYMMETRICAL PULSIVE DELAY NETWORK | 7/25/1997 | 08/900,424 | 4/4/2000 | 6,046,619 | US |
| NMXXS-0366.00/US | Utility - ORG | Issued | CONTROL CIRCUIT OF AN OUTPUT BUFFER | 9/19/1997 | 08/934,499 | 5/18/1999 | 5,905,678 | US |
| NMXXS-0367.00/US | Utility - ORG | Issued | PROTECTION CIRCUIT FOR REDUNDANCY REGISTER SET-UP CELLS OF ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICES | 10/30/1997 | 08/961,368 | 12/29/1998 | 5,854,762 | US |
| NMXXS-0368.00/US | Utility - ORG | Issued | PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES | 12/9/1997 | 08/987,454 | 5/29/2001 | 6,239,042 | US |
| NMXXS-0368.01/US | Utility - DIV | Issued | PROCESS FOR REALIZING AN INTERMEDIATE DIELECTRIC LAYER FOR ENHANCING THE PLANARITY IN SEMICONDUCTOR ELECTRONIC DEVICES | 8/24/2000 | 09/645,711 | 10/29/2002 | 6,472,750 | US |
| NMXXS-0369.00/US | Utility - ORG | Issued | FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE AND MANUFACTURING METHOD | 9/29/1997 | 08/940,856 | 4/25/2000 | 6,054,731 | US |
| NMXXS-0369.01/US | Utility - DIV | Issued | Floating gate non-volatile memory cell with low erasing voltage and having different potential barriers | 3/8/2000 | 09/521,867 | 11/14/2000 | 6,147,380 | US |
| NMXXS-0369.02/US | Utility - DIV | Issued | METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE | 3/8/2000 | 09/521,876 | 6/4/2002 | 6,399,444 | US |
| NMXXS-0369.03/US | Utility - DIV | Issued | METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC | 5/30/2002 | 10/158,706 | 3/23/2004 | 6,710,394 | US |
| NMXXS-0369.04/US | Utility - DIV | Issued | METHOD OF MAKING FLOATING GATE NON-VOLATILE MEMORY CELL WITH LOW ERASING VOLTAGE HAVING DOUBLE LAYER GATE DIELECTRIC | 3/3/2004 | 10/792,308 | 1/11/2005 | 6,841,445 | US |
| NMXXS-0370.00/US | Utility - ORG | Issued | PROCESS FOR DEPOSITING A STRATIFIED DIELECTRIC STRUCTURE FOR ENHANCING THE PLANARITY OF SEMICONDUCTOR ELECTRONIC DEVICES | 12/23/1997 | 08/996,920 | 11/30/1999 | 5,994,231 | US |
| NMXXS-0371.00/US | Utility - ORG | Abandoned | METHOD OF PLANARIZING A SEMICONDUCTOR DEVICE BY DEPOSITING A DIELECTRIC PLY STRUCTURE | 12/23/1997 | 08/997,403 | 12/5/2000 | 6,156,637 | US |
| NMXXS-0371.03/US | Utility - DIV | Abandoned | PLANARIZATION STRUCTURE AND METHOD FOR DIELECTRIC LAYERS | 10/13/2000 | 09/687,217 | 10/7/2003 | 6,630,739 | US |
| NMXXS-0372.00/US | Utility - ORG | Issued | READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS | 9/29/1997 | 08/940,115 | 3/16/1999 | 5,883,837 | US |
| NMXXS-0372.01/US | Utility - DIV | Issued | READING CIRCUIT FOR SEMICONDUCTOR MEMORY CELLS | 12/1/1998 | 09/203,798 | 10/26/1999 | 5,973,966 | US |
| NMXXS-0373.00/US | Utility - ORG | Issued | STARCASE ADAPTIVE VOLTAGE GENERATOR CIRCUIT | 2/26/1998 | 09/032,282 | 9/7/1999 | 5,949,656 | US |
| NMXXS-0374.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT ARCHITECTURE FOR TESTING A NON-VOLATILE MEMORY DEVICE | 5/30/1997 | 08/865,642 | 6/27/2000 | 6,081,911 | US |

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REEL: 029505 FRAME: 0050

Exhibit A - US Issued Patents

| MTI-DC-NO. | Matter Type | Matter Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|---|------------|------------|------------|------------|---------|
| NMMS-0375.00/US | Utility - ORG | Issued | SELF-REGULATED EQUALIZER, PARTICULARLY FOR SENSE AMPLIFIERS | 10/30/1997 | 08/960,926 | 11/16/1999 | 5,986,954 | US |
| NMMS-0376.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT FOR GENERATING INITIALIZATION SIGNALS FOR MEMORY CELL SENSING CIRCUITS | 5/30/1997 | 08/866,283 | 6/22/1999 | 5,914,901 | US |
| NMMS-0377.00/US | Utility - ORG | Issued | CIRCUIT FOR IMMUNIZING AN INTEGRATED CIRCUIT FROM NOISE AFFECTING ENABLE SIGNALS OF THE INTEGRATED CIRCUIT | 3/4/1997 | 08/811,548 | 5/11/1999 | 5,903,166 | US |
| NMMS-0378.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS | 2/20/1998 | 09/027,343 | 11/23/1999 | 5,990,526 | US |
| NMMS-0378.01/US | Utility - DIV | Issued | MEMORY DEVICE WITH A MEMORY CELL ARRAY IN TRIPLE WELL, AND RELATED MANUFACTURING PROCESS | 9/3/1999 | 09/389,955 | 6/6/2000 | 6,071,778 | US |
| NMMS-0379.00/US | Utility - ORG | Issued | HIGH VOLTAGE CAPACITOR | 7/20/1998 | 09/119,115 | 2/13/2001 | 6,188,121 | US |
| NMMS-0380.00/US | Utility - ORG | Issued | CIRCUIT FOR THE GENERATION AND RESET OF TIMING SIGNAL USED FOR READING A MEMORY DEVICE | 3/4/1997 | 08/811,386 | 8/11/1998 | 5,793,699 | US |
| NMMS-0381.00/US | Utility - ORG | Issued | CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT | 10/24/1997 | 08/957,885 | 8/8/2000 | 6,100,740 | US |
| NMMS-0381.01/US | Utility - CON | Issued | CIRCUIT FOR SELECTIVELY ENABLING ONE AMONG A PLURALITY OF CIRCUIT ALTERNATIVES OF AN INTEGRATED CIRCUIT | 4/25/2000 | 09/558,956 | 2/25/2003 | 6,575,591 | US |
| NMMS-0381.02/US | Utility - DIV | Issued | METHOD FOR SELECTIVELY ENABLING ALTERNATIVE CIRCUITS | 7/6/2000 | 09/611,258 | 11/20/2001 | 6,320,440 | US |
| NMMS-0382.00/US | Utility - ORG | Issued | METHOD FOR VERIFYING ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY CELLS OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE AFTER PROGRAMMING | 5/30/1997 | 08/866,531 | 1/26/1999 | 5,864,503 | US |
| NMMS-0383.00/US | Utility - ORG | Issued | AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES | 12/29/1997 | 08/997,499 | 10/10/2000 | 6,130,165 | US |
| NMMS-0383.01/US | Utility - DIV | Issued | AUTOALIGNED ETCHING PROCESS FOR REALIZING WORD LINES IN MEMORY DEVICES INTEGRATED SEMICONDUCTOR SUBSTRATES | 3/17/2000 | 09/528,406 | 4/30/2002 | 6,380,582 | US |
| NMMS-0384.00/US | Utility - ORG | Issued | ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES | 12/29/1997 | 08/998,854 | 10/19/1999 | 5,969,977 | US |
| NMMS-0384.01/US | Utility - CON | Issued | MEMORY BLOCK FOR REALIZING SEMICONDUCTOR MEMORY DEVICES AND CORRESPONDING MANUFACTURING PROCESS | 6/7/1999 | 09/327,111 | 8/8/2000 | 6,101,124 | US |
| NMMS-0384.02/US | Utility - DIV | Issued | ELECTRONIC MEMORY DEVICE HAVING BIT LINES WITH BLOCK SELECTOR SWITCHES | 8/13/1999 | 09/387,103 | 9/4/2001 | 6,284,585 | US |
| NMMS-0385.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS | 7/21/1997 | 08/897,799 | 11/2/1999 | 5,976,933 | US |
| NMMS-0385.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING AN INTEGRATED CIRCUIT COMPRISING AN ARRAY OF MEMORY CELLS | 7/16/1999 | 09/356,080 | 3/5/2002 | 6,353,243 | US |
| NMMS-0386.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR INCREASING THE INTERNAL ADDRESS OF A MEMORY | 3/27/1998 | 09/049,858 | 9/5/2000 | 6,115,801 | US |
| NMMS-0387.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR CHECKING MULTILEVEL PROGRAMMING OF FLOATING-GATE NONVOLATILE MEMORY CELLS PARTICULARLY FLASH CELLS | 9/30/1997 | 08/941,882 | 3/9/1999 | 5,880,993 | US |
| NMMS-0388.00/US | Utility - ORG | Abandoned | METHOD OF PRODUCING MOSFET TRANSISTORS BY MEANS OF TILTED IMPLANTS | 4/20/1998 | 09/062,859 | 6/22/1999 | 5,915,185 | US |
| NMMS-0389.00/US | Utility - ORG | Issued | METHOD FOR SAVING DATA IN THE EVENT OF UNWANTED INTERRUPTIONS IN THE PROGRAMMING CYCLE OF A NONVOLATILE MEMORY AND A NONVOLATILE MEMORY | 4/29/1999 | 09/307,231 | 9/5/2000 | 6,115,313 | US |
| NMMS-0390.00/US | Utility - ORG | Issued | PROCESS FOR THE REPAIR OF FLOATING-GATE NON-VOLATILE MEMORIES DAMAGED BY PLASMA TREATMENT | 12/15/1997 | 08/990,328 | 3/30/1999 | 5,888,836 | US |
| NMMS-0391.00/US | Utility - ORG | Issued | VOLTAGE LEVEL SHIFTER DEVICE, PARTICULARLY FOR A NONVOLATILE MEMORY | 2/25/1998 | 09/030,604 | 9/28/1999 | 5,959,902 | US |
| NMMS-0392.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING A NATIVE MOS P-CHANNEL TRANSISTOR WITH A PROCESS FOR MANUFACTURING NON-VOLATILE MEMORIES | 8/26/1998 | 09/139,909 | 5/16/2000 | 6,063,663 | US |

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REEL: 029505 FRAME: 0051

Exhibit A - US Issued Patents

| Patent No. | Matter Type | Matter Status | Title | File Date | Serial No. | Issue Date | Patent No. | Country |
|------------------|----------------|---------------|---|------------|------------|------------|------------|---------|
| NMXXS-0394.00/US | Utility - ORG | Issued | METHOD OF MANUFACTURING AN EPROM MEMORY DEVICE HAVING MEMORY CELLS ORGANIZED IN A TABLECLOTH MATRIX | 8/27/1998 | 09/144,849 | 12/4/2001 | 6,326,266 | US |
| NMXXS-0395.00/US | Utility - ORG | Issued | SWITCHING MASTER SLAVE CIRCUIT | 1/19/1996 | 08/588,648 | 7/21/1998 | 5,783,958 | US |
| NMXXS-0396.00/US | Utility - ORG | Issued | MULTIPLE ACCESS MEMORY DEVICE | 12/31/1996 | 08/775,664 | 7/21/1998 | 5,784,331 | US |
| NMXXS-0397.00/US | Utility - CIP | Issued | LOW CURRENT CRYSTAL OSCILLATOR WITH FAST START-UP TIME | 5/3/1996 | 08/642,271 | 9/8/1998 | 5,805,027 | US |
| NMXXS-0398.00/US | Utility - ORG | Issued | EXTERNAL WRITE PULSE CONTROL METHOD AND STRUCTURE | 12/21/1996 | 08/771,642 | 6/9/1998 | 5,764,592 | US |
| NMXXS-0399.00/US | Utility - ORG | Issued | BURN-IN STRESS TEST MODE | 12/21/1996 | 08/771,645 | 3/14/2000 | 6,037,792 | US |
| NMXXS-0399.01/US | Utility - DIV | Issued | INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED | 1/27/2000 | 09/491,664 | 10/30/2001 | 6,310,485 | US |
| NMXXS-0399.02/US | Utility - DIV | Issued | INTEGRATED CIRCUIT DEVICE HAVING A BURN-IN MODE FOR WHICH ENTRY INTO AND EXIT FROM CAN BE CONTROLLED | 8/17/2001 | 09/931,820 | 2/11/2003 | 6,518,746 | US |
| NMXXS-0400.00/US | Utility - ORG | Issued | INPUT DELAY CONTROL | 12/23/1996 | 08/780,053 | 2/17/1998 | 5,719,445 | US |
| NMXXS-0401.00/US | Utility - ORG | Issued | SENSE AMPLIFIER CONTROL OF A MEMORY DEVICE | 4/25/1997 | 08/844,696 | 9/28/1999 | 5,959,910 | US |
| NMXXS-0402.00/US | Utility - CIP | Issued | CIRCUIT AND METHOD FOR SELECTING A SIGNAL | 11/27/1996 | 08/758,587 | 3/14/2000 | 6,037,799 | US |
| NMXXS-0403.00/RE | Utility - REIS | Issued | EDGE TRANSDUCER DETECTION CIRCUITRY FOR USE WITH TEST MODE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE | 5/9/2002 | 10/145,606 | 5/9/2000 | RE40,282 | US |
| NMXXS-0403.00/US | Utility - ORG | Issued | AN INTEGRATED DETECTION CIRCUITRY FOR USE WITH TEST MODE OPERATION OF AN INTEGRATED CIRCUIT MEMORY DEVICE | 12/21/1996 | 08/771,643 | 5/9/2000 | 6,059,450 | US |
| NMXXS-0404.00/US | Utility - CIP | Issued | INTEGRATED CIRCUIT THAT SUPPORTS AND METHOD FOR WAFER-LEVEL TESTING | 9/17/1996 | 08/710,357 | 9/15/1998 | 5,808,947 | US |
| NMXXS-0405.00/US | Utility - ORG | Issued | DEVICE FOR READING CELLS OF A MEMORY | 6/12/1997 | 08/873,502 | 7/13/1999 | 5,923,590 | US |
| NMXXS-0406.00/US | Utility - ORG | Issued | PARALLEL-ACCESS MEMORY AND METHOD | 5/9/1997 | 08/853,526 | 7/4/2000 | 6,085,280 | US |
| NMXXS-0407.00/US | Utility - ORG | Issued | ELECTRICALLY MODIFIABLE MULTILEVEL NON-VOLATILE MEMORY COMPRISING INTERNAL REFRESH MEANS | 10/24/1997 | 08/957,715 | 4/11/2000 | 6,049,497 | US |
| NMXXS-0408.00/US | Utility - ORG | Issued | READ CIRCUIT FOR NON-VOLATILE MEMORY WORKING WITH A LOW SUPPLY VOLTAGE | 9/22/1997 | 08/934,696 | 1/12/1999 | 5,859,798 | US |
| NMXXS-0409.00/US | Utility - ORG | Issued | DEVICE FOR THE PROTECTION OF STORED DATA | 8/21/1997 | 08/916,054 | 7/28/1998 | 5,787,040 | US |
| NMXXS-0410.00/US | Utility - ORG | Issued | CURRENT REFERENCE DEVICE IN INTEGRATED CIRCUIT FORM | 1/30/1997 | 08/791,383 | 5/11/1999 | 5,903,141 | US |
| NMXXS-0411.00/US | Utility - ORG | Issued | DEVICE FOR THE PROTECTION OF STORED DATA USING A TIME DELAY CIRCUIT | 8/21/1997 | 08/915,855 | 9/12/2000 | 6,119,210 | US |
| NMXXS-0412.00/US | Utility - ORG | Issued | MEMORY WITH IMPROVED READING TIME | 10/24/1997 | 08/957,666 | 2/9/1999 | 5,870,336 | US |
| NMXXS-0413.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR POWER-ON/POWER-OFF CHECKING OF AN INTEGRATED CIRCUIT | 12/18/1997 | 08/993,071 | 8/28/2001 | 6,281,723 | US |
| NMXXS-0414.00/US | Utility - ORG | Issued | OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR | 12/22/1997 | 08/995,667 | 11/14/2000 | 6,147,566 | US |
| NMXXS-0414.01/US | Utility - DIV | Issued | OSCILLATOR AND SWITCH-OVER CONTROL CIRCUIT FOR A HIGH-VOLTAGE GENERATOR | 5/25/2000 | 09/578,778 | 4/16/2002 | 6,373,311 | US |
| NMXXS-0415.00/US | Utility - ORG | Issued | ELECTRICALLY ERASABLE FLOATING-GATE MEMORY ORGANIZED IN WORDS | 3/24/1999 | 09/275,327 | 8/1/2000 | 6,097,651 | US |
| NMXXS-0416.00/US | Utility - ORG | Abandoned | METHOD AND DEVICE FOR THE PREDICTIVE READING OF A MEMORY | 12/16/1997 | 08/991,693 | 10/24/2000 | 6,138,220 | US |
| NMXXS-0417.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR THE INCREMENTAL READING OF A MEMORY | 12/16/1997 | 08/991,428 | 1/23/2001 | 6,178,490 | US |
| NMXXS-0418.00/US | Utility - ORG | Issued | MEMORY WITH READ PROTECTED ZONES | 12/19/1997 | 08/994,899 | 12/14/1999 | 6,002,619 | US |
| NMXXS-0419.00/US | Utility - ORG | Issued | A READ CIRCUIT FOR MEMORY ADAPTED TO THE MEASUREMENT OF LEAKAGE CURRENTS | 2/27/1998 | 09/031,748 | 3/30/1999 | 5,889,702 | US |
| NMXXS-0420.00/US | Utility - ORG | Issued | LOAD PUMP TYPE OF VOLTAGE GENERATOR CIRCUIT | 4/13/1998 | 09/059,088 | 10/19/1999 | 5,969,961 | US |
| NMXXS-0421.00/US | Utility - ORG | Issued | DIFFERENTIAL AMPLIFIER IN A MOS TRANSISTORS STRUCTURE | 11/6/1998 | 09/188,071 | 10/31/2000 | 6,140,876 | US |
| NMXXS-0422.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR THE FILTERING OF A PULSE SIGNAL | 5/29/1998 | 09/087,478 | 10/12/1999 | 5,966,034 | US |
| NMXXS-0423.00/US | Utility - ORG | Issued | RING OSCILLATOR USING CMOS TECHNOLOGY | 1/12/1998 | 09/005,722 | 10/3/2000 | 6,127,898 | US |
| NMXXS-0424.00/US | Utility - ORG | Issued | PAGE-WRITE INDICATOR FOR NON-VOLATILE MEMORY | 1/20/1998 | 09/009,088 | 9/28/1999 | 5,959,886 | US |
| NMXXS-0425.00/US | Utility - ORG | Issued | WORD ADDRESSABLE FLOATING-GATE MEMORY COMPRISING A REFERENCE VOLTAGE GENERATOR CIRCUIT FOR THE VERIFICATION OF THE CONTENTS OF A WORD | 3/6/1998 | 09/035,654 | 9/14/1999 | 5,953,253 | US |

PATENT

REEL: 029505 FRAME: 0052

Exhibit A - US Issued Patents

| Pub. No. | Pub. No. | Pub. No. | Title | Filed | Serial | Issued | Patent No. | Country |
|-----------------|-----------------|-----------|---|------------|------------|------------|------------|---------|
| NMMS-0426.00/US | Utility - ORG | Issued | ERASABLE AND METHOD FOR THE ERASURE OF A NON-VOLATILE AND ELECTRICALLY PROGRAMMABLE MEMORY | 11/26/1997 | 08/980,195 | 1/4/2000 | 6,011,724 | US |
| NMMS-0427.00/US | Utility - ORG | Issued | DEVICE FOR PROTECTION AFTER A PAGE-WRITE OPERATION IN AN ELECTRICALLY PROGRAMMABLE MEMORY | 11/24/1997 | 08/970,445 | 1/19/1999 | 5,862,075 | US |
| NMMS-0428.00/US | Utility - ORG | Issued | CIRCUIT FOR THE DETECTION OF CHANGES OF ADDRESS | 1/27/1998 | 09/013,966 | 8/15/2000 | 6,104,644 | US |
| NMMS-0429.00/US | Utility - ORG | Abandoned | SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT | 4/8/1998 | 09/056,921 | 3/20/2001 | 6,205,512 | US |
| NMMS-0429.01/US | Utility - DIV | Abandoned | SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT | 12/21/2000 | 09/746,473 | 8/13/2002 | 6,434,056 | US |
| NMMS-0430.02/US | Utility - DIV | Abandoned | SET OF TWO MEMORIES ON THE SAME MONOLITHIC INTEGRATED CIRCUIT | 12/21/2000 | 09/746,472 | 8/21/2001 | 6,279,068 | US |
| NMMS-0430.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR THE PROGRAMMING OF A MEMORY | 1/22/1998 | 09/012,938 | 11/23/1999 | 5,991,199 | US |
| NMMS-0430.02/US | Utility - NSPCT | Issued | METHOD FOR PROGRAMMING AN EPROM-FLASH TYPE MEMORY | 1/22/1998 | 09/355,064 | 10/31/2000 | 6,141,254 | US |
| NMMS-0431.00/US | Utility - CON | Issued | VARIABLE FREQUENCY CHARGE PUMP | 7/11/1998 | 09/118,953 | 5/9/2000 | 6,060,932 | US |
| NMMS-0432.02/US | Utility - CON | Issued | PROCESS OF FINAL PASSIVATION OF AN INTEGRATED CIRCUIT DEVICE | 12/18/2002 | 10/323,961 | 5/3/2005 | 6,888,225 | US |
| NMMS-0433.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH REDUCED POWER DISSIPATION | 4/1/1998 | 09/053,720 | 5/9/2000 | 6,061,286 | US |
| NMMS-0434.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR READING A NON-ERASABLE MEMORY CELL | 3/16/1998 | 09/039,588 | 6/13/2000 | 6,075,718 | US |
| NMMS-0435.00/US | Utility - ORG | Issued | SEMICONDUCTOR INTEGRATED CIRCUIT | 10/6/1999 | 09/093,382 | 4/3/2001 | 6,212,128 | US |
| NMMS-0436.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR GENERATING A GATE VOLTAGE IN NON-VOLATILE MEMORY DEVICES | 8/27/1998 | 09/144,250 | 1/18/2000 | 6,016,271 | US |
| NMMS-0437.00/US | Utility - ORG | Issued | PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE | 8/6/1998 | 09/130,720 | 2/27/2001 | 6,194,270 | US |
| NMMS-0437.01/US | Utility - DIV | Issued | PROCESS FOR THE MANUFACTURING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY DEVICE | 2/1/2001 | 09/776,405 | 8/20/2002 | 6,437,395 | US |
| NMMS-0438.00/US | Utility - ORG | Issued | METHOD FOR FINAL PASSIVATION OF INTEGRATED CIRCUIT | 4/12/1998 | 09/059,740 | 2/13/2001 | 6,187,683 | US |
| NMMS-0439.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR ANALOG PROGRAMMING OF NON-VOLATILE MEMORY CELLS | 5/11/1998 | 09/076,013 | 2/27/2001 | 6,195,283 | US |
| NMMS-0440.00/US | Utility - ORG | Issued | MEMORY DEVICE GENERATOR FOR GENERATING MEMORY DEVICES WITH REDUNDANCY | 10/19/1998 | 09/175,220 | 7/22/2003 | 6,598,190 | US |
| NMMS-0441.00/US | Utility - ORG | Issued | METHOD FOR FORMING NON VOLATILE MEMORY STRUCTURES ON A SEMICONDUCTOR SUBSTRATE | 12/10/1999 | 09/459,754 | 4/23/2002 | 6,376,306 | US |
| NMMS-0442.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR READING A NON-VOLATILE MEMORY | 7/14/1999 | 09/353,756 | 2/27/2001 | 6,195,286 | US |
| NMMS-0443.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR ANALOG PROGRAMMING OF FLASH EEPROM MEMORY CELLS WITH AUTOVERBY | 9/28/1998 | 09/152,639 | 6/27/2000 | 6,081,448 | US |
| NMMS-0444.00/US | Utility - ORG | Abandoned | METHOD FOR LOCALIZING POINT DEFECTS CAUSING LEAKAGE CURRENTS IN A NON-VOLATILE MEMORY DEVICE | 5/13/1999 | 09/311,258 | 4/9/2002 | 6,369,406 | US |
| NMMS-0445.00/US | Utility - ORG | Issued | DATA READ CIRCUIT FOR NON VOLATILE MEMORY CELLS | 10/6/1999 | 09/413,383 | 12/11/2001 | 6,330,188 | US |
| NMMS-0446.00/US | Utility - ORG | Issued | ROW DECODER FOR A FLASH-EEPROM MEMORY DEVICE WITH THE POSSIBILITY OF SELECTIVE ERASING OF A SUB-GROUP OF ROWS OF A SECTOR | 11/25/1998 | 09/200,002 | 9/19/2000 | 6,122,200 | US |
| NMMS-0447.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD OF READING CELLS OF AN ANALOG MEMORY ARRAY, IN PARTICULAR OF THE FLASH TYPE | 7/22/1998 | 09/124,024 | 10/26/1999 | 5,973,959 | US |
| NMMS-0448.00/US | Utility - ORG | Issued | DECODER FOR MEMORIES HAVING OPTIMIZED CONFIGURATION | 11/20/2000 | 09/716,747 | 3/26/2002 | 6,362,658 | US |
| NMMS-0449.00/US | Utility - ORG | Issued | METHOD FOR PARALLEL PROGRAMMING OF NONVOLATILE MEMORY DEVICES, IN PARTICULAR FLASH MEMORIES AND EEPROMS | 10/27/1998 | 09/181,230 | 5/30/2000 | 6,069,822 | US |
| NMMS-0450.00/US | Utility - ORG | Issued | METHOD OF MEASURING THE THICKNESS OF A LAYER OF SILICON DAMAGED BY PLASMA ETCHING | 6/29/1999 | 09/343,207 | 5/15/2001 | 6,233,046 | US |
| NMMS-0451.00/US | Utility - ORG | Issued | SECTORED SEMICONDUCTOR MEMORY DEVICE WITH CONFIGURABLE MEMORY SECTOR ADDRESSES | 9/23/1998 | 09/159,322 | 6/4/2002 | 6,401,164 | US |
| NMMS-0452.00/US | Utility - ORG | Issued | STACKED CHARGE PUMP CIRCUIT | 8/27/1997 | 08/927,391 | 7/20/1999 | 5,926,059 | US |
| NMMS-0453.00/US | Utility - ORG | Issued | CMOS TWIN-TUB NEGATIVE VOLTAGE SWITCHING ARCHITECTURE | 8/27/1997 | 08/921,930 | 11/30/1999 | 5,994,948 | US |
| NMMS-0454.00/US | Utility - ORG | Abandoned | DETERMINATION OF THE THICKNESS OF A DENUDED ZONE IN A SILICON WAFER | 7/1/1998 | 09/108,439 | 3/6/2001 | 6,197,606 | US |

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Exhibit A - US Issued Patents

| Pub. No. | Market Type | Market Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|---|------------|------------|------------|------------|---------|
| NMMS-0455.00/US | Utility - ORG | Issued | HIGH VOLTAGE DRIVER CIRCUIT FOR A DECODING CIRCUIT IN MULTILEVEL NON-VOLATILE MEMORY DEVICES | 12/31/1998 | 09/224,330 | 2/22/2000 | 6,028,793 | US |
| NMMS-0456.00/US | Utility - ORG | Issued | MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELL DEVICES | 5/28/1999 | 09/321,961 | 6/5/2001 | 6,242,971 | US |
| NMMS-0457.00/US | Utility - ORG | Issued | CONTROLLED HOT-ELECTRON WAITING METHOD FOR NON-VOLATILE MEMORY CELLS | 10/8/1998 | 09/169,339 | 1/9/2001 | 6,172,908 | US |
| NMMS-0458.00/US | Utility - ORG | Issued | SELF-TEST AND CORRECTION OF LOSS OF CHARGE ERRORS IN A FLASH MEMORY, ERASABLE AND PROGRAMMABLE BY SECTORS THEREOF | 12/16/1998 | 09/212,896 | 8/14/2001 | 6,275,960 | US |
| NMMS-0459.00/US | Utility - ORG | Issued | COMPENSATED VOLTAGE REGULATOR | 9/30/1998 | 09/163,755 | 11/9/1999 | 5,982,677 | US |
| NMMS-0460.00/US | Utility - ORG | Issued | METHOD FOR MULTILEVEL PROGRAMMING OF A NONVOLATILE MEMORY, AND A MULTILEVEL NONVOLATILE MEMORY | 11/3/1998 | 09/185,906 | 1/4/2000 | 6,011,715 | US |
| NMMS-0461.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR GENERATING AN ATD SIGNAL TO REGULATE THE ACCESS TO A NON-VOLATILE MEMORY | 11/4/1998 | 09/186,497 | 6/13/2000 | 6,075,750 | US |
| NMMS-0462.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR REGULATING THE LENGTH OF AN ATD PULSE SIGNAL | 11/4/1998 | 09/186,496 | 1/2/2001 | 6,169,423 | US |
| NMMS-0463.00/US | Utility - ORG | Issued | BOOSTING CIRCUIT PARTICULARLY FOR A MEMORY DEVICE | 11/5/1998 | 09/186,758 | 11/7/2000 | 6,144,589 | US |
| NMMS-0464.00/US | Utility - ORG | Issued | IMPROVED OUTPUT CIRCUIT FOR INTEGRATED CIRCUITS | 10/13/1998 | 09/170,788 | 11/28/2000 | 6,153,914 | US |
| NMMS-0465.00/US | Utility - ORG | Issued | MEMORY CELL VOLTAGE REGULATOR WITH TEMPERATURE CORRELATED VOLTAGE GENERATOR CIRCUIT | 11/4/1998 | 09/186,498 | 2/6/2001 | 6,184,670 | US |
| NMMS-0467.00/US | Utility - ORG | Issued | HIGH-VOLTAGE PUMP ARCHITECTURE FOR INTEGRATED ELECTRONIC DEVICES | 1/29/1999 | 09/239,908 | 8/14/2001 | 6,275,099 | US |
| NMMS-0468.00/US | Utility - ORG | Issued | CIRCUIT FOR DISCHARGING A NEGATIVE POTENTIAL NODE TO GROUND, INCLUDING CONTROL OF THE DISCHARGE CURRENT | 3/24/1999 | 09/275,200 | 6/19/2001 | 6,249,172 | US |
| NMMS-0469.00/US | Utility - ORG | Issued | SWITCHING CIRCUIT | 3/24/1999 | 09/275,694 | 5/16/2000 | 6,064,598 | US |
| NMMS-0470.00/US | Utility - ORG | Issued | DATA PROTECTION METHOD FOR A SEMICONDUCTOR MEMORY AND CORRESPONDING PROTECTED MEMORY DEVICE | 12/29/1998 | 09/220,127 | 9/4/2001 | 6,286,086 | US |
| NMMS-0471.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORY IN PARTICULAR | 11/20/1998 | 09/196,204 | 8/8/2000 | 6,101,118 | US |
| NMMS-0472.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR SINGLE FEED VOLTAGE MEMORY CIRCUITS, AND FLASH TYPE MEMORIES IN PARTICULAR | 6/26/2000 | 09/602,669 | 9/4/2001 | 6,286,614 | US |
| NMMS-0473.00/US | Utility - ORG | Issued | ELECTRONIC CIRCUIT FOR GENERATING A STABLE VOLTAGE SIGNAL FOR POLARIZING DURING A READING STEP UPROM MEMORY CELLS OPERATING AT LOW FEED VOLTAGE | 12/21/1998 | 09/218,796 | 3/20/2001 | 6,204,722 | US |
| NMMS-0474.00/US | Utility - ORG | Issued | ROW DECODER CIRCUIT FOR AN ELECTRONIC MEMORY DEVICE, PARTICULARLY FOR LOW VOLTAGE APPLICATIONS | 12/29/1998 | 09/222,022 | 5/30/2000 | 6,069,837 | US |
| NMMS-0475.00/US | Utility - ORG | Issued | METHOD AND A RELATED CIRCUIT FOR ADJUSTING THE DURATION OF A SYNCHRONIZATION SIGNAL ATD FOR TIMING THE ACCESS TO A NON-VOLATILE MEMORY | 12/29/1998 | 09/222,070 | 5/22/2001 | 6,237,104 | US |
| NMMS-0476.00/US | Utility - ORG | Issued | DRIVING CIRCUIT WITH THREE OUTPUT LEVELS, ONE OUTPUT LEVEL BEING A BOOSTED LEVEL | 1/19/1999 | 09/234,016 | 12/5/2000 | 6,157,225 | US |
| NMMS-0476.00/US | Utility - ORG | Abandoned | MEMORY CELL INTEGRATED STRUCTURE AND CORRESPONDING BIASING DEVICE | 4/21/1999 | 09/295,667 | 11/21/2000 | 6,151,251 | US |
| NMMS-0476.00/US | Utility - DIV | Abandoned | MEMORY CELL INTEGRATED STRUCTURE WITH CORRESPONDING BIASING DEVICE | 9/29/2000 | 09/675,985 | 10/16/2001 | 6,304,490 | US |
| NMMS-0477.00/US | Utility - ORG | Issued | SWITCHING CIRCUIT HAVING AN OUTPUT VOLTAGE VARYING BETWEEN A REFERENCE VOLTAGE AND A NEGATIVE VOLTAGE | 3/24/1999 | 09/275,255 | 2/29/2000 | 6,031,761 | US |
| NMMS-0478.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TRIMMING THE INTERNAL TIMING CONDITIONS OF A SEMICONDUCTOR MEMORY DEVICE | 2/26/1998 | 09/032,272 | 12/28/1999 | 6,009,041 | US |
| NMMS-0479.00/US | Utility - ORG | Issued | STRUCTURE AND METHOD FOR EVALUATING AN INTEGRATED ELECTRONIC DEVICE | 12/9/1998 | 09/209,049 | 11/6/2001 | 6,313,480 | US |
| NMMS-0480.00/US | Utility - ORG | Issued | LOW CONSUMPTION TTL-CMOS INPUT BUFFER STAGE | 12/30/1998 | 09/231,130 | 10/23/2001 | 6,307,396 | US |

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REEL: 029505 FRAME: 0054

Exhibit A - US Issued Patents

| Patent No. | Material | Material Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|-----------------|-----------------|--|------------|------------|------------|------------|---------|
| NMMS-0481.00/US | Utility - NSPCT | Issued | MONOLITHICALLY INTEGRATED SELECTOR FOR ELECTRICALLY PROGRAMMABLE MEMORY CELLS DEVICES | 6/30/1999 | 09/674,395 | 9/11/2001 | 6,288,594 | US |
| NMMS-0482.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY CAPABLE OF AUTONOMOUSLY EXECUTING A PROGRAM | 7/8/1999 | 09/349,702 | 7/1/2003 | 6,587,914 | US |
| NMMS-0483.00/US | Utility - ORG | Issued | OPERATING VOLTAGE SELECTION CIRCUIT FOR NON-VOLATILE SEMICONDUCTOR MEMORIES | 1/13/1999 | 09/229,474 | 8/8/2000 | 6,103,127 | US |
| NMMS-0484.00/US | Utility - ORG | Issued | METHOD FOR CONTROLLED ERASING MEMORY DEVICES, IN PARTICULAR ANALOG AND MULTI-LEVEL FLASH-EEPROM DEVICES | 1/22/1999 | 09/234,942 | 7/18/2000 | 6,091,642 | US |
| NMMS-0485.00/US | Utility - ORG | Issued | ESD PROTECTION NETWORK FOR CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR | 12/30/1998 | 09/223,621 | 7/24/2001 | 6,266,222 | US |
| NMMS-0486.00/US | Utility - ORG | Issued | METHOD AND A CIRCUIT FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR | 12/30/1998 | 09/231,129 | 6/5/2001 | 6,242,793 | US |
| NMMS-0486.01/US | Utility - DIV | Issued | METHOD FOR IMPROVING THE EFFECTIVENESS OF ESD PROTECTION IN CIRCUIT STRUCTURES FORMED IN A SEMICONDUCTOR SUBSTRATE | 4/17/2001 | 09/837,137 | 4/16/2002 | 6,372,597 | US |
| NMMS-0487.00/US | Utility - ORG | Issued | HIGH STORAGE CAPACITY NON-VOLATILE MEMORY | 5/26/1999 | 09/320,315 | 11/14/2000 | 6,147,902 | US |
| NMMS-0488.00/US | Utility - ORG | Issued | PROCESS FOR FABRICATING A SEMICONDUCTOR NON-VOLATILE MEMORY DEVICE WITH SHALLOW TRENCH ISOLATION (STI) | 6/18/1999 | 09/336,089 | 4/17/2001 | 6,218,265 | US |
| NMMS-0489.00/US | Utility - ORG | Issued | CIRCUIT DEVICE AND CORRESPONDING METHOD FOR PROGRAMMING A NONVOLATILE MEMORY CELL HAVING A SINGLE VOLTAGE SUPPLY | 5/28/1999 | 09/322,644 | 8/29/2000 | 6,111,791 | US |
| NMMS-0490.00/US | Utility - ORG | Issued | ELECTRONIC COUNTER FOR A NON-VOLATILE MEMORY DEVICE INTEGRATED ON A SEMICONDUCTOR | 3/4/1999 | 09/262,500 | 3/27/2001 | 6,208,705 | US |
| NMMS-0491.00/US | Utility - ORG | Issued | EDGE TRANSITION DETECTION CONTROL OF A MEMORY DEVICE | 12/30/1997 | 08/000,547 | 11/30/1999 | 5,996,444 | US |
| NMMS-0492.01/US | Utility - CON | Abandoned | VSS SWITCHING SCHEME FOR BATTERY BACKED-UP SEMICONDUCTOR DEVICES | 10/29/1999 | 09/429,964 | 8/22/2000 | 6,107,865 | US |
| NMMS-0493.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR READING A MEMORY CELL | 5/29/1998 | 09/087,399 | 11/30/1999 | 5,996,421 | US |
| NMMS-0494.00/US | Utility - ORG | Issued | READ CIRCUIT FOR NON VOLATILE MEMORIES | 10/29/1998 | 09/182,843 | 8/1/2000 | 6,097,633 | US |
| NMMS-0495.00/US | Utility - ORG | Issued | IN-SITU DEPOSITION AND DOPING PROCESS FOR POLYCRYSTALLINE SILICON LAYERS AND THE RESULTING DEVICE | 11/13/1998 | 09/191,743 | 3/15/2005 | 6,867,113 | US |
| NMMS-0496.00/US | Utility - ORG | Issued | TEMPERATURE-STABLE CURRENT GENERATION | 2/5/1999 | 09/246,029 | 10/17/2000 | 6,133,718 | US |
| NMMS-0497.00/US | Utility - ORG | Issued | BITLINE BIAS CIRCUIT FOR NON-VOLATILE MEMORY DEVICES | 2/23/1999 | 09/256,648 | 4/11/2000 | 6,049,491 | US |
| NMMS-0498.00/US | Utility - ORG | Issued | SENSE AMPLIFIER FOR NON-VOLATILE MEMORY DEVICES | 2/23/1999 | 09/256,603 | 7/25/2000 | 6,094,394 | US |
| NMMS-0499.00/US | Utility - ORG | Issued | UPROM MEMORY CELLS FOR NON-VOLATILE MEMORY DEVICES INTEGRATED ON SEMICONDUCTORS | 3/25/1999 | 09/276,263 | 8/7/2001 | 6,271,571 | US |
| NMMS-0500.00/US | Utility - ORG | Issued | SENSE AMPLIFIER FOR LOW VOLTAGE MEMORIES | 2/12/1999 | 09/249,834 | 10/15/2002 | 6,466,059 | US |
| NMMS-0501.00/US | Utility - ORG | Issued | LOW CONSUMPTION BOOSTED VOLTAGE DRIVING CIRCUIT | 2/26/1999 | 09/257,682 | 10/10/2000 | 6,130,844 | US |
| NMMS-0502.00/US | Utility - ORG | Issued | VOLTAGE BOOSTING CIRCUIT FOR GENERATING BOOSTED VOLTAGE PHASES | 2/26/1999 | 09/258,224 | 5/16/2000 | 6,064,594 | US |
| NMMS-0503.00/US | Utility - ORG | Issued | VOLTAGE PHASE GENERATOR WITH INCREASED DRIVING CAPACITY | 2/26/1999 | 09/257,684 | 3/6/2001 | 6,198,672 | US |
| NMMS-0504.00/US | Utility - ORG | Issued | PIPELINED NON-BLOCKING LEVEL TWO CACHE SYSTEM WITH INHERENT TRANSACCION COLLISION-AVOIDANCE | 12/4/1998 | 09/205,598 | 2/11/2003 | 6,519,682 | US |
| NMMS-0505.00/US | Utility - ORG | Issued | ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY HAVING A PROTECTABLE ZONE AND AN ELECTRONIC SYSTEM INCLUDING THE MEMORY | 10/23/1998 | 09/177,899 | 3/7/2000 | 6,034,889 | US |
| NMMS-0506.00/US | Utility - ORG | Issued | METHOD FOR WRITING IN AN ELECTRICALLY MODIFIABLE NON-VOLATILE MEMORY | 10/27/1998 | 09/179,621 | 3/21/2000 | 6,040,994 | US |
| NMMS-0507.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR THE GENERATION OF PROGRAMMING AND ERASURE VOLTAGE IN A NON-VOLATILE MEMORY | 9/18/1998 | 09/156,945 | 11/30/1999 | 5,995,416 | US |
| NMMS-0508.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORIES PROGRAMMABLE BY "HOT CARRIER" TUNNEL EFFECT AND ERASABLE BY TUNNEL EFFECT | 10/15/1998 | 09/173,136 | 10/3/2000 | 6,128,222 | US |
| NMMS-0509.00/US | Utility - ORG | Issued | NON-VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY | 11/25/1998 | 09/199,671 | 12/7/1999 | 5,999,447 | US |
| NMMS-0510.00/US | Utility - ORG | Issued | DETECTOR OF RADIO FREQUENCY SIGNALS FOR CONTACTLESS CHIP CARDS | 9/18/1998 | 09/157,060 | 11/28/2000 | 6,152,373 | US |

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REEL: 029505 FRAME: 0055

Exhibit A - US Issued Patents

| Pub. No. | Pub. No. | Pub. No. | Title | Pub. Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|-----------|--|------------|------------|------------|------------|---------|
| NMMS-0511.00/US | Utility - ORG | Issued | CIRCUIT FOR THE GENERATION OF VOLTAGE FOR THE PROGRAMMING OR ERASURE OF A MEMORY THAT USES FLOATING-GATE TRANSISTORS | 10/27/1998 | 09/179,635 | 11/2/1999 | 5,978,268 | US |
| NMMS-0512.00/US | Utility - ORG | Issued | DEVICE FOR DEMODULATING A BINARY PHASE-SHIFT KEYSIGNAL | 1/20/1999 | 09/234,194 | 10/31/2000 | 6,140,869 | US |
| NMMS-0513.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE AND METHOD FOR THE PROGRAMMING OF THE SAME | 11/18/1998 | 09/195,276 | 7/18/2000 | 6,091,641 | US |
| NMMS-0514.00/US | Utility - ORG | Abandoned | DEVICE AND METHOD FOR THE READING OF EEPROM CELLS | 4/27/1999 | 09/300,527 | 4/17/2001 | 6,219,277 | US |
| NMMS-0515.00/US | Utility - ORG | Issued | LINE DECODER FOR A LOW SUPPLY VOLTAGE MEMORY DEVICE | 6/1/1999 | 09/324,087 | 8/79/2000 | 6,111,809 | US |
| NMMS-0516.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR READING NONVOLATILE MEMORY CELLS | 5/28/1999 | 09/322,460 | 1/30/2001 | 6,181,602 | US |
| NMMS-0517.00/US | Utility - ORG | Issued | CIRCUIT FOR PROVIDING A READING PHASE AFTER POWER-ON-RESET | 4/20/1999 | 09/295,263 | 12/5/2000 | 6,157,579 | US |
| NMMS-0519.00/US | Utility - ORG | Issued | SWITCHING CIRCUIT WITH AN OUTPUT VOLTAGE CHANGING AMONG FOUR POSSIBLE VALUES | 3/24/1999 | 09/275,691 | 8/1/2000 | 6,097,213 | US |
| NMMS-0520.00/US | Utility - ORG | Issued | PROTECTION FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR | 6/25/1999 | 09/344,426 | 8/21/2001 | 6,278,159 | US |
| NMMS-0520.01/US | Utility - DIV | Issued | PROTECTION FOR THE MANUFACTURE OF INTEGRATED DEVICES WITH GATE OXIDE PROTECTION FROM MANUFACTURING PROCESS DAMAGE, AND PROTECTION STRUCTURE THEREFOR | 6/25/2001 | 09/891,438 | 4/22/2003 | 6,551,892 | US |
| NMMS-0521.00/US | Utility - ORG | Issued | ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD | 7/30/1999 | 09/364,766 | 4/10/2001 | 6,215,688 | US |
| NMMS-0521.01/US | Utility - DIV | Issued | ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD | 2/9/2001 | 09/779,956 | 2/8/2005 | 6,857,596 | US |
| NMMS-0521.02/US | Utility - DIV | Issued | ELECTRONIC MEMORY CIRCUIT AND RELATED MANUFACTURING METHOD | 1/12/2005 | 11/033,776 | 10/13/2009 | 7,501,590 | US |
| NMMS-0522.00/US | Utility - ORG | Issued | METHOD FOR READING A MULTIPLE-LEVEL MEMORY CELL | 3/25/1999 | 09/276,214 | 7/4/2000 | 6,084,797 | US |
| NMMS-0523.01/US | Utility - CON | Issued | CIRCUIT STRUCTURE FOR PROVIDING A HIERARCHICAL DECODING IN SEMICONDUCTOR MEMORY DEVICES | 6/27/2001 | 09/894,975 | 2/4/2003 | 6,515,911 | US |
| NMMS-0524.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS | 7/22/1999 | 09/359,923 | 6/26/2001 | 6,251,728 | US |
| NMMS-0524.01/US | Utility - DIV | Issued | METHOD FOR MANUFACTURING ELECTRONIC DEVICES HAVING HV TRANSISTORS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS | 5/18/2001 | 09/861,404 | 7/16/2002 | 6,420,789 | US |
| NMMS-0525.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING AN ELECTRONIC DEVICE INCLUDING MOS TRANSISTORS WITH SALICIDED JUNCTIONS AND NON-SALICIDED RESISTORS | 7/21/1999 | 09/358,075 | 10/9/2001 | 6,300,181 | US |
| NMMS-0526.00/US | Utility - ORG | Issued | METHOD FOR THE INTEGRATION OF RESISTORS AND ESD SELF-PROTECTED TRANSISTORS IN AN INTEGRATED DEVICE WITH A MEMORY MATRIX MANUFACTURED BY MEANS OF A PROCESS FEATURING SELF-ALIGNED SOURCE (SAS) FORMATION AND JUNCTION SALICIDATION | 12/15/1999 | 09/464,066 | 10/8/2002 | 6,461,922 | US |
| NMMS-0527.01/US | Utility - DIV | Issued | METHOD FOR ENHANCING SELECTIVITY BETWEEN A FILM OF ALIGHT-SENSITIVE MATERIAL AND A LAYER TO BE ETCHED IN ELECTRONIC SEMICONDUCTOR DEVICE FABRICATION PROCESSES | 4/17/2001 | 09/836,937 | 12/17/2002 | 6,495,455 | US |
| NMMS-0528.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING SELECTION TRANSISTORS FOR NONVOLATILE SERIAL-FLASH, EPROM, EEPROM AND FLASH-EEPROM MEMORIES IN STANDARD OR AMG CONFIGURATION | 6/11/1999 | 09/330,540 | 7/3/2001 | 6,255,163 | US |
| NMMS-0529.00/US | Utility - ORG | Issued | METHOD OF MAKING HIGH-VOLTAGE HV TRANSISTORS WITH DRAIN EXTENSION IN A CMOS PROCESS OF THE DUAL GATE TYPE WITH SILICIDE | 10/1/1999 | 09/411,134 | 9/4/2001 | 6,284,607 | US |
| NMMS-0530.00/US | Utility - ORG | Issued | METHOD FOR FAST PROGRAMMING FLOATING GATE MEMORIES BY TUNNEL EFFECT | 6/25/1999 | 09/344,425 | 1/9/2001 | 6,172,913 | US |
| NMMS-0531.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING OF A NON VOLATILE MEMORY WITH REDUCED RESISTANCE OF THE COMMON SOURCE LINES | 6/21/1999 | 09/337,051 | 1/30/2001 | 6,180,460 | US |
| NMMS-0532.00/US | Utility - ORG | Issued | SIMPLIFIED PROCESS FOR DEFINING THE TUNNEL AREA IN NON-ALIGNED, NON-VOLATILE SEMICONDUCTOR MEMORY CELLS | 10/14/1999 | 09/419,403 | 9/3/2002 | 6,444,526 | US |
| NMMS-0533.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE WITH ROW REDUNDANCY | 5/12/2000 | 09/570,332 | 10/9/2001 | 6,301,152 | US |
| NMMS-0534.00/US | Utility - ORG | Issued | METHOD FOR FORMING CONTACTLESS MOS TRANSISTORS AND RESULTING DEVICES, ESPECIALLY FOR USE IN NON-VOLATILE MEMORY ARRAYS | 12/28/1999 | 09/473,368 | 6/26/2001 | 6,251,736 | US |

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Exhibit A - US Issued Patents

| MTI-DefNo | MasterType | MasterStatus | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|-----------------|---------------|--------------|---|------------|------------|------------|-----------|---------|
| NMXX-0535.00/US | Utility - ORG | Abandoned | PROCESS FOR THE DEFINITION OF OPENINGS IN A DIELECTRIC LAYER | 9/28/1999 | 09/406,503 | 11/6/2001 | 6,313,040 | US |
| NMXX-0536.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS | 9/9/1999 | 09/392,937 | 8/28/2001 | 6,281,077 | US |
| NMXX-0536.01/US | Utility - DIV | Issued | METHOD FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NON-VOLATILE MEMORY CELLS AND LV TRANSISTORS WITH SALICIDED JUNCTIONS | 4/16/2001 | 09/836,590 | 5/28/2002 | 6,396,101 | US |
| NMXX-0537.00/US | Utility - ORG | Issued | SELECTIVE SALICIDATION PROCESS FOR ELECTRONIC DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE | 12/28/1999 | 09/473,567 | 8/5/2003 | 6,602,774 | US |
| NMXX-0538.00/US | Utility - ORG | Issued | METHOD FOR CORRECTION OF ERRORS IN A BINARY WORD STORED IN MULTILEVEL MEMORY CELLS, NOT REQUIRING ADDITIONAL CELLS | 2/24/2000 | 09/513,286 | 3/4/2003 | 6,590,058 | US |
| NMXX-0539.00/US | Utility - ORG | Issued | NONVOLATILE MULTILEVEL MEMORY AND READING METHOD THEREFORE | 2/9/2000 | 09/501,131 | 9/24/2002 | 6,456,527 | US |
| NMXX-0540.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TESTING MEMORY CELLS IN A MULTILEVEL MEMORY DEVICE | 10/7/1999 | 09/415,024 | 10/9/2001 | 6,301,157 | US |
| NMXX-0541.00/US | Utility - ORG | Issued | DEVICE FOR READING NON-VOLATILE MEMORY CELLS, IN PARTICULAR ANALOG FLASH MEMORY CELLS | 10/19/1999 | 09/421,616 | 11/27/2001 | 6,323,799 | US |
| NMXX-0542.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH AUTOMATIC GENERATION OF PROGRAMMING VOLTAGE | 11/12/1999 | 09/438,232 | 10/15/2002 | 6,466,481 | US |
| NMXX-0543.00/US | Utility - ORG | Issued | CIRCUIT FOR PARALLEL PROGRAMMING NONVOLATILE MEMORY CELLS, WITH ADJUSTABLE PROGRAMMING SPEED | 11/23/1999 | 09/447,531 | 12/19/2000 | 6,163,483 | US |
| NMXX-0544.00/US | Utility - ORG | Issued | CIRCUIT FOR HIGH-PRECISION ANALOG READING OF NONVOLATILE MEMORY CELLS, IN PARTICULAR ANALOG OR MULTILEVEL FLASH OR EEPROM MEMORY CELLS | 11/12/1999 | 09/438,823 | 10/3/2000 | 6,128,228 | US |
| NMXX-0545.00/US | Utility - ORG | Issued | PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY | 11/24/1999 | 09/449,044 | 6/25/2002 | 6,410,387 | US |
| NMXX-0545.01/US | Utility - DIV | Issued | PROCESS FOR INTEGRATING IN A SAME CHIP A NON-VOLATILE MEMORY AND A HIGH-PERFORMANCE LOGIC CIRCUITRY | 5/29/2002 | 10/158,424 | 3/30/2004 | 6,713,347 | US |
| NMXX-0546.00/US | Utility - ORG | Issued | METHOD FOR MAINTAINING THE MEMORY CONTENT OF NON-VOLATILE MEMORY CELLS | 9/15/1999 | 09/397,387 | 1/2/2001 | 6,169,691 | US |
| NMXX-0547.00/US | Utility - ORG | Issued | METHOD OF FABRICATION OF A NO-FIELD MOS TRANSISTOR | 4/5/2000 | 09/543,400 | 2/26/2002 | 6,350,637 | US |
| NMXX-0548.00/US | Utility - CIP | Issued | DEVICE FOR READING ANALOG NONVOLATILE MEMORY CELLS, IN PARTICULAR FLASH CELLS | 10/22/1999 | 09/425,446 | 2/27/2001 | 6,195,289 | US |
| NMXX-0549.00/US | Utility - ORG | Issued | CAPACITIVE BOOSTING CIRCUIT FOR THE REGULATION OF THE WORD LINE READING VOLTAGE IN NON-VOLATILE MEMORIES | 1/19/2000 | 09/491,476 | 7/10/2001 | 6,259,635 | US |
| NMXX-0550.00/US | Utility - ORG | Issued | CAPACITIVE COMPENSATION CIRCUIT FOR THE REGULATION OF THE WORD LINE READING VOLTAGE IN NON-VOLATILE MEMORIES | 1/19/2000 | 09/491,475 | 7/10/2001 | 6,259,632 | US |
| NMXX-0551.00/US | Utility - ORG | Issued | CHIP OUTLINE BAND (COB) STRUCTURE FOR INTEGRATED CIRCUITS | 1/14/2000 | 09/483,656 | 10/8/2002 | 6,462,400 | US |
| NMXX-0552.00/US | Utility - ORG | Issued | IMPROVED FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD | 11/18/1999 | 09/442,834 | 5/14/2002 | 6,387,763 | US |
| NMXX-0552.01/US | Utility - DIV | Issued | FIELD-EFFECT TRANSISTOR AND CORRESPONDING MANUFACTURING METHOD | 3/4/2002 | 10/090,978 | 5/18/2004 | 6,737,715 | US |
| NMXX-0553.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR DRIVING PLURAL LOADS BASED ON THE NUMBER OF LOADS BEING DRIVEN | 12/20/1999 | 09/467,726 | 5/15/2001 | 6,232,753 | US |
| NMXX-0554.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING ELECTRONIC DEVICES, COMPRISING NON-SALICIDED NON-VOLATILE MEMORY CELLS, NON-SALICIDED HV TRANSISTORS, AND LV TRANSISTORS WITH SALICIDED JUNCTIONS WITH FEW MASKS | 12/21/1999 | 09/469,849 | 8/14/2001 | 6,274,411 | US |
| NMXX-0555.00/US | Utility - ORG | Issued | METHOD FOR HIGH PRECISION PROGRAMMING NONVOLATILE MEMORY CELLS, WITH OPTIMIZED PROGRAMMING SPEED | 11/24/1999 | 09/449,168 | 5/21/2002 | 6,392,931 | US |
| NMXX-0556.00/US | Utility - ORG | Issued | PROCESS OF MANUFACTURE OF A NON VOLATILE MEMORY WITH ELECTRIC CONTINUITY OF THE COMMON SOURCE LINES | 4/12/2000 | 09/547,520 | 9/25/2001 | 6,294,431 | US |
| NMXX-0557.00/US | Utility - ORG | Issued | FLASH COMPATIBLE EEPROM | 6/21/2000 | 09/599,356 | 4/24/2001 | 6,222,775 | US |

PATENT

REEL: 029505 FRAME: 0057

Exhibit A - US Issued Patents

| MTI-DeckNo | MatterType | MatterStatus | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|-----------------|---------------|--------------|---|------------|------------|------------|-----------|---------|
| NMXS-0558.00/US | Utility - ORG | Issued | METHOD FOR READING A MEMORY, PARTICULARLY A NON-VOLATILE MEMORY | 12/29/1999 | 09/474,932 | 11/5/2002 | 6,477,625 | US |
| NMXS-0559.00/US | Utility - ORG | Issued | SYNCHRONOUS OUTPUT BUFFER, PARTICULARLY FOR NON-VOLATILE MEMORIES | 11/20/2000 | 09/716,759 | 7/23/2002 | 6,424,575 | US |
| NMXS-0560.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS HAVING VIRTUAL GROUND | 2/18/2000 | 09/507,777 | 4/2/2002 | 6,365,456 | US |
| NMXS-0561.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED MEMORY DEVICES WITH CELLS HAVING VIRTUAL GROUND | 2/25/2000 | 09/512,900 | 10/9/2001 | 6,300,195 | US |
| NMXS-0562.00/US | Utility - ORG | Abandoned | BIT COUNTER STAGE, PARTICULARLY FOR MEMORIES | 12/15/1999 | 09/464,631 | 11/27/2001 | 6,324,238 | US |
| NMXS-0563.00/US | Utility - ORG | Issued | PULSE GENERATOR CIRCUIT, PARTICULARLY FOR NON-VOLATILE MEMORIES | 12/27/1999 | 09/472,496 | 8/14/2001 | 6,275,416 | US |
| NMXS-0564.00/US | Utility - ORG | Issued | PRIORITY DETERMINING CIRCUIT FOR NON-VOLATILE MEMORY | 2/8/2000 | 09/499,799 | 4/16/2002 | 6,373,781 | US |
| NMXS-0565.00/US | Utility - ORG | Issued | METHOD FOR AUTOALIGNING OVERLAPPED LINES OF A CONDUCTIVE MATERIAL PROVIDED IN INTEGRATED ELECTRONIC CIRCUITS | 5/26/2000 | 09/579,778 | 2/26/2002 | 6,350,671 | US |
| NMXS-0566.00/US | Utility - ORG | Issued | METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE | 4/20/2000 | 09/552,933 | 3/18/2003 | 6,535,431 | US |
| NMXS-0566.01/US | Utility - DIV | Issued | METHOD OF ADJUSTING PROGRAM VOLTAGE IN NON-VOLATILE MEMORIES, AND PROCESS FOR FABRICATING A NON-VOLATILE MEMORY DEVICE | 1/24/2003 | 10/350,745 | 10/12/2004 | 6,803,630 | US |
| NMXS-0567.00/US | Utility - ORG | Issued | ADDRESS LATCH ENABLE SIGNAL CONTROL CIRCUIT FOR ELECTRONIC MEMORIES | 12/8/1999 | 09/457,500 | 6/19/2001 | 6,249,463 | US |
| NMXS-0569.00/US | Utility - ORG | Issued | SEMICONDUCTOR DEVICE WITH IMPROVED INTERCONNECTIONS BETWEEN THE CHIP AND THE TERMINALS, AND PROCESS FOR ITS MANUFACTURE | 2/10/2000 | 09/502,070 | 5/28/2002 | 6,396,132 | US |
| NMXS-0570.00/US | Utility - ORG | Issued | Method for reading a multilevel nonvolatile memory and multilevel nonvolatile memory | 2/25/2000 | 09/513,598 | 10/9/2001 | 6,301,149 | US |
| NMXS-0571.00/US | Utility - ORG | Issued | VOLTAGE REGULATING CIRCUIT FOR A CAPACITIVE LOAD | 6/29/2000 | 09/608,445 | 6/19/2001 | 6,249,112 | US |
| NMXS-0572.00/US | Utility - ORG | Issued | APPARATUS AND METHOD FOR SWITCHING BETWEEN TWO POWER SUPPLIES OF AN INTEGRATED CIRCUIT | 12/21/1998 | 09/217,321 | 9/12/2000 | 6,118,188 | US |
| NMXS-0573.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR INCREASING COMPARATOR GAIN WITHOUT AFFECTING STANDBY CURRENT | 12/21/1998 | 09/217,323 | 7/4/2000 | 6,084,390 | US |
| NMXS-0574.00/US | Utility - ORG | Issued | METHOD AND STRUCTURE FOR ENHANCING THE ACCESS TIME OF INTEGRATED CIRCUIT MEMORY DEVICES | 10/30/1998 | 09/183,231 | 8/31/1999 | 5,946,264 | US |
| NMXS-0575.00/US | Utility - ORG | Issued | CIRCUIT CIRCUIT FOR TERMINATING A MEMORY ACCESS CYCLE IN A MEMORY BLOCK OF AN ELECTRONIC STORAGE DEVICE | 10/30/1998 | 09/183,589 | 3/7/2000 | 6,034,917 | US |
| NMXS-0576.00/US | Utility - ORG | Issued | STRESS TEST MODE ENTRY AT POWER UP FOR LOW/ZERO POWER MEMORIES | 10/30/1998 | 09/183,451 | 6/27/2000 | 6,081,466 | US |
| NMXS-0577.00/US | Utility - ORG | Issued | INITIALIZATION FOR FUSE CONTROL | 10/30/1998 | 09/183,840 | 3/21/2000 | 6,041,009 | US |
| NMXS-0578.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT STRUCTURE COMPRISING CAPACITOR ELEMENT AND CORRESPONDING MANUFACTURING PROCESS | 10/12/1999 | 09/415,992 | 9/25/2001 | 6,294,798 | US |
| NMXS-0578.01/US | Utility - DIV | Issued | INTEGRATED CIRCUIT STRUCTURE COMPRISING CAPACITOR ELEMENT AND CORRESPONDING MANUFACTURING PROCESS | 7/24/2001 | 09/912,638 | 1/28/2003 | 6,511,874 | US |
| NMXS-0579.00/US | Utility - ORG | Issued | CONTENT ADDRESSABLE MEMORY PROTECTION CIRCUIT AND METHOD | 4/28/2000 | 09/561,271 | 5/29/2001 | 6,240,002 | US |
| NMXS-0580.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR FAST ADDRESSING REDUNDANT COLUMNS IN A NON VOLATILE MEMORY | 4/13/2000 | 09/548,783 | 10/30/2001 | 6,310,801 | US |
| NMXS-0581.00/US | Utility - ORG | Issued | READING CIRCUIT FOR NONVOLATILE MEMORY CELLS WITHOUT LIMITATION OF THE SUPPLY VOLTAGE | 4/11/2000 | 09/546,957 | 11/27/2001 | 6,324,098 | US |
| NMXS-0582.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR AUTOMATICALLY REGULATING THE EQUALIZATION DURATION WHEN READING A NONVOLATILE MEMORY | 4/11/2000 | 09/546,975 | 6/5/2001 | 6,243,310 | US |
| NMXS-0583.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING SOI INTEGRATED CIRCUITS AND CIRCUITS MADE THEREBY | 4/28/2000 | 09/561,272 | 6/25/2002 | 6,410,404 | US |
| NMXS-0584.00/US | Utility - ORG | Issued | COMMUNICATIONS SYSTEM AND METHOD FOR REDUCING THE EFFECTS OF TRANSMITTER NON-LINEAR DISTORTION ON A RECEIVED SIGNAL | 6/17/1999 | 09/335,024 | 8/13/2002 | 6,434,189 | US |
| NMXS-0585.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT COMPRISING AT LEAST TWO MEMORIES | 5/18/1999 | 09/313,926 | 7/23/2002 | 6,425,056 | US |

PATENT

REEL: 029505 FRAME: 0058

Exhibit A - US Issued Patents

| Patent No. | Country | Patent No. | Issue Date | Serial No. | Filed Date | Title | Patent Status | Material Type | Material No. |
|------------|---------|------------|------------|------------|------------|---|---------------|---------------|------------------|
| 6,404,679 | US | 6,351,413 | 6/11/2002 | 09/453,753 | 12/22/1999 | MULTIPLE LEVEL FLOATING-GATE MEMORY | Issued | Utility - ORG | NMXXS-0586.00/US |
| 6,157,243 | US | 9/18/2001 | 09/371,549 | 8/10/1999 | 8/10/1999 | DEVICE AND METHOD FOR GENERATING A HIGH VOLTAGE | Issued | Utility - ORG | NMXXS-0587.00/US |
| 6,212,112 | US | 4/3/2001 | 09/452,446 | 12/22/1999 | 12/22/1999 | METHOD FOR VERIFYING THE MEMORY CIRCUIT INTEGRITY | Abandoned | Utility - ORG | NMXXS-0588.00/US |
| 6,249,456 | US | 6/19/2001 | 09/448,652 | 11/24/1999 | 11/24/1999 | SECURED EEPROM MEMORY COMPRISING MEANS FOR THE DETECTION OF ERASURE BY ULTRAVIOLET RADIATION | Issued | Utility - ORG | NMXXS-0589.00/US |
| 6,292,396 | US | 9/18/2001 | 09/556,476 | 4/21/2000 | 4/21/2000 | METHOD AND DEVICE FOR THE PROGRAMMING OF AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE MEMORY FOR IMPROVING RELIABILITY | Issued | Utility - ORG | NMXXS-0590.00/US |
| 6,282,125 | US | 8/28/2001 | 09/553,526 | 4/20/2000 | 4/20/2000 | METHOD FOR ERASING AND REWRITING NON VOLATILE MEMORY CELLS AND PARTICULARLY FLASH CELLS | Issued | Utility - ORG | NMXXS-0591.00/US |
| 6,363,015 | US | 3/26/2002 | 09/589,723 | 6/8/2000 | 6/8/2000 | READING METHOD FOR NON-VOLATILE MEMORIES WITH SENSING RATIO VARIABLE WITH THE READING VOLTAGE, AND DEVICE TO REALIZE SAID METHOD | Issued | Utility - ORG | NMXXS-0592.00/US |
| 6,314,043 | US | 11/6/2001 | 09/592,796 | 6/13/2000 | 6/13/2000 | ERASING AND PARALLEL REWRITING CIRCUIT FOR MEMORY CELL BLOCKS, PARTICULARLY FOR ANALOG FLASH CELLS, AND RELATED OPERATING METHOD | Issued | Utility - ORG | NMXXS-0593.00/US |
| 6,351,413 | US | 2/26/2002 | 09/552,945 | 4/20/2000 | 4/20/2000 | NONVOLATILE MEMORY DEVICE, IN PARTICULAR A FLASH-EEPROM | Issued | Utility - ORG | NMXXS-0594.00/US |
| 6,297,398 | US | 9/18/2001 | 09/569,232 | 5/11/2000 | 5/11/2000 | METHOD FOR THE IN-WRITING VERIFICATION OF THE THRESHOLD VALUE IN NON-VOLATILE MEMORIES | Issued | Utility - ORG | NMXXS-0595.00/US |
| 6,456,530 | US | 9/24/2002 | 09/602,660 | 6/26/2000 | 6/26/2000 | NONVOLATILE MEMORY DEVICE WITH HIERARCHICAL SECTOR DECODING | Issued | Utility - ORG | NMXXS-0596.00/US |
| 6,198,660 | US | 3/6/2001 | 09/572,127 | 5/17/2000 | 5/17/2000 | SYNCHRONOUS MULTILEVEL NON-VOLATILE MEMORY AND RELATED READING METHOD | Issued | Utility - ORG | NMXXS-0597.00/US |
| 6,333,885 | US | 12/26/2001 | 09/603,275 | 6/26/2000 | 6/26/2000 | CIRCUIT FOR READING A SEMICONDUCTOR MEMORY | Issued | Utility - ORG | NMXXS-0598.00/US |
| 6,320,790 | US | 11/20/2001 | 09/586,399 | 6/2/2000 | 6/2/2000 | BIASING STAGE FOR BIASING THE DRAIN TERMINAL OF A NONVOLATILE MEMORY CELL DURING THE READ PHASE | Issued | Utility - ORG | NMXXS-0599.00/US |
| 6,507,183 | US | 1/14/2003 | 09/608,847 | 6/29/2000 | 6/29/2000 | METHOD AND A DEVICE FOR MEASURING AN ANALOG VOLTAGE IN A NON-VOLATILE MEMORY | Issued | Utility - ORG | NMXXS-0600.00/US |
| 6,392,936 | US | 5/21/2002 | 09/608,239 | 6/30/2000 | 6/30/2000 | METHOD AND APPARATUS FOR GENERATING FROM A SINGLE SUPPLY LINE VOLTAGES INTERNAL TO A FLASH MEMORY WITH REDUCED SETTLING TIMES | Issued | Utility - ORG | NMXXS-0601.00/US |
| 6,292,400 | US | 9/18/2001 | 09/620,765 | 7/21/2000 | 7/21/2000 | NON-VOLATILE MEMORY DEVICE WITH LOW POWER CONSUMPTION AND AND RELATIVE WRITING, READING AND ERASING METHODS | Issued | Utility - ORG | NMXXS-0602.00/US |
| 6,366,496 | US | 4/2/2002 | 09/631,187 | 8/2/2000 | 8/2/2000 | METHOD FOR PROGRAMMING MULTI-LEVEL NON-VOLATILE MEMORIES BY CONTROLLING THE GATE VOLTAGE | Issued | Utility - ORG | NMXXS-0603.00/US |
| 6,433,583 | US | 8/13/2002 | 09/585,916 | 6/2/2000 | 6/2/2000 | CMOS SWITCH CIRCUIT FOR TRANSFERRING HIGH VOLTAGES, IN PARTICULAR FOR LINE ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE | Issued | Utility - ORG | NMXXS-0604.00/US |
| 6,356,481 | US | 3/12/2002 | 09/595,054 | 6/16/2000 | 6/16/2000 | ROW DECODER FOR SELECTIVELY BIASING A WORDLINE TO A POSITIVE OR NEGATIVE VOLTAGE | Abandoned | Utility - ORG | NMXXS-0605.00/US |
| 6,349,059 | US | 2/19/2002 | 09/716,746 | 11/20/2000 | 11/20/2000 | METHOD FOR READING DATA FROM A NON-VOLATILE MEMORY DEVICE WITH AUTODETECT BURST MODE READING AND CORRESPONDING READING CIRCUIT | Issued | Utility - ORG | NMXXS-0606.00/US |
| 6,469,934 | US | 10/22/2002 | 09/738,253 | 12/14/2000 | 12/14/2000 | SOFT PROGRAMMING METHOD FOR NON-VOLATILE MEMORY CELLS | Issued | Utility - ORG | NMXXS-0607.00/US |
| 6,570,229 | US | 12/30/2003 | 10/077,288 | 2/15/2002 | 2/15/2002 | BIPOLAR TRANSISTOR PRODUCED USING PROCESSES COMPATIBLE WITH THOSE EMPLOYED IN THE MANUFACTURE OF MOS DEVICES | Issued | Utility - Div | NMXXS-0608.01/US |
| 6,320,361 | US | 11/20/2001 | 09/736,984 | 12/13/2000 | 12/13/2000 | BUFFER DEVICE WITH DUAL SUPPLY VOLTAGE FOR LOW SUPPLY VOLTAGE APPLICATIONS | Issued | Utility - ORG | NMXXS-0610.00/US |
| 6,912,598 | US | 6/28/2005 | 09/627,703 | 7/28/2000 | 7/28/2000 | NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF SIMULTANEOUS MODIFICATION OF THE CONTENT AND BURST MODE READ OR PAGE MODE READ | Issued | Utility - ORG | NMXXS-0611.00/US |
| 6,442,068 | US | 8/27/2002 | 09/619,589 | 7/19/2000 | 7/19/2000 | NON-VOLATILE MEMORY WITH FUNCTIONAL CAPABILITY OF BURST MODE READ AND PAGE MODE READ DURING SUSPENSION OF AN OPERATION OF ELECTRICAL ALTERATION | Issued | Utility - ORG | NMXXS-0612.00/US |

PATENT

REEL: 029505 FRAME: 0059

Exhibit A - US Issued Patents

| Patent No. | Material | Material | Material | Title | Filed | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|-----------|----------|---|------------|------------|------------|------------|---------|
| NMMS-0613.00/US | Utility - ORG | Issued | | METHOD FOR CONTROLLED SOFT PROGRAMMING OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE FLASH EEPROM TYPE | 10/27/2000 | 09/699,309 | 4/30/2002 | 6,383,177 | US |
| NMMS-0614.00/US | Utility - ORG | Issued | | MANUFACTURE OF AN HY-MOS TRANSISTOR WITH LOW MULTIPLICATION FACTOR IN A DUAL-GATE CMOS PROCESS | 11/14/2000 | 09/713,144 | 12/31/2002 | 6,501,147 | US |
| NMMS-0615.00/US | Utility - ORG | Issued | | READ CIRCUIT FOR A NONVOLATILE MEMORY | 7/21/2000 | 09/621,019 | 12/4/2001 | 6,327,184 | US |
| NMMS-0617.00/US | Utility - ORG | Issued | | ENABLING CIRCUIT FOR OUTPUT DEVICES IN ELECTRONIC MEMORIES | 7/31/2000 | 09/629,229 | 8/20/2002 | 6,438,040 | US |
| NMMS-0618.00/US | Utility - ORG | Issued | | PROCESS FOR THE FABRICATION OF INTEGRATED DEVICES WITH REDUCTION OF DAMAGE FROM PLASMA | 3/9/2001 | 09/804,693 | 10/28/2003 | 6,638,833 | US |
| NMMS-0619.00/US | Utility - ORG | Issued | | NON VOLATILE MEMORY WITH DETECTION OF SHORT CIRCUITS BETWEEN WORD LINES | 9/8/2000 | 09/658,236 | 10/23/2001 | 6,307,778 | US |
| NMMS-0620.00/US | Utility - ORG | Issued | | CIRCUIT AND METHOD FOR TIMING MULTI-LEVEL NON-VOLATILE MEMORIES | 12/15/2000 | 09/738,889 | 6/3/2003 | 6,574,146 | US |
| NMMS-0621.00/US | Utility - ORG | Issued | | NON-VOLATILE MEMORY DEVICE WITH BURST MODE READING AND CORRESPONDING READING METHOD | 11/21/2000 | 09/717,938 | 2/8/2005 | 6,854,040 | US |
| NMMS-0622.00/US | Utility - ORG | Issued | | VOLTAGE GENERATOR SWITCHING BETWEEN ALTERNATING, FIRST AND SECOND VOLTAGE VALUES, IN PARTICULAR FOR PROGRAMMING MULTILEVEL CELLS | 11/15/2000 | 09/714,837 | 7/23/2002 | 6,424,121 | US |
| NMMS-0623.00/US | Utility - ORG | Lapsed | | ANTI-DECIPHERING CONTACTS | 10/1/2001 | 09/668,682 | 3/4/2003 | 6,528,885 | US |
| NMMS-0624.00/US | Utility - ORG | Issued | | READING CIRCUIT FOR A NON-VOLATILE MEMORY | 10/27/2000 | 09/699,304 | 6/4/2002 | 6,400,607 | US |
| NMMS-0625.00/US | Utility - ORG | Issued | | READING METHOD AND CIRCUIT FOR A NON-VOLATILE MEMORY | 10/27/2000 | 09/699,043 | 10/29/2002 | 6,473,340 | US |
| NMMS-0626.00/US | Utility - ORG | Issued | | COLUMN DECODER CIRCUIT FOR PAGE READING OF A SEMICONDUCTOR MEMORY | 2/27/2001 | 09/797,171 | 1/4/2003 | 6,507,534 | US |
| NMMS-0627.00/US | Utility - ORG | Issued | | FLOW PROCESS FOR PRODUCING NON-VOLATILE MEMORIES WITH DIFFERENTIATED REMOVAL OF SACRIFICIAL OXIDE | 8/2/2000 | 09/630,933 | 3/26/2002 | 6,362,053 | US |
| NMMS-0628.00/US | Utility - ORG | Issued | | ARCHITECTURE FOR HANDLING INTERNAL VOLTAGES IN A NON-VOLATILE MEMORY, PARTICULARLY IN A SINGLE-VOLTAGE SUPPLY TYPE OF DUAL-WORK FLASH MEMORY | 11/9/2000 | 09/710,067 | 5/7/2002 | 6,385,107 | US |
| NMMS-0629.00/US | Utility - ORG | Issued | | CONTROL AND TIMING STRUCTURE FOR A MEMORY | 10/5/2001 | 09/972,753 | 4/15/2003 | 6,549,485 | US |
| NMMS-0630.00/US | Utility - ORG | Issued | | PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS | 11/22/2000 | 09/718,971 | 1/21/2003 | 6,509,222 | US |
| NMMS-0630.01/US | Utility - Div | Issued | | PROCESS FOR MANUFACTURING ELECTRONIC DEVICES COMPRISING NONVOLATILE MEMORY CELLS OF REDUCED DIMENSIONS | 8/20/2002 | 10/725,315 | 8/5/2003 | 6,603,171 | US |
| NMMS-0631.00/US | Utility - ORG | Issued | | MANUFACTURING PROCESS FOR NON-VOLATILE FLOATING GATE MEMORY CELLS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND COMPRISED IN A CELL MATRIX WITH AN ASSOCIATED CONTROL CIRCUITRY | 12/5/2000 | 09/730,518 | 7/16/2002 | 6,420,223 | US |
| NMMS-0632.00/US | Utility - ORG | Issued | | SINGLE SUPPLY VOLTAGE NONVOLATILE MEMORY DEVICE WITH ROW DECODING | 7/28/2000 | 09/627,273 | 4/16/2002 | 6,373,780 | US |
| NMMS-0633.00/US | Utility - ORG | Issued | | NONVOLATILE MEMORY TEST STRUCTURE AND NONVOLATILE MEMORY RELIABILITY TEST METHOD | 10/27/1999 | 09/428,683 | 10/3/2000 | 6,128,219 | US |
| NMMS-0633.00/US | Utility - ORG | Issued | | METHOD AND CIRCUIT FOR PROGRAMMING A MULTILEVEL NON-VOLATILE MEMORY SERIAL-FLASH, EPROM, EEPROM AND FLASH EEPROM NONVOLATILE MEMORY IN AMG CONFIGURATION | 9/12/2001 | 09/952,957 | 2/25/2003 | 6,525,961 | US |
| NMMS-0637.00/US | Utility - ORG | Issued | | LOW CONSUMPTION VOLTAGE BOOST DEVICE | 10/10/2000 | 09/686,362 | 4/30/2002 | 6,381,173 | US |
| NMMS-0638.00/US | Utility - ORG | Issued | | NON-VOLATILE MEMORY DEVICE WITH CONFIGURABLE ROW REDUNDANCY | 12/22/2000 | 09/747,312 | 8/20/2002 | 6,437,936 | US |
| NMMS-0639.00/US | Utility - ORG | Abandoned | | INTEGRATED DEVICE WITH OPERATIVITY TESTING | 2/14/2001 | 09/785,079 | 7/9/2002 | 6,418,051 | US |
| NMMS-0640.00/US | Utility - ORG | Issued | | VOLTAGE BOOSTING DEVICE, IN PARTICULAR FOR SPEEDING POWER-UP OF MULTILEVEL NONVOLATILE MEMORIES | 3/27/2001 | 09/798,347 | 5/24/2005 | 6,898,745 | US |
| NMMS-0641.00/US | Utility - ORG | Issued | | NON-VOLATILE HIGH-PERFORMANCE MEMORY DEVICE AND RELATIVE MANUFACTURING PROCESS | 2/6/2001 | 09/778,330 | 8/6/2002 | 6,429,634 | US |
| NMMS-0642.00/US | Utility - ORG | Issued | | MANUFACTURING PROCESS | 12/19/2000 | 09/740,407 | 1/13/2004 | 6,677,206 | US |
| NMMS-0643.00/US | Utility - ORG | Issued | | SYNCHRONOUS COUNTER FOR ELECTRONIC MEMORIES | 1/23/2001 | 09/767,762 | 2/26/2002 | 6,351,434 | US |

PATENT

Exhibit A - US Issued Patents

| NIMX-DocNo | MatterType | MatterStatus | Title | FileDate | SerialNo | IssueDate | PatentNo | Country |
|------------------|---------------|--------------|--|------------|------------|------------|-----------|---------|
| NIMXS-0644.00/US | Utility - ORG | Issued | SYNCHRONIZATION CIRCUIT FOR READ PATHS OF AN ELECTRONIC MEMORY | 4/9/2001 | 09/827,569 | 10/12/2004 | 6,804,756 | US |
| NIMXS-0645.00/US | Utility - ORG | Issued | INTERNAL ADDRESSING STRUCTURE OF A SEMICONDUCTOR MEMORY | 10/9/2001 | 09/974,737 | 12/31/2002 | 6,501,700 | US |
| NIMXS-0646.00/US | Utility - ORG | Issued | STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE | 3/20/2001 | 09/817,363 | 7/2/2002 | 6,414,875 | US |
| NIMXS-0646.01/US | Utility - DIV | Issued | STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE | 6/24/2002 | 10/179,553 | 1/27/2004 | 6,683,808 | US |
| NIMXS-0646.02/US | Utility - DIV | Issued | STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE | 12/19/2003 | 10/742,429 | 7/4/2006 | 7,072,212 | US |
| NIMXS-0646.03/US | Utility - DIV | Issued | STRING PROGRAMMABLE NONVOLATILE MEMORY WITH NOR ARCHITECTURE | 12/19/2003 | 10/742,181 | 10/11/2005 | 6,954,395 | US |
| NIMXS-0647.00/US | Utility - ORG | Issued | MANUFACTURING PROCESS FOR THE INTEGRATION IN A SEMICONDUCTOR CHIP OF AN INTEGRATED CIRCUIT INCLUDING A HIGH-DENSITY INTEGRATED CIRCUIT COMPONENTS PORTION AND A HIGH-PERFORMANCE LOGIC INTEGRATED CIRCUIT COMPONENTS PORTION | 5/15/2001 | 09/858,335 | 9/17/2002 | 6,451,653 | US |
| NIMXS-0648.00/US | Utility - ORG | Issued | LOGIC PARTITIONING OF A NONVOLATILE MEMORY ARRAY | 3/26/2001 | 09/817,804 | 6/17/2003 | 6,581,134 | US |
| NIMXS-0649.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY MATRIX ARCHITECTURE WITH VERTICAL INSULATION STRIPS BETWEEN ADJACENT MEMORY BLOCKS | 7/3/2001 | 09/898,744 | 10/15/2002 | 6,466,479 | US |
| NIMXS-0650.00/US | Utility - ORG | Issued | PROGRAMMABLE VOLTAGE GENERATOR | 11/15/2000 | 09/714,852 | 11/18/2003 | 6,650,173 | US |
| NIMXS-0651.00/US | Utility - ORG | Issued | METHOD OF FORMING LOW-RESISTIVITY CONNECTIONS IN NON-VOLATILE MEMORIES | 3/2/2001 | 09/798,778 | 2/3/2004 | 6,686,241 | US |
| NIMXS-0652.00/US | Utility - ORG | Issued | METHOD AND A DEVICE FOR TESTING ELECTRONIC MEMORY DEVICES | 3/30/2001 | 09/823,826 | 1/23/2007 | 7,168,016 | US |
| NIMXS-0653.00/US | Utility - ORG | Issued | CIRCUITAL STRUCTURE FOR PROGRAMMING DATA IN A NON-VOLATILE MEMORY DEVICE | 5/30/2001 | 09/871,235 | 1/14/2003 | 6,507,517 | US |
| NIMXS-0654.00/US | Utility - ORG | Issued | CIRCUITAL STRUCTURE FOR READING DATA IN A NON-VOLATILE MEMORY DEVICE | 5/30/2001 | 09/871,234 | 4/15/2003 | 6,549,473 | US |
| NIMXS-0655.00/US | Utility - ORG | Abandoned | INTEGRATED DEVICE WITH VOLTAGE SELECTOR | 3/29/2001 | 09/823,262 | 11/5/2002 | 6,476,664 | US |
| NIMXS-0656.00/US | Utility - ORG | Abandoned | LOW-CONSUMPTION CHARGE PUMP FOR A NONVOLATILE MEMORY | 3/28/2001 | 09/821,827 | 5/6/2003 | 6,559,709 | US |
| NIMXS-0657.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING A NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT | 7/6/2001 | 09/900,501 | 3/25/2003 | 6,537,879 | US |
| NIMXS-0657.01/US | Utility - DIV | Issued | NON-VOLATILE MEMORY CELL WITH A FLOATING GATE REGION AUTOALIGNED TO THE ISOLATION AND WITH A HIGH COUPLING COEFFICIENT | 1/7/2003 | 10/337,556 | 6/15/2004 | 6,750,505 | US |
| NIMXS-0658.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY ARCHITECTURE | 10/5/2001 | 09/972,769 | 6/17/2003 | 6,580,637 | US |
| NIMXS-0659.00/US | Utility - ORG | Issued | REFERENCE VOLTAGE ADJUSTMENT | 12/31/1999 | 09/476,036 | 8/28/2001 | 6,281,734 | US |
| NIMXS-0659.01/US | Utility - DIV | Issued | REFERENCE VOLTAGE ADJUSTMENT | 7/10/2001 | 09/902,206 | 11/5/2002 | 6,476,669 | US |
| NIMXS-0660.00/US | Utility - ORG | Issued | INTEGRATED VOLATILE AND NON-VOLATILE MEMORY | 8/31/2000 | 09/653,495 | 7/15/2003 | 6,594,192 | US |
| NIMXS-0660.01/US | Utility - DIV | Issued | INTEGRATED VOLATILE AND NON-VOLATILE MEMORY | 5/20/2003 | 10/442,844 | 8/24/2004 | 6,781,916 | US |
| NIMXS-0661.00/US | Utility - ORG | Issued | CMOS TECHNOLOGY VOLTAGE BOOSTER | 12/15/2000 | 09/738,890 | 7/16/2002 | 6,420,926 | US |
| NIMXS-0662.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY AND HIGH SPEED MEMORY TEST METHOD | 9/26/2000 | 09/670,248 | 8/20/2002 | 6,438,048 | US |
| NIMXS-0663.00/US | Utility - ORG | Issued | Memory test method and nonvolatile memory with low error masking probability | 9/26/2000 | 09/670,471 | 8/28/2001 | 6,282,134 | US |
| NIMXS-0664.00/US | Utility - ORG | Issued | ROW SELECTION CIRCUIT FOR FAST MEMORY DEVICES | 12/21/2000 | 09/745,286 | 8/27/2002 | 6,442,072 | US |
| NIMXS-0665.00/US | Utility - ORG | Issued | INTERLEAVED DATA PATH AND OUTPUT MANAGEMENT ARCHITECTURE FOR AN INTERLEAVED MEMORY AND LOAD PULSER CIRCUIT FOR OUTPUTTING THE READ DATA | 1/31/2001 | 09/774,542 | 10/22/2002 | 6,470,431 | US |
| NIMXS-0666.00/US | Utility - ORG | Issued | INTERLEAVED MEMORY DEVICE FOR SEQUENTIAL ACCESS SYNCHRONOUS READING WITH SIMPLIFIED ADDRESS COUNTERS | 1/31/2001 | 09/774,539 | 9/17/2002 | 6,452,864 | US |
| NIMXS-0667.00/US | Utility - ORG | Issued | REDUNDANCY ARCHITECTURE FOR AN INTERLEAVED MEMORY | 1/31/2001 | 09/773,272 | 10/29/2002 | 6,473,339 | US |
| NIMXS-0668.00/US | Utility - ORG | Issued | ACCELERATED CARRY GENERATION | 1/31/2001 | 09/774,878 | 4/2/2002 | 6,366,634 | US |
| NIMXS-0669.00/US | Utility - ORG | Issued | ATD GENERATION IN A SYNCHRONOUS MEMORY | 1/31/2001 | 09/773,760 | 9/23/2003 | 6,625,706 | US |
| NIMXS-0670.00/US | Utility - ORG | Issued | INTERLEAVED MEMORY DEVICE FOR BURST TYPE ACCESS IN SYNCHRONOUS READ MODE WITH THE TWO SEMI-ARRAYS INDEPENDENTLY READABLE IN RANDOM ACCESS ASYNCHRONOUS MODE | 1/31/2001 | 09/773,300 | 7/1/2003 | 6,587,913 | US |
| NIMXS-0671.00/US | Utility - ORG | Issued | COLOR IMAGE RESTORATION WITH ANTIALIAS | 11/2/2000 | 09/705,145 | 1/11/2005 | 6,842,191 | US |

PATENT

REEL: 029505 FRAME: 0061

Exhibit A - US Issued Patents

| Patent No. | MarketType | MarketStatus | Title | FiledDate | SerialNo. | IssueDate | PatentNo. | Country |
|-----------------|-----------------|--------------|--|------------|------------|------------|-----------|---------|
| NMMS-0672.00/US | Utility - NSPCT | Issued | VOLTAGE PRODUCTION CIRCUIT | 6/26/2000 | 10/019,771 | 9/16/2003 | 6,621,720 | US |
| NMMS-0673.00/US | Utility - ORG | Issued | METHOD FOR PAGE MODE WRITING IN AN ELECTRICALLY ERASABLE/PROGRAMMABLE NON-VOLATILE MEMORY AND CORRESPONDING ARCHITECTURE | 9/12/2000 | 09/660,303 | 1/7/2003 | 6,504,791 | US |
| NMMS-0674.00/US | Utility - ORG | Issued | MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY | 9/29/2000 | 09/675,366 | 10/23/2001 | 6,307,792 | US |
| NMMS-0674.01/US | Utility - DIV | Issued | MEMORY INCORPORATING COLUMN REGISTER AND METHOD OF WRITING IN SAID MEMORY | 9/13/2001 | 09/952,904 | 5/7/2002 | 6,385,096 | US |
| NMMS-0675.00/US | Utility - ORG | Issued | ARCHITECTURE OF A NON-VOLATILE ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY | 9/7/2000 | 09/657,319 | 8/14/2001 | 6,275,413 | US |
| NMMS-0677.00/US | Utility - ORG | Issued | PAGE BY PAGE PROGRAMMABLE FLASH MEMORY | 12/14/2000 | 09/737,170 | 1/4/2005 | 6,839,285 | US |
| NMMS-0678.00/US | Utility - ORG | Issued | METHOD FOR THE CORRECTION OF A BIT IN A STRING OF BITS | 12/15/2000 | 09/737,827 | 5/11/2004 | 6,735,733 | US |
| NMMS-0679.00/US | Utility - ORG | Issued | HIGH-EFFICIENCY BIDIRECTIONAL VOLTAGE BOOSTING DEVICE | 2/13/2001 | 09/788,623 | 9/10/2002 | 6,448,842 | US |
| NMMS-0680.00/US | Utility - ORG | Issued | CHARGE PUMP BOOSTER DEVICE WITH TRANSFER AND RECOVERY OF THE CHARGE | 2/13/2001 | 09/785,042 | 6/11/2002 | 6,404,272 | US |
| NMMS-0681.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY CELL WITH HIGH PROGRAMMING EFFICIENCY | 7/30/2001 | 09/919,341 | 5/11/2004 | 6,734,490 | US |
| NMMS-0682.00/US | Utility - ORG | Issued | METHOD AND A CIRCUIT STRUCTURE FOR MODIFYING THE THRESHOLD VOLTAGES OF NON-VOLATILE MEMORY CELLS | 7/18/2001 | 09/908,986 | 2/11/2003 | 6,519,183 | US |
| NMMS-0683.00/US | Utility - ORG | Issued | CONTROL CIRCUIT FOR A VARIABLE-VOLTAGE REGULATOR OF A NONVOLATILE MEMORY WITH HIERARCHICAL ROW DECODING | 9/21/2001 | 09/960,851 | 1/7/2003 | 6,504,758 | US |
| NMMS-0684.00/US | Utility - ORG | Issued | CIRCUIT ARRANGEMENT FOR THE LOWERING OF THE THRESHOLD VOLTAGE OF A DIODE CONFIGURED TRANSISTOR | 6/13/2001 | 09/881,661 | 12/31/2002 | 6,501,673 | US |
| NMMS-0685.00/US | Utility - ORG | Issued | DIRECT-COMPARISON READING CIRCUIT FOR A NONVOLATILE MEMORY ARRAY | 8/15/2001 | 09/930,875 | 10/8/2002 | 6,462,987 | US |
| NMMS-0686.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY WITH A CHARGE PUMP WITH REGULATED VOLTAGE | 7/19/2001 | 09/909,467 | 11/12/2002 | 6,480,436 | US |
| NMMS-0687.00/US | Utility - ORG | Issued | CHARGE PUMP WITH EFFICIENT SWITCHING TECHNIQUES | 12/11/2000 | 09/735,277 | 3/19/2002 | 6,359,509 | US |
| NMMS-0688.00/US | Utility - ORG | Issued | High-voltage bidirectional switch made using high-voltage MOS transistors | 6/16/2000 | 09/595,680 | 9/11/2001 | 6,288,603 | US |
| NMMS-0689.00/US | Utility - ORG | Issued | READING CIRCUIT FOR SEMICONDUCTOR NON-VOLATILE MEMORIES | 9/13/2001 | 09/953,070 | 5/13/2003 | 6,563,737 | US |
| NMMS-0691.00/US | Utility - ORG | Issued | LATERAL DIODES TRANSISTOR WITH FIRST AND SECOND DRAIN ELECTRODES IN RESPECTIVE CONTACT WITH HIGH-AND LOW-CONCENTRATION PORTIONS OF A DRAIN REGION | 9/20/2001 | 09/960,254 | 9/23/2003 | 6,624,471 | US |
| NMMS-0692.00/US | Utility - ORG | Issued | VOLTAGE BOOSTER WITH A LOW OUTPUT RESISTANCE | 2/13/2001 | 09/785,083 | 6/11/2002 | 6,404,273 | US |
| NMMS-0693.00/US | Utility - ORG | Issued | MULTIPURPOSE METHOD FOR CONSTRUCTING AN ERROR-CONTROL CODE FOR MULTILEVEL MEMORY CELLS OPERATING WITH A VARIABLE NUMBER OF STORAGE LEVELS, AND MULTIPURPOSE ERROR-CONTROL METHOD USING SAID ERROR-CONTROL CODE | 11/2/2001 | 10/015,949 | 5/16/2006 | 7,047,478 | US |
| NMMS-0694.00/US | Utility - ORG | Issued | FOLDING TOP FOR A MOTOR VEHICLE | 10/31/2001 | 09/002,599 | 8/5/2003 | 6,603,681 | US |
| NMMS-0695.00/US | Utility - ORG | Issued | NONVOLATILE SEMICONDUCTOR MEMORY CAPABLE OF SELECTIVELY ERASING A PLURALITY OF ELEMENTAL MEMORY UNITS | 7/31/2001 | 09/919,789 | 3/11/2003 | 6,552,171 | US |
| NMMS-0696.00/US | Utility - ORG | Issued | ELECTRICALLY MODIFIABLE, NON-VOLATILE, SEMICONDUCTOR MEMORY WHICH CAN KEEP A DATUM STORED UNTIL AN OPERATION TO MODIFY THE DATUM IS COMPLETED | 12/28/2001 | 10/036,088 | 1/4/2005 | 6,839,818 | US |
| NMMS-0697.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR FOR LOW-CONSUMPTION CIRCUITS | 11/7/2001 | 09/038,540 | 5/6/2003 | 6,559,627 | US |
| NMMS-0698.00/US | Utility - ORG | Issued | SMALL SIZE, LOW CONSUMPTION, MULTILEVEL, NONVOLATILE MEMORY | 10/4/2001 | 09/972,726 | 4/1/2003 | 6,542,404 | US |
| NMMS-0699.00/US | Utility - ORG | Issued | METHOD FOR STORING AND READING DATA IN A MULTILEVEL, NONVOLATILE MEMORY | 10/11/2001 | 09/976,473 | 11/11/2003 | 6,646,913 | US |
| NMMS-0700.00/US | Utility - ORG | Abandoned | NONVOLATILE MEMORY DEVICE, HAVING PARTS WITH DIFFERENT ACCESS TIME, RELIABILITY, AND CAPACITY | 9/19/2001 | 09/957,628 | 12/10/2002 | 6,493,260 | US |
| NMMS-0701.00/US | Utility - ORG | Issued | CONTROL CIRCUIT FOR AN OUTPUT DRIVING STAGE OF AN INTEGRATED CIRCUIT | 11/21/2001 | 09/991,493 | 5/20/2003 | 6,567,318 | US |

PATENT

REEL: 029505 FRAME: 0062

Exhibit A - US Issued Patents

| MT-Id-No | MasterType | MasterStatus | Title | FiledDate | SerialNo | IssuedDate | PatentNo | Country |
|-----------------|---------------|--------------|---|------------|------------|------------|-----------|---------|
| NMKS-0702.00/US | Utility - ORG | Issued | BIASING CIRCUIT FOR MULTI-LEVEL MEMORY CELLS | 6/14/2001 | 09/882,535 | 3/18/2003 | 6,535,428 | US |
| NMKS-0703.00/US | Utility - ORG | Issued | CIRCUIT DEVICE FOR PERFORMING HIERARCHIC ROW DECODING IN NON-VOLATILE MEMORY DEVICES | 7/11/2001 | 09/905,163 | 12/10/2002 | 6,493,268 | US |
| NMKS-0704.01/US | Utility - CON | Issued | ANALOG-TO-DIGITAL CONVERSION METHOD AND DEVICE, IN HIGH-DENSITY MULTILEVEL NON-VOLATILE MEMORY DEVICES | 1/29/2002 | 10/060,076 | 1/6/2004 | 6,674,385 | US |
| NMKS-0705.00/US | Utility - ORG | Issued | POWER-ON RESET CIRCUIT FOR DUAL SUPPLY VOLTAGES | 10/25/2001 | 09/003,474 | 11/12/2002 | 6,480,421 | US |
| NMKS-0706.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING NONVOLATILE MEMORY CELLS WITH PROGRAM AND VERIFY ALGORITHM USING A STAIRCASE VOLTAGE WITH VARYING STEP AMPLITUDE | 4/9/2002 | 10/119,523 | 9/7/2004 | 6,788,579 | US |
| NMKS-0707.00/US | Utility - ORG | Issued | CONDUCTION LINE DECOUPLING CIRCUIT | 7/26/2001 | 09/917,613 | 9/7/2004 | 6,788,517 | US |
| NMKS-0708.00/US | Utility - ORG | Issued | MULTI-EMITTER BIPOLAR TRANSISTOR FOR BANDGAP REFERENCE CIRCUITS | 12/27/2001 | 10/035,006 | 3/2/2004 | 6,700,226 | US |
| NMKS-0710.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY SYSTEM | 5/30/2002 | 10/158,554 | 7/15/2003 | 6,594,180 | US |
| NMKS-0711.00/US | Utility - ORG | Issued | OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OUTPUT SIGNAL SWITCHING NOISE REDUCTION, AND NONVOLATILE MEMORY COMPRISING THE SAME | 5/30/2002 | 10/161,053 | 9/7/2004 | 6,788,586 | US |
| NMKS-0712.00/US | Utility - ORG | Issued | OUTPUT BUFFER FOR A NONVOLATILE MEMORY WITH OPTIMIZED SLEW-RATE CONTROL | 5/30/2002 | 10/161,055 | 12/7/2004 | 6,829,177 | US |
| NMKS-0713.00/US | Utility - ORG | Issued | EEPROM FLASH MEMORY ERASABLE LINE BY LINE | 8/20/2002 | 10/225,513 | 2/3/2004 | 6,687,167 | US |
| NMKS-0714.00/US | Utility - ORG | Issued | METHOD OF PROGRAMMING A PLURALITY OF MEMORY CELLS CONNECTED IN PARALLEL, AND A PROGRAMMING CIRCUIT THEREFOR | 12/19/2001 | 10/036,337 | 2/3/2004 | 6,687,159 | US |
| NMKS-0715.00/US | Utility - ORG | Issued | COLUMN MULTIPLEXER FOR SEMICONDUCTOR MEMORIES | 5/30/2002 | 10/158,553 | 4/22/2003 | 6,552,952 | US |
| NMKS-0716.00/US | Utility - ORG | Issued | PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL | 12/14/2001 | 10/017,502 | 12/23/2003 | 6,667,903 | US |
| NMKS-0717.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL, IN PARTICULAR A MULTI-LEVEL, NONVOLATILE MEMORY CELL | 1/14/2002 | 10/047,918 | 11/4/2003 | 6,643,179 | US |
| NMKS-0718.00/US | Utility - ORG | Issued | METHOD FOR STORING DATA IN A NONVOLATILE MEMORY | 12/19/2001 | 10/035,909 | 12/2/2003 | 6,655,758 | US |
| NMKS-0720.00/US | Utility - ORG | Issued | AUTOTESTING METHOD OF A MEMORY CELL MATRIX, PARTICULARLY OF THE NON-VOLATILE TYPE | 12/23/2002 | 10/328,721 | 11/8/2005 | 6,963,512 | US |
| NMKS-0721.00/US | Utility - ORG | Issued | READING CIRCUIT AND METHOD FOR A MULTILEVEL NON-VOLATILE MEMORY | 4/8/2002 | 10/118,660 | 12/2/2003 | 6,657,895 | US |
| NMKS-0722.00/US | Utility - ORG | Abandoned | METHOD OF REFRESHING AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY | 6/20/2002 | 10/176,387 | 5/4/2004 | 6,731,557 | US |
| NMKS-0723.00/US | Utility - ORG | Issued | HIGH-EFFICIENCY POWER CHARGE PUMP SUPPLYING HIGH DC OUTPUT CURRENTS | 6/3/2002 | 10/162,135 | 8/12/2003 | 6,605,985 | US |
| NMKS-0724.00/US | Utility - ORG | Issued | NON-VOLATILE, ELECTRICALLY ALTERABLE SEMICONDUCTOR MEMORY | 1/24/2002 | 10/057,769 | 9/9/2003 | 6,618,315 | US |
| NMKS-0725.00/US | Utility - ORG | Issued | METHOD FOR ERASING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, IN PARTICULAR AN EEPROM-FLASH MEMORY DEVICE | 5/30/2002 | 10/159,780 | 3/22/2005 | 6,871,258 | US |
| NMKS-0726.00/US | Utility - ORG | Issued | METHOD FOR REFRESHING STORED DATA IN AN ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY | 1/24/2002 | 10/057,768 | 12/23/2003 | 6,668,303 | US |
| NMKS-0727.00/US | Utility - ORG | Issued | MEMORY WITH IMPROVED DIFFERENTIAL READING SYSTEM | 6/20/2002 | 10/176,954 | 3/2/2004 | 6,700,819 | US |
| NMKS-0728.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR TIMING DYNAMIC READING OF A MEMORY CELL WITH CONTROL OF THE INTEGRATION TIME | 4/18/2002 | 10/123,874 | 4/27/2004 | 6,728,141 | US |
| NMKS-0729.00/US | Utility - CIP | Issued | METHOD AND CIRCUIT FOR DYNAMIC READING OF A MEMORY CELL AT LOW SUPPLY VOLTAGE AND WITH LOW OUTPUT DYNAMICS | 2/13/2002 | 10/076,023 | 10/28/2003 | 6,639,833 | US |
| NMKS-0730.00/US | Utility - CIP | Issued | METHOD AND CIRCUIT FOR GENERATING REFERENCE VOLTAGES FOR READING A MULTILEVEL MEMORY CELL | 4/26/2002 | 10/133,231 | 4/20/2004 | 6,724,658 | US |
| NMKS-0731.00/US | Utility - ORG | Issued | METHOD FOR ERROR CONTROL IN MULTILEVEL CELLS WITH CONFIGURABLE NUMBER OF STORED BITS | 5/30/2002 | 10/159,782 | 3/21/2006 | 7,017,099 | US |
| NMKS-0732.00/US | Utility - ORG | Issued | MANUFACTURING PROCESS OF AN INTERPOLY DIELECTRIC STRUCTURE FOR NON-VOLATILE SEMICONDUCTOR INTEGRATED MEMORIES | 1/30/2003 | 10/356,351 | 8/1/2006 | 7,084,032 | US |

PATENT

REEL: 029505 FRAME: 0063

Exhibit A - US Issued Patents

| WIPO-No. | MasterType | MasterStatus | Title | FiledDate | SerialNo. | IssuedDate | PatentNo. | Country |
|-----------------|-----------------|--------------|--|------------|------------|------------|-----------|---------|
| NMKS-0733.00/US | Utility - ORG | Issued | MANUFACTURING PROCESS OF A SEMICONDUCTOR NON-VOLATILE MEMORY CELL | 12/18/2002 | 10/323,615 | 8/28/2007 | 7,262,098 | US |
| NMKS-0734.00/US | Utility - ORG | Issued | PROCESS FOR REMOVING POLYMERS DURING THE FABRICATION OF SEMICONDUCTOR DEVICES | 7/2/2002 | 10/189,152 | 4/13/2004 | 6,720,271 | US |
| NMKS-0735.00/US | Utility - ORG | Issued | LOW POWER CHARGE PUMP CIRCUIT | 11/7/2002 | 10/290,030 | 11/9/2004 | 6,816,001 | US |
| NMKS-0736.00/US | Utility - ORG | Issued | CONTENT ADDRESSABLE MEMORY (CAM) WITH BATTERY BACK-UP | 6/29/2001 | 09/895,491 | 12/17/2002 | 6,496,439 | US |
| NMKS-0737.00/US | Utility - ORG | Issued | Data output buffer with precharge | 8/11/2000 | 09/636,363 | 9/18/2001 | 6,292,405 | US |
| NMKS-0738.00/US | Utility - ORG | Issued | INTERLACED MEMORY DEVICE WITH RANDOM OR SEQUENTIAL ACCESS | 10/15/2001 | 09/977,561 | 3/2/2004 | 6,701,419 | US |
| NMKS-0739.00/US | Utility - ORG | Issued | OUTPUT BUFFER AND METHOD OF DRIVING | 8/8/2001 | 09/925,842 | 12/3/2002 | 6,489,807 | US |
| NMKS-0740.00/US | Utility - ORG | Issued | GENERATOR CIRCUIT FOR VOLTAGE RAMPS AND CORRESPONDING VOLTAGE GENERATION METHOD | 12/28/2001 | 10/033,711 | 11/18/2003 | 6,650,133 | US |
| NMKS-0741.00/US | Utility - ORG | Issued | BOOST DEVICE FOR NONVOLATILE MEMORIES WITH AN INTEGRATED STAND-BY CHARGE PUMP | 2/13/2002 | 10/076,134 | 11/18/2003 | 6,650,569 | US |
| NMKS-0742.00/US | Utility - ORG | Abandoned | CHARGE PUMP FOR A NONVOLATILE MEMORY WITH READ VOLTAGE REGULATION IN THE PRESENCE OF ADDRESS SKEW, AND NONVOLATILE MEMORY COMPRISING SUCH A CHARGE PUMP | 2/5/2002 | 10/068,560 | 5/6/2003 | 6,560,145 | US |
| NMKS-0743.00/US | Utility - ORG | Issued | CHARGE AND METHOD FOR TIMING THE READING OF A NONVOLATILE MEMORY WITH REDUCED SWITCHING NOISE | 2/15/2002 | 10/077,687 | 1/6/2004 | 6,674,666 | US |
| NMKS-0744.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR AUTOMATICALLY GENERATING AN APPROPRIATE NUMBER OF WAIT CYCLES WHILE READING A NONVOLATILE MEMORY | 4/3/2002 | 10/115,888 | 7/12/2005 | 6,917,994 | US |
| NMKS-0745.00/US | Utility - ORG | Issued | CIRCUIT FOR GENERATING A PULSE SIGNAL INDEPENDENT OF VOLTAGE AND TEMPERATURE VARIATIONS | 10/31/2001 | 09/998,903 | 4/15/2003 | 6,549,486 | US |
| NMKS-0746.00/US | Utility - ORG | Issued | NEGATIVE CHARGE PUMP ARCHITECTURE WITH SELF-GENERATED BOOSTED PHASES | 10/31/2001 | 09/998,902 | 4/13/2004 | 6,720,822 | US |
| NMKS-0748.00/US | Utility - ORG | Issued | THRESHOLD AMPLIFIER | 8/9/2001 | 09/925,979 | 4/15/2003 | 6,549,048 | US |
| NMKS-0749.00/US | Utility - NSPCT | Issued | ERASEABLE FLASH MEMORY | 11/14/2001 | 10/438,733 | 10/19/2004 | 6,807,103 | US |
| NMKS-0750.00/US | Utility - ORG | Issued | CIRCUIT FOR THE DETECTION OF A DEFECTIVE POWER SUPPLY CONNECTION | 1/29/2002 | 10/060,105 | 8/10/2004 | 6,774,663 | US |
| NMKS-0751.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR SEQUENTIAL READOUT OF A MEMORY WITH ADDRESS LUMP | 2/22/2002 | 10/081,740 | 8/9/2005 | 6,928,530 | US |
| NMKS-0752.00/US | Utility - ORG | Issued | FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES | 11/15/2001 | 09/997,214 | 5/27/2003 | 6,568,510 | US |
| NMKS-0752.00/US | Utility - DIV | Issued | FLASH MEMORY INCLUDING MEANS OF CHECKING MEMORY CELL THRESHOLD VOLTAGES | 1/28/2003 | 10/352,581 | 3/30/2004 | 6,714,453 | US |
| NMKS-0753.00/US | Utility - NSPCT | Issued | CONTRACT LESSIC CARD WITH OPERATING SYSTEM USED IN CONTRACT TYPE CARDS AND READER FOR SUCH CONTACTLESS CARDS | 2/14/2002 | 10/471,883 | 1/16/2007 | 7,163,154 | US |
| NMKS-0754.00/US | Utility - ORG | Issued | FLASH EEPROM AND EPROM ARRAYS WITH SELECT TRANSISTORS WITHIN THE BIT LINE PITCH | 3/11/1994 | 08/212,176 | 9/17/1996 | 5,557,124 | US |
| NMKS-0755.00/US | Utility - ORG | Issued | METHOD OF REPROGRAMMING AN ARRAY OF NON-VOLATILE MEMORY CELLS, IN PARTICULAR OF THE NOR ARCHITECTURE FLASH TYPE, AFTER AN ERASE OPERATION, AND A CORRESPONDING MEMORY DEVICE | 6/12/2002 | 10/171,078 | 11/25/2003 | 6,654,287 | US |
| NMKS-0756.00/US | Utility - ORG | Issued | MEMORY DEVICE | 10/24/2001 | 10/041,684 | 5/20/2003 | 6,567,296 | US |
| NMKS-0757.00/US | Utility - ORG | Issued | WORD LINE SELECTOR FOR A SEMICONDUCTOR MEMORY | 2/20/2003 | 10/372,626 | 3/8/2005 | 6,865,116 | US |
| NMKS-0758.00/US | Utility - ORG | Issued | DESIGN FAILURE MODE EFFECT ANALYSIS (DFMEA) | 12/26/2002 | 10/330,485 | 4/25/2006 | 7,035,769 | US |
| NMKS-0759.00/US | Utility - ORG | Issued | POWER SUPPLY CIRCUIT STRUCTURE FOR A ROW DECODER OF A MULTILEVEL NON-VOLATILE MEMORY DEVICE | 12/30/2002 | 10/334,126 | 12/7/2004 | 6,829,168 | US |
| NMKS-0760.00/US | Utility - ORG | Issued | BINARY ENCODING CIRCUIT | 12/20/2002 | 10/325,707 | 2/24/2004 | 6,636,990 | US |
| NMKS-0761.00/US | Utility - ORG | Issued | REGULATION METHOD FOR THE DRAIN, BODY AND SOURCE TERMINALS VOLTAGES IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT | 12/27/2002 | 10/331,116 | 10/26/2004 | 6,809,961 | US |

PATENT

REEL: 029505 FRAME: 0064

Exhibit A - US Issued Patents

| Pat. No. | Master Type | Master Status | Title | Filed | Serial No. | Issued Date | Patent No. | Country |
|------------------|---------------|---------------|---|------------|------------|-------------|------------|---------|
| NMXXS-0762.00/US | Utility - ORG | Issued | METHOD FOR STORING AND READING DATA IN A MULTILEVEL NONVOLATILE MEMORY, AND ARCHITECTURE THEREOF | 9/26/2002 | 10/259,252 | 11/9/2004 | 6,816,407 | US |
| NMXXS-0762.01/US | Utility - DIV | Issued | MULTILEVEL MEMORY DEVICE WITH MEMORY CELLS STORING NON-POWER OF TWO VOLTAGE LEVELS | 10/12/2004 | 10/964,160 | 11/15/2005 | 6,965,523 | US |
| NMXXS-0763.00/US | Utility - ORG | Issued | ELECTRICALLY-PROGRAMMABLE NON-VOLATILE MEMORY CELL | 2/20/2003 | 10/372,044 | 4/19/2005 | 6,882,001 | US |
| NMXXS-0764.00/US | Utility - ORG | Issued | DECODING STRUCTURE FOR A MEMORY DEVICE WITH A CONTROL CODE | 12/27/2002 | 10/331,177 | 10/25/2005 | 6,958,949 | US |
| NMXXS-0765.00/US | Utility - ORG | Issued | SENSE AMPLIFIER STRUCTURE FOR MULTILEVEL NON-VOLATILE MEMORY DEVICES AND CORRESPONDING READING METHOD | 12/26/2002 | 10/331,158 | 11/23/2004 | 6,822,906 | US |
| NMXXS-0766.00/US | Utility - ORG | Issued | PROCESS FOR FABRICATING A DUAL CHARGE STORAGE LOCATION MEMORY CELL | 11/14/2002 | 10/294,999 | 10/25/2005 | 6,958,510 | US |
| NMXXS-0767.00/US | Utility - ORG | Issued | FINITE STATE MACHINE INTERFACE HAS ARBITRATION STRUCTURE TO STORE COMMAND GENERATED BY INTERNAL CIRCUITS DURING EVALUATION PHASE OF STATE MACHINE FOR FLASH EEPROM DEVICE | 12/4/2002 | 10/309,759 | 10/16/2007 | 7,284,144 | US |
| NMXXS-0768.00/US | Utility - ORG | Issued | SINGLE SUPPLY VOLTAGE, NONVOLATILE PHASE CHANGE MEMORY DEVICE WITH CASCODED COLUMN SELECTION AND SIMULTANEOUS WORD READ/WRITE OPERATIONS | 12/27/2002 | 10/331,185 | 6/22/2004 | 6,754,107 | US |
| NMXXS-0769.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL | 10/7/2002 | 10/267,033 | 11/30/2004 | 6,825,523 | US |
| NMXXS-0769.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING A DUAL CHARGE STORAGE LOCATION MEMORY CELL | 10/12/2004 | 10/964,049 | 10/3/2006 | 7,115,472 | US |
| NMXXS-0770.00/US | Utility - ORG | Issued | ARCHITECTURE FOR A FLASH-EEPROM SIMULTANEOUSLY READABLE IN OTHER SECTORS WHILE ERASING AND/OR PROGRAMMING ONE OR MORE SECTORS | 1/10/2003 | 10/340,207 | 5/10/2005 | 6,891,755 | US |
| NMXXS-0771.00/US | Utility - ORG | Issued | FAST PROGRAMMING METHOD FOR NONVOLATILE MEMORIES, IN PARTICULAR FLASH MEMORIES, AND RELATIVE MEMORY ARCHITECTURE | 10/24/2002 | 10/281,078 | 12/27/2005 | 6,981,107 | US |
| NMXXS-0772.00/US | Utility - ORG | Issued | ARCHITECTURE OF A PHASE-CHANGE NONVOLATILE MEMORY ARRAY | 12/12/2002 | 10/319,439 | 11/9/2004 | 6,816,404 | US |
| NMXXS-0773.00/US | Utility - ORG | Issued | MEMORY SYSTEM COMPRISING A SEMICONDUCTOR MEMORY | 12/12/2003 | 10/735,250 | 5/22/2007 | 7,221,602 | US |
| NMXXS-0774.00/US | Utility - ORG | Issued | SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES WITH ERASING/PROGRAMMING FAILURE, AND RELATIVE NONVOLATILE MEMORY DEVICE | 5/15/2003 | 10/440,043 | 9/13/2005 | 6,944,072 | US |
| NMXXS-0775.00/US | Utility - ORG | Issued | INTEGRATED RESISTOR, PHASE-CHANGE MEMORY ELEMENT INCLUDING THIS RESISTOR, AND PROCESS FOR THE FABRICATION THEREOF | 1/14/2003 | 10/345,129 | 9/20/2005 | 6,946,673 | US |
| NMXXS-0776.00/US | Utility - ORG | Issued | METHOD FOR AVOIDING THE EFFECTS OF LACK OF UNIFORMITY IN TRENCH ISOLATED INTEGRATED CIRCUITS | 11/29/2001 | 09/997,227 | 7/1/2003 | 6,586,313 | US |
| NMXXS-0777.00/US | Utility - ORG | Issued | SMALL AREA CONTACT REGION, HIGH EFFICIENCY PHASE CHANGE MEMORY CELL AND FABRICATION METHOD THEREOF | 12/5/2002 | 10/313,991 | 6/5/2007 | 7,227,171 | US |
| NMXXS-0778.00/US | Utility - ORG | Issued | PROGRAMMING METHOD OF THE MEMORY CELLS IN A MULTILEVEL NON-VOLATILE MEMORY DEVICE | 5/13/2003 | 10/438,175 | 7/19/2005 | 6,920,066 | US |
| NMXXS-0779.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE | 3/14/2003 | 10/390,556 | 12/12/2006 | 7,149,844 | US |
| NMXXS-0780.00/US | Utility - CIP | Issued | PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES | 2/20/2003 | 10/372,761 | 5/10/2005 | 6,891,747 | US |
| NMXXS-0780.01/US | Utility - DIV | Issued | PHASE CHANGE MEMORY CELL AND MANUFACTURING METHOD THEREOF USING MINITRENCHES | 1/27/2005 | 11/045,170 | 8/9/2011 | 7,993,957 | US |
| NMXXS-0782.00/US | Utility - CIP | Issued | SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF | 2/20/2003 | 10/371,154 | 12/6/2005 | 6,972,430 | US |
| NMXXS-0782.01/US | Utility - DIV | Issued | SUBLITHOGRAPHIC CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL WITH OPTIMIZED HEATER SHAPE, AND MANUFACTURING METHOD THEREOF | 10/24/2005 | 11/258,340 | 5/13/2008 | 7,372,166 | US |
| NMXXS-0783.00/US | Utility - CIP | Issued | CONTACT STRUCTURE, PHASE CHANGE MEMORY CELL, AND MANUFACTURING METHOD THEREOF WITH ELIMINATION OF DOUBLE CONTACTS | 2/20/2003 | 10/372,639 | 8/16/2005 | 6,930,913 | US |

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Exhibit A - US Issued Patents

| NIMXS-0783.00/US | Utility - DIV | Issued | MANUFACTURING METHOD OF A CONTACT STRUCTURE AND PHASE CHANGE MEMORY CELL WITH ELIMINATION OF DOUBLE CONTACTS | 6/20/2005 | 11/156,989 | 7/22/2008 | 7,402,455 | US |
|------------------|---------------|-----------|--|------------|------------|------------|-----------|----|
| NIMXS-0784.00/US | Utility - ORG | Issued | BASIC STAGE FOR A CHARGE PUMP CIRCUIT | 3/28/2003 | 10/402,852 | 2/21/2006 | 7,002,399 | US |
| NIMXS-0785.00/US | Utility - ORG | Issued | ELECTRICALLY ERASABLE AND PROGRAMMABLE NON-VOLATILE MEMORY CELL | 6/25/2003 | 10/606,164 | 4/5/2005 | 6,876,033 | US |
| NIMXS-0786.00/US | Utility - ORG | Issued | PROGRAMMING METHOD FOR A MULTILEVEL MEMORY CELL | 12/26/2002 | 10/331,161 | 8/8/2006 | 7,088,614 | US |
| NIMXS-0787.00/US | Utility - ORG | Issued | ADJUSTABLE FREQUENCY OSCILLATOR WITH PROGRAMMABLE CALIBRATING CIRCUIT AND RELATED SYSTEM AND METHOD | 4/2/2003 | 10/406,628 | 4/19/2005 | 6,882,231 | US |
| NIMXS-0788.00/US | Utility - ORG | Issued | TEST STRUCTURE FOR THE MEASUREMENT OF CONTACT TO GATE DISTANCE IN NON-VOLATILE MEMORY DEVICES AND CORRESPONDING TEST METHOD | 5/30/2003 | 10/449,761 | 6/7/2005 | 6,903,995 | US |
| NIMXS-0789.00/US | Utility - ORG | Abandoned | METHOD FOR MANUFACTURING ELECTRONIC CIRCUITS INTEGRATED ON A SEMICONDUCTOR SUBSTRATE | 5/1/2003 | 10/428,338 | 2/14/2006 | 6,998,348 | US |
| NIMXS-0790.00/US | Utility - ORG | Issued | SINGLE ENDED OUTPUT SENSE AMPLIFIER CIRCUIT WITH REDUCED POWER CONSUMPTION AND NOISE | 7/8/2002 | 10/190,917 | 11/23/2004 | 6,822,919 | US |
| NIMXS-0791.00/US | Utility - ORG | Issued | REDUNDANCY CIRCUIT AND METHOD FOR SEMICONDUCTOR MEMORY DEVICES | 5/31/2002 | 10/161,501 | 5/4/2004 | 6,731,550 | US |
| NIMXS-0792.00/US | Utility - ORG | Issued | CIRCUIT FOR CONTROLLING A REFERENCE NODE IN A SENSE AMPLIFIER | 12/27/2002 | 10/331,147 | 10/5/2004 | 6,801,466 | US |
| NIMXS-0793.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY DEVICE WITH DOUBLE SERIAL/PARALLEL COMMUNICATION INTERFACE | 10/15/2002 | 10/271,352 | 5/10/2005 | 6,892,269 | US |
| NIMXS-0794.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY WITH SELF-REFRESH CAPABILITY | 3/11/2003 | 10/387,141 | 5/8/2007 | 7,216,212 | US |
| NIMXS-0796.00/US | Utility - ORG | Issued | MEMORY DEVICE OUTPUTTING READ DATA IN A TIME STARTING FROM A RISING EDGE OF AN EXTERNAL CLOCK THAT IS SHORTER THAN THAT OF KNOWN DEVICES | 12/19/2002 | 10/325,486 | 1/24/2006 | 6,990,596 | US |
| NIMXS-0797.00/US | Utility - ORG | Issued | DEVICE INTEGRATING A NONVOLATILE MEMORY ARRAY AND A VOLATILE MEMORY ARRAY | 2/7/2003 | 10/360,840 | 5/23/2006 | 7,050,322 | US |
| NIMXS-0798.00/US | Utility - ORG | Issued | METHOD OF WRITING A GROUP OF DATA BYTES IN A MEMORY AND MEMORY DEVICE | 2/21/2003 | 10/371,221 | 2/7/2006 | 6,996,697 | US |
| NIMXS-0799.00/US | Utility - ORG | Issued | NONVOLATILE STORAGE DEVICE AND SELF-REDUNDANCY METHOD FOR THE SAME | 8/11/2003 | 10/639,240 | 4/8/2008 | 7,355,908 | US |
| NIMXS-0800.00/US | Utility - ORG | Issued | BUILT-IN TESTING METHODOLOGY IN FLASH MEMORY | 2/27/2004 | 10/789,443 | 5/23/2006 | 7,050,343 | US |
| NIMXS-0801.00/US | Utility - ORG | Issued | SECTOR PROTECTION CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES | 8/2/2001 | 09/922,043 | 12/3/2002 | 6,490,197 | US |
| NIMXS-0802.00/US | Utility - ORG | Issued | DUAL BANK FLASH MEMORY DEVICE AND METHOD | 8/2/2001 | 09/922,044 | 4/22/2003 | 6,552,935 | US |
| NIMXS-0803.00/US | Utility - ORG | Issued | REDUNDANCY CIRCUIT AND METHOD FOR FLASH MEMORY DEVICES | 8/2/2001 | 09/922,068 | 5/13/2003 | 6,563,732 | US |
| NIMXS-0804.00/US | Utility - ORG | Issued | REDUNDANCY CIRCUIT AND METHOD FOR REPLACING DEFECTIVE MEMORY CELLS IN A FLASH MEMORY DEVICE | 8/2/2001 | 09/922,176 | 7/15/2003 | 6,594,177 | US |
| NIMXS-0805.00/US | Utility - ORG | Issued | CIRCUIT AND ASSOCIATED METHOD FOR THE ERASURE OR PROGRAMMING OF A MEMORY CELL | 3/11/2002 | 10/096,531 | 9/16/2003 | 6,621,737 | US |
| NIMXS-0806.00/US | Utility - ORG | Issued | EEPROM MEMORY COMPRISING MEANS FOR SIMULTANEOUS READING OF SPECIAL BITS OF A FIRST AND SECOND TYPE | 10/21/2002 | 10/277,183 | 5/18/2004 | 6,738,286 | US |
| NIMXS-0807.00/US | Utility - ORG | Issued | EEPROM MEMORY PROTECTED AGAINST THE EFFECTS FROM A BREAKDOWN OF AN ACCESS TRANSISTOR | 6/24/2002 | 10/178,796 | 8/23/2005 | 6,934,192 | US |
| NIMXS-0808.00/US | Utility - ORG | Issued | READ AMPLIFIER WITH A LOW CURRENT CONSUMPTION DIFFERENTIAL OUTPUT STAGE | 11/19/2002 | 10/299,965 | 7/6/2004 | 6,760,265 | US |
| NIMXS-0809.00/US | Utility - ORG | Issued | METHOD FOR ERASING NON-VOLATILE MEMORY CELLS AND CORRESPONDING MEMORY DEVICE | 9/30/2003 | 10/675,221 | 2/27/2007 | 7,184,319 | US |
| NIMXS-0810.00/US | Utility - ORG | Issued | NON-VOLATILE LATCH CIRCUIT | 5/7/2003 | 10/434,395 | 4/18/2006 | 7,031,189 | US |
| NIMXS-0811.00/US | Utility - ORG | Issued | METHOD FOR REDUCING SPURIOUS ERASING DURING PROGRAMMING OF A NONVOLATILE NROM | 4/29/2003 | 10/426,924 | 11/30/2004 | 6,826,083 | US |
| NIMXS-0812.00/US | Utility - CIP | Issued | METHOD FOR POST ETCH CLEANS | 5/1/2002 | 10/137,096 | 6/24/2008 | 7,390,755 | US |

PATENT

REEL: 029505 FRAME: 0066

Exhibit A - US Issued Patents

| Patent No. | Patent Type | Patent Status | Title | Filed Date | Serial No. | Inventor | Priority No. | Country |
|-----------------|---------------|---------------|---|------------|------------|------------|--------------|---------|
| NMKS-0813.00/US | Utility - ORG | Issued | REGULATION METHOD FOR THE SOURCE TERMINAL VOLTAGE IN A NON-VOLATILE MEMORY CELL DURING A PROGRAM PHASE AND CORRESPONDING PROGRAM CIRCUIT | 12/27/2002 | 10/331,106 | 11/23/2004 | 6,822,905 | US |
| NMKS-0815.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING SEMICONDUCTOR INTEGRATED CIRCUIT STRUCTURES | 7/30/2003 | 10/631,463 | 1/16/2007 | 7,163,898 | US |
| NMKS-0816.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR WITH VERY QUICK RESPONSE | 6/26/2003 | 10/608,998 | 6/21/2005 | 6,909,264 | US |
| NMKS-0817.00/US | Utility - ORG | Issued | ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF | 10/7/2003 | 10/680,727 | 11/14/2006 | 7,135,756 | US |
| NMKS-0817.01/US | Utility - DIV | Issued | ARRAY OF CELLS INCLUDING A SELECTION BIPOLAR TRANSISTOR AND FABRICATION METHOD THEREOF | 10/19/2006 | 11/551,170 | 11/14/2008 | 7,446,011 | US |
| NMKS-0818.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS | 10/7/2003 | 10/680,721 | 1/24/2006 | 6,989,580 | US |
| NMKS-0818.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING AN ARRAY OF CELLS INCLUDING SELECTION BIPOLAR JUNCTION TRANSISTORS | 11/1/2005 | 11/264,084 | 7/21/2009 | 7,563,684 | US |
| NMKS-0819.00/US | Utility - ORG | Issued | SELF-REPAIR METHOD VIA ECC FOR NONVOLATILE MEMORY DEVICES, AND RELATIVE NONVOLATILE MEMORY DEVICE | 4/15/2003 | 10/417,416 | 5/31/2005 | 6,901,011 | US |
| NMKS-0820.00/US | Utility - ORG | Issued | SELF-REPAIR METHOD FOR NONVOLATILE MEMORY DEVICES USING A SUPERSECURE ARCHITECTURE AND NONVOLATILE MEMORY DEVICE | 4/24/2003 | 10/423,845 | 7/26/2005 | 6,922,366 | US |
| NMKS-0821.00/US | Utility - ORG | Issued | LINE SELECTOR FOR A MATRIX OF MEMORY ELEMENTS | 7/8/2003 | 10/616,414 | 8/16/2005 | 6,930,927 | US |
| NMKS-0822.00/US | Utility - ORG | Issued | MANUFACTURING PROCESS FOR A HIGH VOLTAGE TRANSISTOR INTEGRATED ON A SEMICONDUCTOR SUBSTRATE WITH NON-VOLATILE MEMORY CELLS AND CORRESPONDING TRANSISTOR | 9/29/2003 | 10/675,245 | 9/27/2005 | 6,949,803 | US |
| NMKS-0823.00/US | Utility - ORG | Issued | PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE | 11/18/2003 | 10/715,887 | 12/6/2005 | 6,972,454 | US |
| NMKS-0823.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING A BYTE SELECTION TRANSISTOR FOR A MATRIX OF NON VOLATILE MEMORY CELLS AND CORRESPONDING STRUCTURE | 10/25/2005 | 11/258,675 | 11/25/2008 | 7,456,467 | US |
| NMKS-0824.00/US | Utility - ORG | Issued | ION-IMPLANTATION MACHINE, CONTROL METHOD THEREOF, AND PROCESS FOR MANUFACTURING INTEGRATED DEVICES | 9/8/2003 | 10/657,801 | 6/13/2006 | 7,060,995 | US |
| NMKS-0826.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY | 12/5/2003 | 10/729,875 | 4/18/2006 | 7,031,193 | US |
| NMKS-0827.00/US | Utility - ORG | Issued | CIRCUIT FOR PROGRAMMING A NON-VOLATILE MEMORY DEVICE WITH ADAPTIVE PROGRAM LOAD CONTROL | 11/12/2003 | 10/706,306 | 10/18/2005 | 6,956,773 | US |
| NMKS-0828.00/US | Utility - ORG | Issued | SINGLE CELL ERASING METHOD FOR RECOVERING MEMORY CELLS UNDER PROGRAMMING DISTURBS IN NON VOLATILE SEMICONDUCTOR MEMORY DEVICES | 11/26/2003 | 10/724,022 | 9/13/2005 | 6,944,061 | US |
| NMKS-0829.00/US | Utility - ORG | Issued | CIRCUIT FOR BIASING AN INPUT NODE OF A SENSE AMPLIFIER WITH A PRE-CHARGE STAGE | 9/16/2003 | 10/664,606 | 2/15/2005 | 6,856,547 | US |
| NMKS-0830.00/US | Utility - ORG | Issued | INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION | 9/26/2003 | 10/672,293 | 2/13/2007 | 7,176,553 | US |
| NMKS-0830.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING INTEGRATED RESISTIVE ELEMENTS WITH SILICIDATION PROTECTION | 1/30/2006 | 11/343,593 | 7/28/2009 | 7,566,610 | US |
| NMKS-0831.00/US | Utility - ORG | Issued | SELF-ALIGNED INTEGRATED ELECTRONIC DEVICES | 11/14/2003 | 10/713,538 | 12/23/2008 | 7,468,535 | US |
| NMKS-0831.01/US | Utility - DIV | Issued | PROCESS FOR SELF-ALIGNED MANUFACTURE OF INTEGRATED ELECTRONIC DEVICES | 1/4/2008 | 12/006,706 | 8/10/2010 | 7,772,084 | US |
| NMKS-0832.00/US | Utility - ORG | Issued | VOLTAGE BOOST DEVICE AND MEMORY SYSTEM | 7/7/2003 | 10/614,693 | 12/28/2004 | 6,836,442 | US |
| NMKS-0833.00/US | Utility - ORG | Issued | METHOD OF PROGRAMMING A MULTI-LEVEL, ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY | 2/19/2004 | 10/782,725 | 9/19/2006 | 7,110,300 | US |
| NMKS-0834.00/US | Utility - ORG | Issued | STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY | 12/18/2003 | 10/741,815 | 1/13/2009 | 7,478,292 | US |

PATENT

REEL: 029505 FRAME: 0067

Exhibit A - US Issued Patents

| Multi-Entry No | Market Type | Master Status | Title | Filed Date | Serial No | Issued Date | Patent No | Country |
|-----------------|---------------|---------------|--|------------|------------|-------------|-----------|---------|
| NMMS-0834.00/US | Utility - DIV | Issued | STRUCTURE AND METHOD FOR DETECTING ERRORS IN A MULTILEVEL MEMORY DEVICE WITH IMPROVED PROGRAMMING GRANULARITY | 10/14/2008 | 12/251,289 | 6/1/2010 | 7,730,383 | US |
| NMMS-0835.00/US | Utility - ORG | Issued | METHOD FOR CONTROLLING PROGRAMMING VOLTAGE LEVELS OF NON-VOLATILE MEMORY CELLS, THE METHOD TRACKING THE CELL FEATURES, AND CORRESPONDING VOLTAGE REGULATOR | 8/28/2003 | 10/651,019 | 11/22/2005 | 6,967,876 | US |
| NMMS-0836.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY SYSTEM INCLUDING SELECTION TRANSISTORS | 12/24/2003 | 10/746,555 | 4/4/2006 | 7,023,728 | US |
| NMMS-0837.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR TIMING RANDOM READING OF A MEMORY DEVICE | 11/3/2003 | 10/700,322 | 10/18/2005 | 6,956,787 | US |
| NMMS-0838.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE WITH IMPROVED SEQUENTIAL PROGRAMMING SPEED | 12/18/2003 | 10/739,928 | 9/6/2005 | 6,940,756 | US |
| NMMS-0839.00/US | Utility - ORG | Issued | MEMORY DEVICE COMPOSED OF A PLURALITY OF MEMORY CHIPS IN A SINGLE PACKAGE | 12/3/2003 | 10/727,150 | 9/27/2005 | 6,950,324 | US |
| NMMS-0840.00/US | Utility - ORG | Issued | NONVOLATILE MEMORY DEVICE WITH SIMULTANEOUS READ/WRITE | 11/21/2003 | 10/719,650 | 9/27/2005 | 6,950,337 | US |
| NMMS-0842.00/US | Utility - ORG | Issued | NON VOLATILE MEMORY DEVICE INCLUDING A PREDETERMINED NUMBER OF SECTORS | 12/30/2003 | 10/748,696 | 4/25/2006 | 7,035,142 | US |
| NMMS-0843.00/US | Utility - ORG | Issued | PROGRAMMING METHOD FOR NON VOLATILE MULTILEVEL MEMORY CELLS AND CORRESPONDING PROGRAMMING CIRCUIT | 11/26/2003 | 10/724,023 | 8/23/2005 | 6,934,185 | US |
| NMMS-0844.00/US | Utility - ORG | Issued | STABILIZATION METHOD FOR DRAIN VOLTAGE IN NON-VOLATILE MULTI-LEVEL MEMORY CELLS AND RELATED MEMORY DEVICE | 12/30/2003 | 10/748,701 | 4/18/2006 | 7,031,191 | US |
| NMMS-0845.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY WITH ACCESS PROTECTION SCHEME | 2/18/2004 | 10/781,974 | 7/24/2007 | 7,249,231 | US |
| NMMS-0849.00/US | Utility - ORG | Issued | ANALYSIS OF THE QUALITY OF CONTACTS AND VIAS IN MULTI-METAL FABRICATION PROCESSES OF SEMICONDUCTOR DEVICES, METHOD AND TEST CHIP ARCHITECTURE | 5/21/2004 | 10/850,834 | 12/4/2007 | 7,304,485 | US |
| NMMS-0850.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTIVE SUBSTRATE | 12/29/2003 | 10/749,020 | 10/24/2006 | 7,125,808 | US |
| NMMS-0851.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING NON-VOLATILE MEMORY CELLS ON A SEMICONDUCTOR SUBSTRATE | 12/23/2003 | 10/746,878 | 10/24/2006 | 7,125,807 | US |
| NMMS-0853.00/US | Utility - ORG | Issued | METHOD FOR DETECTING A RESISTIVE PATH OR A PREDETERMINED POTENTIAL IN NON-VOLATILE MEMORY ELECTRONIC DEVICES | 9/30/2003 | 10/675,805 | 9/20/2005 | 6,947,329 | US |
| NMMS-0854.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY CELL SENSING CIRCUIT, PARTICULARLY FOR LOW POWER SUPPLY VOLTAGES AND HIGH CAPACITIVE LOAD VALUES | 12/4/2003 | 10/728,372 | 5/17/2005 | 6,894,934 | US |
| NMMS-0855.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY WITH EMBEDDED DRAM | 11/20/2003 | 10/729,013 | 4/11/2006 | 7,027,317 | US |
| NMMS-0857.00/US | Utility - ORG | Issued | REUNDANCY SCHEME FOR A MEMORY INTEGRATED CIRCUIT | 7/16/2004 | 10/893,760 | 12/26/2006 | 7,154,803 | US |
| NMMS-0858.00/US | Utility - ORG | Issued | FULL-SWING WORMLINE DRIVING CIRCUIT | 4/29/2004 | 10/835,538 | 4/4/2006 | 7,023,738 | US |
| NMMS-0859.00/US | Utility - ORG | Issued | METHOD FOR GENERATING A REFERENCE CURRENT FOR SENSE AMPLIFIERS AND CORRESPONDING GENERATOR | 6/4/2004 | 10/861,340 | 2/28/2006 | 7,006,025 | US |
| NMMS-0860.00/US | Utility - ORG | Issued | METHOD AND DEVICE FOR PROGRAMMING AN ELECTRICALLY PROGRAMMABLE NON-VOLATILE SEMICONDUCTOR MEMORY | 12/5/2003 | 10/729,829 | 6/27/2006 | 7,068,540 | US |
| NMMS-0861.00/US | Utility - ORG | Issued | HIGH-DENSITY PLASMA PROCESS FOR DEPOSITING A LAYER OF SILICON NITRIDE | 10/14/2003 | 10/686,556 | 10/11/2005 | 6,953,609 | US |
| NMMS-0862.00/US | Utility - ORG | Issued | SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS | 2/12/2004 | 10/777,457 | 3/24/2009 | 7,508,716 | US |
| NMMS-0862.01/US | Utility - CON | Issued | SENSE AMPLIFIER FOR LOW-SUPPLY-VOLTAGE NONVOLATILE MEMORY CELLS | 2/9/2009 | 12/368,271 | 2/8/2011 | 7,885,116 | US |
| NMMS-0863.00/US | Utility - ORG | Issued | VOLTAGE SUPPLY DISTRIBUTION ARCHITECTURE FOR A PLURALITY OF MEMORY MODULES | 12/30/2003 | 10/748,697 | 5/24/2005 | 6,897,710 | US |
| NMMS-0864.00/US | Utility - ORG | Issued | NONLITHOGRAPHIC METHOD OF DEFINING GEOMETRIES FOR PLASMA AND/OR ION IMPLANTATION TREATMENTS ON A SEMICONDUCTOR WAFER | 3/25/2005 | 11/089,942 | 10/30/2007 | 7,288,008 | US |
| NMMS-0865.00/US | Utility - ORG | Issued | PARALLEL SENSE AMPLIFIER WITH MIRRORING OF THE CURRENT TO BE MEASURED INTO EACH REFERENCE BRANCH | 1/20/2004 | 10/762,195 | 7/11/2006 | 7,075,844 | US |
| NMMS-0866.00/US | Utility - ORG | Issued | METHOD FOR THE FABRICATION OF ISOLATION STRUCTURES | 8/21/2004 | 10/909,749 | 5/8/2007 | 7,214,596 | US |
| NMMS-0869.00/US | Utility - ORG | Issued | MOS DEVICE AND PROCESS FOR MANUFACTURING MOS DEVICES USING DUAL-POLYSILICON LAYER TECHNOLOGY | 12/23/2003 | 10/745,295 | 4/4/2006 | 7,023,047 | US |

PATENT

REEL: 029505 FRAME: 0068

Exhibit A - US Issued Patents

| NMXX-XXXX.XX/US | Matter Type | Matter Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|-----------------|---------------|---|------------|------------|------------|------------|---------|
| NMXX-0870.00/US | Utility - ORG | Issued | MOS DEVICE AND A PROCESS FOR MANUFACTURING MOS DEVICES USING A DUAL-POLYSILICON LAYER TECHNOLOGY WITH SIDE CONTACT | 12/23/2003 | 10/745,297 | 8/15/2006 | 7,091,570 | US |
| NMXX-0871.00/US | Utility - ORG | Issued | FAST READING, LOW CONSUMPTION MEMORY DEVICE AND READING METHOD THEREOF | 12/20/2004 | 11/018,550 | 4/10/2007 | 7,203,087 | US |
| NMXX-0872.00/US | Utility - ORG | Issued | METHOD FOR READING A NONVOLATILE MEMORY DEVICE AND NONVOLATILE MEMORY DEVICE IMPLEMENTING THE READING METHOD | 4/8/2004 | 10/820,458 | 5/30/2006 | 7,054,197 | US |
| NMXX-0873.00/US | Utility - ORG | Issued | TESTING METHOD AND DEVICE FOR NON-VOLATILE MEMORIES HAVING A LPC (LOW PIN COUNT) COMMUNICATION SERIAL INTERFACE | 5/28/2003 | 10/447,293 | 8/31/2004 | 6,785,174 | US |
| NMXX-0874.00/US | Utility - ORG | Issued | DEVICE AND METHOD FOR READING NON-VOLATILE MEMORIES HAVING AT LEAST ONE PSEUDO-PARALLEL COMMUNICATION INTERFACE | 5/30/2003 | 10/452,762 | 12/13/2005 | 6,975,559 | US |
| NMXX-0875.00/US | Utility - ORG | Issued | AUTOMATIC DECODING METHOD FOR MAPPING AND SELECTING A NON-VOLATILE MEMORY DEVICE HAVING A LPC SERIAL COMMUNICATION INTERFACE IN THE AVAILABLE ADDRESSING AREA ON MOTHERBOARDS | 7/18/2003 | 10/623,474 | 6/12/2007 | 7,231,487 | US |
| NMXX-0876.00/US | Utility - ORG | Issued | STRUCTURE FOR UPDATING A BLOCK OF MEMORY CELLS IN A FLASH MEMORY DEVICE WITH ERASE AND PROGRAM OPERATION REDUCTION | 10/15/2003 | 10/686,552 | 7/26/2005 | 6,922,362 | US |
| NMXX-0877.00/US | Utility - ORG | Issued | VOLTAGE REGULATION SYSTEM FOR A MULTWORD PROGRAMMING OF A LOW INTEGRATION AREA NON VOLATILE MEMORY | 2/26/2004 | 10/789,351 | 11/21/2006 | 7,139,197 | US |
| NMXX-0878.00/US | Utility - ORG | Issued | GATE VOLTAGE REGULATION SYSTEM FOR A NON VOLATILE MEMORY CELLS PROGRAMMING AND/OR SOFT PROGRAMMING PHASE | 2/26/2004 | 10/788,525 | 8/1/2006 | 7,085,163 | US |
| NMXX-0879.00/US | Utility - ORG | Issued | METHOD FOR SOFT-PROGRAMMING AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE, AND AN ELECTRICALLY ERASABLE NONVOLATILE MEMORY DEVICE IMPLEMENTING THE SOFT-PROGRAMMING METHOD | 2/17/2004 | 10/779,856 | 10/10/2006 | 7,120,062 | US |
| NMXX-0880.00/US | Utility - ORG | Issued | MEMORY DEVICE ACCESSIBLE WITH DIFFERENT COMMUNICATION PROTOCOLS | 9/2/2003 | 10/653,459 | 8/9/2005 | 6,927,991 | US |
| NMXX-0881.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE ARCHITECTURE, FOR INSTANCE A FLASH KIND, HAVING A SERIAL COMMUNICATION INTERFACE | 11/26/2003 | 10/727,341 | 12/19/2006 | 7,151,705 | US |
| NMXX-0882.00/US | Utility - ORG | Issued | FAST PAGE PROGRAMMING ARCHITECTURE AND METHOD IN A NON-VOLATILE MEMORY DEVICE WITH AN SPI INTERFACE | 12/30/2003 | 10/748,447 | 4/26/2005 | 6,885,584 | US |
| NMXX-0883.00/US | Utility - ORG | Issued | ELECTRICALLY ERASABLE AND PROGRAMMABLE MEMORY COMPRISING AN INTERNAL SUPPLY VOLTAGE MANAGEMENT DEVICE | 4/22/2003 | 10/420,533 | 12/7/2004 | 6,829,169 | US |
| NMXX-0884.00/US | Utility - ORG | Issued | PROGRAMMABLE FOR CIRCUIT WITH TWO SWITCHING THRESHOLDS | 8/14/2003 | 10/641,337 | 5/24/2005 | 6,897,689 | US |
| NMXX-0885.00/US | Utility - NSPCT | Issued | EEPROM MEMORY COMPRISING A NON-VOLATILE REGISTER INTEGRATED INTO THE MEMORY ARRAY THEREOF | 8/21/2003 | 11/067,345 | 11/21/2006 | 7,139,195 | US |
| NMXX-0886.00/US | Utility - ORG | Issued | DOUBLE READ STAGE SENSE AMPLIFIER | 4/1/2004 | 10/816,204 | 4/18/2006 | 7,031,212 | US |
| NMXX-0887.00/US | Utility - ORG | Issued | MANUFACTURING PROCESS FOR A FLASH MEMORY AND FLASH MEMORY THUS PRODUCED | 1/22/2004 | 10/763,044 | 2/27/2007 | 7,183,160 | US |
| NMXX-0888.00/US | Utility - ORG | Issued | FLASH MEMORY COMPRISING AN ERASE VERIFY ALGORITHM INTEGRATED INTO A PROGRAMMING ALGORITHM | 2/26/2004 | 10/789,449 | 5/10/2005 | 6,891,756 | US |
| NMXX-0889.00/US | Utility - ORG | Issued | NEGATIVE VOLTAGE WORD LINE DECODER HAVING COMPACT TERMINATING ELEMENTS | 1/20/2004 | 10/760,631 | 5/16/2006 | 7,046,577 | US |
| NMXX-0890.00/US | Utility - ORG | Issued | SECTORED FLASH MEMORY COMPRISING MEANS FOR CONTROLLING AND FOR REFRESHING MEMORY CELLS | 2/9/2004 | 10/775,032 | 11/15/2005 | 6,965,526 | US |
| NMXX-0891.00/US | Utility - ORG | Issued | METHOD FOR ERASING/PROGRAMMING A NON-VOLATILE ELECTRICALLY ERASABLE MEMORY | 7/31/2004 | 10/903,927 | 3/14/2006 | 7,012,837 | US |
| NMXX-0892.00/US | Utility - ORG | Issued | WORD-PROGRAMMABLE FLASH MEMORY | 6/14/2004 | 10/867,381 | 7/18/2006 | 7,079,448 | US |
| NMXX-0893.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING DIFFERENTIAL ISOLATION STRUCTURES IN A SEMICONDUCTOR ELECTRONIC DEVICE AND CORRESPONDING STRUCTURE | 7/12/2004 | 10/890,529 | 10/26/2010 | 7,820,504 | US |
| NMXX-0894.00/US | Utility - ORG | Issued | CHARGE PUMP CIRCUIT WITH A BRIEF SETTLING TIME AND HIGH OUTPUT VOLTAGE REGULATION PRECISION | 11/5/2004 | 10/982,528 | 2/13/2007 | 7,176,748 | US |

PATENT

REEL: 029505 FRAME: 0069

Exhibit A - US Issued Patents

| WIPO Class | Material | Material Status | Title | Filing Date | Serial No. | Issue Date | Patent No. | Country |
|------------------|---------------|-----------------|--|-------------|------------|------------|------------|---------|
| NMXXS-0895.00/US | Utility - ORG | Issued | METHOD FOR REDUCING NON-UNIFORMITY OR TOPOGRAPHY VARIATION BETWEEN AN ARRAY AND CIRCUITRY IN A PROCESS FOR MANUFACTURING SEMICONDUCTOR INTEGRATED NON-VOLATILE MEMORY DEVICES | 2/16/2005 | 11/059,294 | 3/20/2007 | 7,192,820 | US |
| NMXXS-0896.00/US | Utility - ORG | Issued | EXPLOITING A STATISTICAL DISTRIBUTION OF THE VALUES OF AN ELECTRICAL CHARACTERISTIC IN A POPULATION OF AUXILIARY MEMORY CELLS FOR OBTAINING REFERENCE CELLS | 12/23/2005 | 11/318,053 | 12/8/2009 | 7,630,263 | US |
| NMXXS-0897.00/US | Utility - ORG | Issued | SENSE AMPLIFIER WITH EQUALIZER | 8/6/2004 | 10/913,788 | 11/14/2006 | 7,136,305 | US |
| NMXXS-0898.00/US | Utility - ORG | Issued | METHOD FOR REDUCING DEFECTS AFTER A METAL ETCHING IN SEMICONDUCTOR DEVICES | 12/10/2004 | 11/009,687 | 10/30/2007 | 7,288,427 | US |
| NMXXS-0899.00/US | Utility - ORG | Issued | METHOD FOR PERFORMING ERROR CORRECTIONS OF DIGITAL INFORMATION CODED AS A SYMBOL SEQUENCE | 3/19/2004 | 10/805,168 | 2/5/2008 | 7,328,397 | US |
| NMXXS-0900.00/US | Utility - ORG | Issued | INTEGRATED MEMORY SYSTEM | 3/19/2004 | 10/805,182 | 6/1/2010 | 7,730,357 | US |
| NMXXS-0901.00/US | Utility - ORG | Issued | PHASE CHANGE MEMORY DEVICE WITH BIASING OF DESELECTED BIT LINES | 8/25/2004 | 10/926,784 | 8/15/2006 | 7,092,277 | US |
| NMXXS-0902.00/US | Utility - ORG | Issued | MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT | 8/3/2004 | 10/911,220 | 2/21/2006 | 7,001,800 | US |
| NMXXS-0902.01/US | Utility - DIV | Issued | MANUFACTURING METHOD FOR NON-ACTIVE ELECTRICALLY STRUCTURES IN ORDER TO OPTIMIZE THE DEFINITION OF ACTIVE ELECTRICALLY STRUCTURES IN AN ELECTRONIC CIRCUIT INTEGRATED ON A SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT | 1/19/2006 | 11/334,988 | 1/22/2008 | 7,320,904 | US |
| NMXXS-0903.00/US | Utility - ORG | Issued | SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE | 10/22/2004 | 10/971,774 | 7/18/2006 | 7,078,294 | US |
| NMXXS-0904.00/US | Utility - ORG | Issued | SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY | 8/6/2004 | 10/913,128 | 9/18/2007 | 7,272,059 | US |
| NMXXS-0905.00/US | Utility - ORG | Issued | 8BIT LINE DISCHARGE CONTROL METHOD AND CIRCUIT FOR A SEMICONDUCTOR MEMORY | 10/22/2004 | 10/971,776 | 8/14/2007 | 7,257,039 | US |
| NMXXS-0906.00/US | Utility - ORG | Issued | SENSING CIRCUIT FOR A SEMICONDUCTOR MEMORY | 8/3/2005 | 11/194,739 | 2/27/2007 | 7,184,348 | US |
| NMXXS-0908.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE | 12/27/2005 | 11/319,798 | 9/2/2008 | 7,419,876 | US |
| NMXXS-0910.00/US | Utility - ORG | Issued | DISTRIBUTION OF AN ELECTRIC QUANTITY THROUGH A CIRCUIT | 7/29/2005 | 11/185,905 | 4/21/2009 | 7,521,989 | US |
| NMXXS-0912.00/US | Utility - ORG | Issued | PAGE BUFFER CIRCUIT AND METHOD FOR A PROGRAMMABLE MEMORY DEVICE | 6/24/2005 | 11/166,354 | 7/28/2009 | 7,567,456 | US |
| NMXXS-0913.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY DEVICE WITH INFORMATION LOSS SELF-DETECT CAPABILITY | 5/1/2006 | 11/415,879 | 8/19/2008 | 7,414,902 | US |
| NMXXS-0914.00/US | Utility - ORG | Issued | NONVOLATILE PHASE CHANGE MEMORY DEVICE AND BIASING METHOD THEREFOR | 8/2/2005 | 11/195,359 | 9/11/2007 | 7,269,080 | US |
| NMXXS-0916.00/US | Utility - ORG | Issued | PHASE CHANGE MEMORY CELL WITH JUNCTION SELECTOR AND MANUFACTURING METHOD THEREOF | 12/19/2005 | 11/312,253 | 10/14/2008 | 7,436,692 | US |
| NMXXS-0917.00/US | Utility - ORG | Issued | READ/VERIFY CIRCUIT FOR MULTILEVEL MEMORY CELLS WITH RAMP READ VOLTAGE, AND READ/VERIFY METHOD THEREOF | 7/8/2005 | 11/178,240 | 7/8/2008 | 7,397,702 | US |
| NMXXS-0919.00/US | Utility - ORG | Issued | METHOD OF MAKING A FLOATING GATE NON-VOLATILE MOS SEMICONDUCTOR MEMORY DEVICE WITH IMPROVED CAPACITIVE COUPLING AND DEVICE THUS OBTAINED | 12/22/2005 | 11/317,641 | 8/30/2011 | 8,008,701 | US |
| NMXXS-0920.00/US | Utility - ORG | Issued | PROGRAMMABLE NAND MEMORY | 7/14/2005 | 11/183,229 | 6/8/2010 | 7,733,697 | US |
| NMXXS-0921.00/US | Utility - ORG | Issued | DATA CONTROL UNIT CAPABLE OF CORRECTING BOOT ERRORS, AND CORRESPONDING SELF-CORRECTION METHOD | 6/9/2005 | 11/149,948 | 10/28/2008 | 7,444,543 | US |
| NMXXS-0923.00/US | Utility - ORG | Issued | TRIMMING FUNCTIONAL PARAMETERS IN INTEGRATED CIRCUITS | 4/25/2005 | 11/113,818 | 5/22/2007 | 7,221,212 | US |
| NMXXS-0924.00/US | Utility - ORG | Issued | METHOD FOR MANUFACTURING ELECTRONIC NON-VOLATILE MEMORY DEVICES INTEGRATED IN A SEMICONDUCTOR SUBSTRATE | 12/27/2005 | 11/319,750 | 2/5/2008 | 7,326,615 | US |

PATENT

REEL: 029505 FRAME: 0070

Exhibit A - US Issued Patents

| Patent No. | Member Types | Member Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|---|------------|------------|------------|------------|---------|
| NMKS-0928.00/US | Utility - ORG | Issued | FLASH MEMORY DEVICE WITH NAND ARCHITECTURE WITH REDUCED CAPACITIVE COUPLING EFFECT | 4/11/2006 | 11/445,491 | 7/1/2008 | 7,394,694 | US |
| NMKS-0929.00/US | Utility - ORG | Issued | INTEGRATED ELECTRONIC DEVICE HAVING A LOW VOLTAGE ELECTRIC SUPPLY REGULATOR CIRCUITRY AND METHOD | 10/27/2003 | 10/695,523 | 11/30/2009 | 7,616,515 | US |
| NMKS-0930.00/US | Utility - ORG | Issued | MAGNITUDE CONTENT ADDRESSABLE MEMORY | 10/21/2003 | 10/695,594 | 6/20/2006 | 7,064,534 | US |
| NMKS-0931.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR WITH STRESS MODE | 10/21/2003 | 10/690,368 | 6/12/2007 | 7,230,839 | US |
| NMKS-0932.00/US | Utility - ORG | Issued | USER RAM FLASH CLEAR | 2/27/2004 | 10/789,332 | 3/14/2006 | 7,012,417 | US |
| NMKS-0933.00/US | Utility - ORG | Issued | RESET INITIALIZATION | 11/30/2004 | 10/788,581 | 2/6/2007 | 7,133,845 | US |
| NMKS-0934.00/US | Utility - ORG | Issued | TAMPER MEMORY CELL | 2/20/2004 | 10/999,751 | 4/24/2007 | 7,208,987 | US |
| NMKS-0935.00/US | Utility - ORG | Issued | RESET RAMP CONTROL | 12/15/2004 | 10/783,935 | 5/29/2007 | 7,224,600 | US |
| NMKS-0936.00/US | Utility - ORG | Issued | ESD BONDING PAD | 12/15/2004 | 11/012,693 | 8/12/2008 | 7,411,433 | US |
| NMKS-0937.00/US | Utility - ORG | Issued | VOLTAGE TRANSLATING CONTROL STRUCTURE | 12/15/2004 | 11/013,123 | 2/19/2008 | 7,333,310 | US |
| NMKS-0938.00/US | Utility - ORG | Issued | RESET CIRCUIT | 12/15/2004 | 11/012,533 | 5/6/2008 | 7,368,947 | US |
| NMKS-0939.00/US | Abandoned | Abandoned | SENSE AMPLIFIER FOR READING A CELL OF A NON-VOLATILE MEMORY DEVICE | 5/4/2005 | 11/121,516 | 1/23/2007 | 7,167,394 | US |
| NMKS-0940.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR VERIFYING AND EVENTUALLY SUBSTITUTING DEFECTIVE REFERENCE CELLS OF A MEMORY | 5/4/2005 | 11/121,515 | 2/13/2007 | 7,177,217 | US |
| NMKS-0941.00/US | Utility - ORG | Issued | CIRCUIT FOR SELECTING/DESELECTING A BITLINE OF A NON-VOLATILE MEMORY | 5/3/2005 | 11/120,766 | 8/7/2007 | 7,254,062 | US |
| NMKS-0943.01/US | Utility - CON | Issued | METHOD FOR MANAGING BAD MEMORY BLOCKS IN A NONVOLATILE-MEMORY DEVICE AND NONVOLATILE-MEMORY DEVICE IMPLEMENTING THE MANAGEMENT METHOD | 2/19/2008 | 12/033,855 | 10/13/2009 | 7,603,593 | US |
| NMKS-0944.00/US | Utility - ORG | Issued | ROW DECODER FOR NAND MEMORIES | 8/13/2005 | 11/202,632 | 2/20/2007 | 7,180,786 | US |
| NMKS-0945.00/US | Utility - ORG | Issued | METHOD OF GENERATING AN ENABLE SIGNAL OF A STANDARD MEMORY CORE AND RELATIVE MEMORY DEVICE | 7/7/2004 | 10/886,003 | 4/14/2009 | 7,519,751 | US |
| NMKS-0946.00/US | Utility - ORG | Issued | INTEGRATED MEMORY DEVICE WITH MULTI-SECTOR SELECTION COMMANDS | 11/8/2004 | 10/984,372 | 11/25/2008 | 7,457,908 | US |
| NMKS-0947.00/US | Utility - ORG | Issued | SYNCHRONOUS MEMORY DEVICE WITH REDUCED POWER CONSUMPTION | 5/29/2005 | 11/138,884 | 4/29/2008 | 7,366,012 | US |
| NMKS-0948.00/US | Utility - ORG | Issued | FLASH MEMORY COMPRISING MEANS FOR CHECKING AND REFRESHING MEMORY CELLS IN THE ERASED STATE | 6/14/2004 | 10/867,378 | 5/23/2006 | 7,050,335 | US |
| NMKS-0949.00/US | Utility - ORG | Issued | MEMORY CIRCUIT WITH NON-VOLATILE IDENTIFICATION MEMORY AND ASSOCIATED METHOD | 8/18/2004 | 10/921,365 | 6/27/2006 | 7,068,538 | US |
| NMKS-0950.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR A CONTINUOUS READ COMMAND IN AN EXTENDED MEMORY ARRAY | 12/9/2004 | 11/008,586 | 2/12/2008 | 7,330,381 | US |
| NMKS-0952.00/US | Utility - ORG | Issued | SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION | 12/9/2004 | 11/008,588 | 10/30/2007 | 7,290,078 | US |
| NMKS-0953.00/US | Utility - DIV | Issued | SERIAL MEMORY COMPRISING MEANS FOR PROTECTING AN EXTENDED MEMORY ARRAY DURING A WRITE OPERATION | 9/10/2007 | 11/852,937 | 9/7/2010 | 7,793,033 | US |
| NMKS-0954.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH UNIPOLAR AND BIPOLAR SELECTORS | 9/22/2005 | 11/233,464 | 1/27/2009 | 7,483,296 | US |
| NMKS-0957.00/US | Utility - ORG | Issued | ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING A NAND STRUCTURE AND BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR | 4/11/2006 | 11/401,521 | 3/9/2010 | 7,675,788 | US |
| NMKS-0958.00/US | Utility - ORG | Issued | MEMORY DEVICE | 10/13/2005 | 11/249,763 | 3/27/2007 | 7,196,943 | US |
| NMKS-0959.00/US | Utility - ORG | Issued | CHANGE-PUMP DEVICE WITH INCREASED CURRENT OUTPUT | 11/9/2005 | 11/270,308 | 5/12/2009 | 7,532,060 | US |
| NMKS-0961.00/US | Utility - ORG | Issued | INTEGRATED ELECTRONIC NON-VOLATILE MEMORY DEVICE HAVING NAND STRUCTURE | 4/11/2006 | 11/279,384 | 11/13/2007 | 7,295,472 | US |
| NMKS-0963.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR | 4/11/2006 | 11/279,378 | 9/25/2007 | 7,274,594 | US |
| NMKS-0964.00/US | Utility - ORG | Issued | PROGRAMMING METHOD OF MULTILEVEL MEMORIES AND CORRESPONDING CIRCUIT | 10/27/2005 | 11/261,903 | 1/8/2008 | 7,317,637 | US |
| NMKS-0965.00/US | Utility - ORG | Issued | MEMORY DEVICE | 10/13/2005 | 11/250,176 | 4/1/2008 | 7,352,645 | US |
| NMKS-0965.00/US | Utility - ORG | Issued | MEMORY DEVICE AND METHOD FOR OPERATING THE SAME WITH HIGH REJECTION OF THE NOISE ON THE HIGH-VOLTAGE SUPPLY LINE | 9/30/2005 | 11/241,729 | 1/29/2008 | 7,324,379 | US |

PATENT

REEL: 029505 FRAME: 0071

Exhibit A - US Issued Patents

| INT-Office | MarketType | MarketStatus | Title | FiledDate | SerialNo | IssueDate | PatentNo | Country |
|------------------|---------------|--------------|---|------------|------------|------------|-----------|---------|
| NMXXS-0966.00/US | Utility - ORG | Issued | ELECTRONIC MEMORY DEVICE HAVING HIGH DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE INTERFERENCE CELL-TO-CELL | 12/14/2005 | 11/300,053 | 1/15/2008 | 7,319,604 | US |
| NMXXS-0968.00/US | Utility - ORG | Issued | ROW DECODER CIRCUIT AND RELATED SYSTEM AND METHOD | 5/15/2006 | 11/434,564 | 4/28/2009 | 7,525,851 | US |
| NMXXS-0969.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY ELECTRONIC DEVICE WITH NAND STRUCTURE BEING MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR | 4/11/2006 | 11/279,381 | 7/8/2008 | 7,397,700 | US |
| NMXXS-0971.00/US | Utility - ORG | Issued | FLASH MEMORY DEVICE WITH REDUCED DRAIN STRESSES | 2/6/2007 | 11/703,535 | 5/19/2009 | 7,535,770 | US |
| NMXXS-0972.00/US | Utility - ORG | Issued | REMOVABLE DATA STORAGE DEVICE AND RELATED ASSEMBLING METHOD | 1/31/2006 | 11/344,519 | 2/2/2010 | 7,656,676 | US |
| NMXXS-0974.00/US | Utility - ORG | Issued | METHOD FOR CONFIGURING A VOLTAGE REGULATOR | 11/16/2005 | 11/280,803 | 6/17/2008 | 7,388,793 | US |
| NMXXS-0974.01/US | Utility - DIV | Issued | VOLTAGE REGULATOR FOR THE PROGRAMMING CIRCUIT OF A MEMORY CELL | 12/26/2007 | 11/964,250 | 4/27/2010 | 7,706,193 | US |
| NMXXS-0975.00/US | Utility - ORG | Issued | PROCESS FOR DIGGING A DEEP TRENCH IN A SEMICONDUCTOR BODY AND SEMICONDUCTOR BODY SO OBTAINED | 12/28/2006 | 11/648,838 | 6/9/2009 | 7,544,620 | US |
| NMXXS-0976.00/US | Utility - ORG | Issued | METHOD AND SYSTEM FOR CONTROLLING MRAM WRITE CURRENT TO REDUCE POWER CONSUMPTION | 3/31/2004 | 10/816,271 | 9/19/2006 | 7,110,289 | US |
| NMXXS-0977.00/US | Utility - ORG | Issued | MAGNETIC MEMORY CELL WITH PLURAL READ TRANSISTORS | 10/31/2003 | 10/698,747 | 3/14/2006 | 7,012,832 | US |
| NMXXS-0978.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE THE LATERAL COUPLING EFFECTS BETWEEN MEMORY CELLS | 2/6/2006 | 11/348,513 | 12/30/2008 | 7,473,571 | US |
| NMXXS-0979.00/US | Utility - ORG | Issued | DUAL RESISTANCE HEATER FOR PHASE CHANGE DEVICES AND MANUFACTURING METHOD THEREOF | 12/19/2005 | 11/312,231 | 2/1/2011 | 7,880,123 | US |
| NMXXS-0983.00/US | Utility - ORG | Issued | HIGH-VOLTAGE SWITCH WITH LOW OUTPUT RIPPLE FOR NON-VOLATILE FLOATING-GATE MEMORIES | 5/19/2006 | 11/437,405 | 4/21/2009 | 7,521,983 | US |
| NMXXS-0984.00/US | Utility - ORG | Issued | CHARGE-PUMP TYPE VOLTAGE-BOOSTING DEVICE WITH REDUCED RIPPLE, IN PARTICULAR FOR NON-VOLATILE FLASH MEMORIES | 5/19/2006 | 11/437,268 | 5/12/2009 | 7,532,061 | US |
| NMXXS-0985.00/US | Utility - ORG | Issued | PHASE CHANGE MEMORY CELL WITH TUBULAR HEATER AND MANUFACTURING METHOD THEREOF | 4/6/2006 | 11/398,858 | 10/21/2008 | 7,439,536 | US |
| NMXXS-0986.00/US | Utility - ORG | Issued | ELECTRONIC MEMORY DEVICE HAVING HIGH INTEGRATION DENSITY NON-VOLATILE MEMORY CELLS AND A REDUCED CAPACITIVE COUPLING | 12/14/2005 | 11/300,145 | 9/22/2009 | 7,593,247 | US |
| NMXXS-0987.00/US | Utility - ORG | Issued | METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR | 11/20/2006 | 11/561,799 | 5/5/2009 | 7,529,881 | US |
| NMXXS-0987.01/US | Utility - DIV | Issued | METHOD FOR ACCESSING IN READING, WRITING AND PROGRAMMING TO A NAND NON-VOLATILE MEMORY ELECTRONIC DEVICE MONOLITHICALLY INTEGRATED ON SEMICONDUCTOR | 3/24/2009 | 12/409,740 | 1/19/2010 | 7,649,778 | US |
| NMXXS-0988.00/US | Utility - ORG | Issued | VERTICAL MOSFET TRANSISTOR, IN PARTICULAR OPERATING AS A SELECTOR IN NONVOLATILE MEMORY DEVICES | 4/26/2006 | 11/411,982 | 12/7/2010 | 7,847,329 | US |
| NMXXS-0989.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY IMPLEMENTED WITH LOW-VOLTAGES TRANSISTORS AND RELATED SYSTEM AND METHOD | 11/27/2006 | 11/605,209 | 3/3/2009 | 7,499,345 | US |
| NMXXS-0990.00/US | Utility - ORG | Issued | CONTROL OF VOLTAGES DURING ERASE AND RE-PROGRAM OPERATIONS OF MEMORY CELLS | 1/18/2006 | 11/334,205 | 10/30/2007 | 7,289,368 | US |
| NMXXS-0991.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE BASED ON A CURRENT GENERATOR | 1/26/2006 | 11/340,414 | 4/15/2008 | 7,359,246 | US |
| NMXXS-0992.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR RETRIEVING DATA STORED IN SEMICONDUCTOR MEMORY CELLS | 5/31/2006 | 11/444,892 | 1/6/2009 | 7,474,577 | US |
| NMXXS-0992.01/US | Utility - DIV | Issued | CIRCUIT AND METHOD FOR RETRIEVING DATA STORED IN SEMICONDUCTOR MEMORY CELLS | 10/9/2008 | 12/748,843 | 2/1/2011 | 7,889,586 | US |
| NMXXS-0993.00/US | Utility - ORG | Issued | DATA STORING METHOD FOR A NON-VOLATILE MEMORY CELL ARRAY HAVING AN ERROR CORRECTION CODE | 4/25/2006 | 11/411,010 | 1/26/2010 | 7,653,863 | US |
| NMXXS-0995.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH A RAMP-LIKE VOLTAGE BIASING STRUCTURE AND REDUCED NUMBER OF REFERENCE CELLS | 3/3/2006 | 11/368,363 | 6/30/2009 | 7,554,861 | US |
| NMXXS-0996.00/US | Utility - ORG | Issued | METHOD OF MANAGING FAILS IN A NON-VOLATILE MEMORY DEVICE AND RELATIVE MEMORY DEVICE | 11/8/2006 | 11/557,786 | 8/4/2009 | 7,571,362 | US |

PATENT

REEL: 029505 FRAME: 0072

Exhibit A - US Issued Patents

| Patent No. | MetType | MetStatus | Title | FiledDate | SerialNo. | IssueDate | PatentNo. | Country |
|------------------|-----------------|-----------|---|------------|------------|------------|-----------|---------|
| NMXXS-0997.00/US | Utility - NSPCT | Issued | METHOD FOR MULTILEVEL PROGRAMMING OF PHASE CHANGE MEMORY CELLS USING A PERCOLATION ALGORITHM | 6/1/2006 | 11/949,598 | 12/29/2009 | 7,639,526 | US |
| NMXXS-0998.00/US | Utility - ORG | Issued | FLASH MEMORY DEVICE WITH IMPROVED MANAGEMENT OF PROTECTION INFORMATION | 5/10/2006 | 11/432,301 | 7/20/2010 | 7,761,675 | US |
| NMXXS-0999.00/US | Utility - ORG | Issued | NAND FLASH MEMORY WITH ERASE VERIFY BASED ON SHORTER EVALUATION TIME TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY | 7/28/2006 | 11/495,886 | 4/22/2008 | 7,362,616 | US |
| NMXXS-1000.00/US | Utility - ORG | Issued | TRANSISTOR STRUCTURE WITH HIGH INPUT IMPEDANCE AND HIGH CURRENT CAPABILITY | 11/27/2006 | 11/605,190 | 7/14/2009 | 7,560,782 | US |
| NMXXS-1001.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH TIME-SHIFTING BASED EMULATION OF REFERENCE CELLS | 3/2/2006 | 11/367,707 | 3/18/2008 | 7,345,905 | US |
| NMXXS-1002.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING A MEMORY DEVICE SUITABLE TO MINIMIZE FLOATING GATE COUPLING AND MEMORY DEVICE | 4/2/2007 | 11/732,486 | 3/30/2010 | 7,688,633 | US |
| NMXXS-1003.00/US | Utility - ORG | Issued | NON VOLATILE MEMORY DEVICE ARCHITECTURE AND CORRESPONDING PROGRAMMING METHOD | 2/28/2007 | 11/713,081 | 1/19/2010 | 7,649,791 | US |
| NMXXS-1004.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE WITH MULTIPLE REFERENCES AND CORRESPONDING CONTROL METHOD | 7/27/2006 | 11/460,531 | 1/12/2010 | 7,646,644 | US |
| NMXXS-1006.00/US | Utility - ORG | Issued | RAMP GENERATOR AND RELATIVE ROW DECODER FOR FLASH MEMORY DEVICE | 5/3/2006 | 11/381,426 | 1/22/2008 | 7,321,512 | US |
| NMXXS-1007.00/US | Utility - ORG | Issued | RAMP GENERATOR AND RELATIVE ROW DECODER FOR FLASH MEMORY DEVICE | 5/3/2006 | 11/381,426 | 1/22/2008 | 7,321,512 | US |
| NMXXS-1008.00/US | Utility - ORG | Issued | ROW SELECTOR WITH REDUCED AREA OCCUPATION FOR SEMICONDUCTOR MEMORY DEVICES | 2/8/2007 | 11/672,857 | 6/1/2011 | 7,965,561 | US |
| NMXXS-1009.00/US | Utility - ORG | Issued | BUILT-IN SELF TEST FOR A COUNTER SYSTEM | 3/10/2005 | 11/076,785 | 12/13/2005 | 6,975,696 | US |
| NMXXS-1009.00/US | Utility - ORG | Issued | READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE | 9/28/2005 | 11/238,137 | 7/10/2007 | 7,242,619 | US |
| NMXXS-1009.01/US | Utility - CON | Issued | READING CIRCUIT AND METHOD FOR A NONVOLATILE MEMORY DEVICE | 6/8/2007 | 11/811,394 | 11/11/2008 | 7,450,428 | US |
| NMXXS-1010.00/US | Utility - ORG | Issued | SELF-ADAPTIVE OUTPUT BUFFER BASED ON CHARGE SHARING | 7/7/2006 | 11/482,524 | 9/8/2009 | 7,586,331 | US |
| NMXXS-1011.00/US | Utility - ORG | Issued | CIRCUIT FOR GENERATING AN INTERNAL ENABLING SIGNAL FOR AN OUTPUT BUFFER OF A MEMORY | 1/20/2006 | 11/337,030 | 5/19/2009 | 7,535,774 | US |
| NMXXS-1014.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR SIMULTANEOUSLY PROGRAMMING MEMORY CELLS | 4/13/2006 | 11/279,663 | 12/4/2007 | 7,304,896 | US |
| NMXXS-1016.00/US | Utility - ORG | Issued | SEQUENTIAL PROGRAM-VERIFY METHOD WITH RESULT BUFFERING | 3/29/2005 | 11/093,012 | 2/27/2007 | 7,184,310 | US |
| NMXXS-1017.00/US | Utility - ORG | Issued | OPTIMIZING WRITE/ERASE OPERATIONS IN MEMORY DEVICES | 1/13/2005 | 11/035,013 | 4/22/2008 | 7,363,421 | US |
| NMXXS-1018.00/US | Utility - ORG | Issued | CONTROLLING OPERATION OF FLASH MEMORIES | 1/14/2005 | 11/036,179 | 11/25/2008 | 7,457,909 | US |
| NMXXS-1026.00/US | Utility - ORG | Issued | MEMORY ARCHITECTURE | 9/14/2006 | 11/469,754 | 7/28/2009 | 7,567,475 | US |
| NMXXS-1033.00/US | Utility - ORG | Issued | MEMORY ARCHITECTURE WITH SERIAL PERIPHERAL INTERFACE | 9/8/2006 | 11/530,199 | 9/7/2010 | 7,793,031 | US |
| NMXXS-1038.00/US | Utility - ORG | Issued | VOLTAGE REGULATOR OR NON-VOLATILE MEMORIES IMPLEMENTED WITH LOW-VOLTAGE TRANSISTORS | 8/24/2007 | 11/844,470 | 8/17/2010 | 7,777,466 | US |
| NMXXS-1040.00/US | Utility - ORG | Issued | READING CIRCUIT FOR SEMICONDUCTOR MEMORY | 4/27/2007 | 11/740,941 | 3/24/2009 | 7,508,717 | US |
| NMXXS-1043.00/US | Utility - ORG | Issued | SENSING CIRCUIT FOR SEMICONDUCTOR MEMORIES | 4/24/2007 | 11/739,167 | 4/7/2009 | 7,515,493 | US |
| NMXXS-1044.00/US | Utility - ORG | Issued | ELECTRONIC DEVICE CONTAINING SEMICONDUCTOR POLYMERS AND CORRESPONDING MANUFACTURING PROCESS | 1/30/2007 | 11/700,541 | 10/18/2011 | 8,039,831 | US |
| NMXXS-1046.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY DEVICE WITH A PAGE BUFFER HAVING AN IMPROVED LAYOUT ARRANGEMENT | 7/25/2006 | 11/459,831 | 8/5/2008 | 7,408,819 | US |
| NMXXS-1047.00/US | Utility - ORG | Issued | REDUCTION OF THE TIME FOR EXECUTING AN EXTERNALLY COMMANDED TRANSFER OF DATA IN AN INTEGRATED DEVICE | 3/16/2007 | 11/687,353 | 7/28/2009 | 7,567,107 | US |
| NMXXS-1048.00/US | Utility - ORG | Issued | SYNCHRONIZATION OF OPERATIONS IN DISTINCT MEMORY PARTITIONS | 3/14/2007 | 11/686,133 | 4/7/2009 | 7,515,464 | US |
| NMXXS-1050.00/US | Utility - ORG | Issued | OPTIMIZED FLASH MEMORY ACCESS METHOD AND DEVICE | 4/13/2007 | 11/787,101 | 9/6/2011 | 8,015,945 | US |
| NMXXS-1052.00/US | Utility - ORG | Issued | METHOD AND CIRCUIT FOR PROGRAMMING A MEMORY CELL, IN PARTICULAR OF THE NOR FLASH TYPE | 4/16/2008 | 12/104,118 | 2/2/2010 | 7,656,712 | US |
| NMXXS-1053.00/US | Utility - ORG | Issued | HIGH VOLTAGE GENERATOR OF THE DAC-CONTROLLED TYPE | 8/8/2006 | 11/463,260 | 4/27/2010 | 7,706,160 | US |

PATENT

REEL: 029505 FRAME: 0073

Exhibit A - US Issued Patents

| Patent No. | Metes/Type | Patent Status | Title | Filed Date | Serial No. | Issue Date | Patent No. | Country |
|-----------------|---------------|---------------|---|------------|------------|------------|------------|---------|
| NMMS-1054.00/US | Utility - ORG | Issued | READING METHOD OF A MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE AND MEMORY DEVICE WITH EMBEDDED ERROR-CORRECTING CODE | 3/1/2007 | 11/713,376 | 3/15/2011 | 7,908,543 | US |
| NMMS-1055.00/US | Utility - ORG | Issued | FAST PROGRAMMING MEMORY DEVICE | 5/19/2008 | 12/123,359 | 9/13/2011 | 8,018,771 | US |
| NMMS-1056.00/US | Utility - ORG | Issued | OUTPUT BUFFER | 12/13/2006 | 11/638,321 | 12/9/2008 | 7,463,051 | US |
| NMMS-1056.01/US | Utility - DIV | Issued | REFERENCE CELL LAYOUT WITH ENHANCED RTN IMMUNITY | 10/30/2008 | 12/261,101 | 9/28/2010 | 7,804,322 | US |
| NMMS-1062.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE | 4/27/2007 | 11/741,462 | 6/23/2009 | 7,551,465 | US |
| NMMS-1066.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE | 10/12/2006 | 11/549,067 | 1/27/2009 | 7,483,300 | US |
| NMMS-1067.00/US | Utility - ORG | Issued | METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE | 12/8/2006 | 11/636,382 | 10/20/2009 | 7,606,078 | US |
| NMMS-1067.01/US | Utility - DIV | Issued | METHOD FOR PROGRAMMING OF MEMORY CELLS, IN PARTICULAR OF THE FLASH TYPE, AND CORRESPONDING PROGRAMMING ARCHITECTURE | 9/20/2009 | 12/556,970 | 5/17/2011 | 7,944,751 | US |
| NMMS-1068.00/US | Utility - ORG | Issued | AUTOMATIC REGULATION METHOD FOR THE REFERENCE SOURCES IN A NON-VOLATILE MEMORY DEVICE AND CORRESPONDING MEMORY DEVICE | 6/29/2007 | 11/771,677 | 7/28/2009 | 7,567,470 | US |
| NMMS-1070.00/US | Utility - ORG | Issued | METHOD FOR ACCESSING A MULTILEVEL NONVOLATILE MEMORY DEVICE OF THE FLASH NAND TYPE | 7/20/2006 | 11/458,904 | 6/3/2008 | 7,382,660 | US |
| NMMS-1071.00/US | Utility - ORG | Issued | CONFIGURATION OF A MULTILEVEL FLASH MEMORY DEVICE | 7/28/2006 | 11/460,777 | 5/3/2011 | 7,937,576 | US |
| NMMS-1075.00/US | Utility - ORG | Issued | ELECTRONIC DEVICE COMPRISING NON VOLATILE MEMORY CELLS WITH OPTIMIZED PROGRAMMING AND CORRESPONDING PROGRAMMING METHOD | 2/28/2007 | 11/713,074 | 3/31/2009 | 7,512,032 | US |
| NMMS-1079.00/US | Utility - CIP | Issued | SEALING METHOD FOR ELECTRONIC DEVICES FORMED ON A COMMON SEMICONDUCTOR SUBSTRATE AND CORRESPONDING CIRCUIT STRUCTURE | 7/17/2006 | 11/457,966 | 8/12/2008 | 7,410,872 | US |
| NMMS-1084.00/US | Utility - ORG | Issued | METHOD FOR COMPACTING THE ERASED THRESHOLD VOLTAGE DISTRIBUTION OF FLASH MEMORY DEVICES DURING WRITING OPERATIONS | 8/24/2007 | 11/844,480 | 5/5/2009 | 7,529,136 | US |
| NMMS-1085.00/US | Utility - ORG | Issued | CIRCUIT AND METHOD FOR ELECTRICALLY PROGRAMMING A NON-VOLATILE | 6/21/2007 | 11/766,493 | 3/3/2009 | 7,499,332 | US |
| NMMS-1089.00/US | Utility - ORG | Issued | METHOD OF MANAGING A MULTILEVEL MEMORY DEVICE AND RELATED DEVICE | 4/25/2008 | 12/109,525 | 5/4/2010 | 7,710,772 | US |
| NMMS-1090.00/US | Utility - ORG | Issued | METHOD OF MANAGING A MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS | 2/28/2008 | 12/039,268 | 8/24/2010 | 7,782,665 | US |
| NMMS-1091.00/US | Utility - ORG | Issued | MEMORY DEVICE EMPLOYING THREE-LEVEL CELLS AND RELATED METHODS OF MANAGING | 11/2/2007 | 11/934,144 | 9/29/2009 | 7,596,023 | US |
| NMMS-1093.00/US | Utility - ORG | Issued | MEMORY DEVICE WITH FAIL SEARCH AND REDUNDANCY | 7/20/2007 | 11/780,581 | 1/12/2010 | 7,546,655 | US |
| NMMS-1094.00/US | Utility - ORG | Issued | NON-VOLATILE MEMORY DEVICE AND METHOD OF HANDLING A DATUM READ FROM A MEMORY CELL | 8/3/2007 | 11/833,400 | 5/12/2009 | 7,532,512 | US |
| NMMS-1095.00/US | Utility - ORG | Issued | ADDRESS COUNTER FOR NONVOLATILE MEMORY DEVICE | 7/27/2007 | 11/829,527 | 7/7/2009 | 7,558,152 | US |
| NMMS-1104.01/US | Utility - CON | Expired | REDUCED-BREAK PLANOX PROCESS FOR THE FORMATION OF INTEGRATED ELECTRONIC COMPONENTS | 11/23/1987 | 07/124,440 | 1/30/1990 | 4,897,365 | US |
| NMMS-1105.01/US | Utility - DIV | Expired | A METHOD FOR MANUFACTURING MOS/CMOS MONOLITHIC INTEGRATED CIRCUITS INCLUDING SILICIDE AND POLYSILICON PATTERNING | 12/15/1988 | 07/289,391 | 11/6/1990 | 4,968,645 | US |
| NMMS-1106.00/US | Utility - ORG | Expired | ELECTRICALLY ALTERABLE, NONVOLATILE FLOATING GATE MEMORY DEVICE | 5/27/1987 | 07/054,712 | 4/18/1989 | 4,823,175 | US |
| NMMS-1107.00/US | Utility - ORG | Expired | NONVOLATILE, SEMICONDUCTOR MEMORY DEVICE | 6/22/1987 | 07/064,480 | 3/28/1989 | 4,816,883 | US |
| NMMS-1108.00/US | Utility - ORG | Expired | GENERATOR OF RESET PULSES UPON THE RISE OF THE POWER SUPPLY FOR CMOS-TYPE INTEGRATED CIRCUITS | 4/28/1988 | 07/187,581 | 12/19/1989 | 4,888,497 | US |
| NMMS-1109.00/US | Utility - ORG | Expired | PROCESS FOR MANUFACTURING CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTHS | 12/14/1988 | 07/284,272 | 11/6/1990 | 4,968,639 | US |
| NMMS-1110.00/US | Utility - ORG | Expired | CIRCUIT FOR SENSING THE STATE OF MATRIX CELLS IN MOS EPROM MEMORIES INCLUDING AN OFFSET CURRENT GENERATOR | 1/18/1989 | 07/298,487 | 8/14/1990 | 4,949,307 | US |
| NMMS-1111.00/US | Utility - ORG | Expired | CMOS VOLTAGE MULTIPLIER | 6/28/1989 | 07/372,493 | 5/1/1990 | 4,922,402 | US |
| NMMS-1112.00/US | Utility - ORG | Expired | CMOS LOGIC CIRCUIT FOR HIGH VOLTAGE OPERATION | 6/30/1989 | 07/373,203 | 9/11/1990 | 4,956,569 | US |
| NMMS-1113.00/US | Utility - ORG | Expired | FABRICATION OF CMOS DEVICES WITH REDUCED GATE LENGTH | 7/18/1989 | 07/381,283 | 1/22/1991 | 4,987,088 | US |
| NMMS-1114.00/US | Utility - ORG | Expired | FABRICATION OF CMOS INTEGRATED DEVICES WITH REDUCED GATE LENGTH AND LIGHTLY DOPED DRAIN | 7/28/1989 | 07/386,189 | 3/5/1991 | 4,997,782 | US |

PATENT

REEL: 029505 FRAME: 0074

Exhibit A - US Issued Patents

| App. No. | Market Type | Market Status | Title | Filed Date | Serial No. | Issued Date | Payment No. | Country |
|-----------------|----------------|---------------|---|------------|------------|-------------|-------------|---------|
| NMKS-1115.00/US | Utility - ORG | Expired | GRIPPER FOR THE ADVANTAGEOUSLY ROBOTIZED HANDLING OF ONE OR MORE PROGRAMMABLE LOGIC DEVICE HAVING A PLURALITY OF PROGRAMMABLE LOGIC ARRAYS ARRANGED IN A MOSAIC LAYOUT TOGETHER WITH A PLURALITY OF INTERMINGLINGLY ARRANGED INTERFACING BLOCKS | 12/5/1989 | 07/446,196 | 10/8/1991 | 5,054,834 | US |
| NMKS-1116.00/US | Utility - ORG | Expired | METHOD OF MANUFACTURING INTEGRATED CIRCUITS HAVING ELECTRONIC COMPONENTS OF TWO DIFFERENT TYPES EACH HAVING PAIRS OF ELECTRODES OBTAINED FROM THE SAME POLYCRYSTALLINE SILICON LAYERS AND SEPARATED BY DIFFERENT DIELECTRIC MATERIALS | 12/27/1989 | 07/456,782 | 2/12/1991 | 4,992,680 | US |
| NMKS-1117.00/US | Utility - ORG | Expired | VOLTAGE BOOSTED PHASE OSCILLATOR FOR DRIVING A VOLTAGE MULTIPLIER | 12/13/1990 | 07/625,764 | 12/24/1991 | 5,075,246 | US |
| NMKS-1118.00/US | Utility - ORG | Expired | SENSE CIRCUIT FOR READING DATA STORED IN NONVOLATILE MEMORY CELLS | 2/4/1991 | 07/655,049 | 3/17/1992 | 5,097,226 | US |
| NMKS-1119.00/RE | Utility - REIS | Abandoned | READING CIRCUIT FOR NONVOLATILE MEMORY CELL | 6/8/1995 | 08/488,718 | 6/8/1993 | RE36,579 | US |
| NMKS-1119.00/US | Utility - ORG | Abandoned | METHOD FOR ADJUSTING THE THRESHOLD OF A READ-ONLY MEMORY TO ACHIEVE LOW CAPACITANCE AND HIGH BREAKDOWN VOLTAGE | 2/19/1991 | 07/657,083 | 6/8/1993 | 5,218,570 | US |
| NMKS-1120.00/US | Utility - CIP | Issued | METHOD FOR CARRYING OUT A BOOLEAN OPERATION BETWEEN ANY TWO BITS OF ANY TWO REGISTERS | 10/19/1993 | 08/139,800 | 1/23/1996 | 5,486,487 | US |
| NMKS-1121.02/US | Utility - CON | Issued | DATA OUTPUT STAGE HAVING FEEDBACK LOOPS TO PRECHARGE THE OUTPUT NODE | 12/27/1994 | 08/364,505 | 8/12/1997 | 5,657,484 | US |
| NMKS-1122.00/US | Utility - ORG | Expired | READING DEVICE FOR EPROM MEMORY CELLS WITH THE OPERATIONAL FIELD INDEPENDENT OF THE THRESHOLD JUMP OF THE WRITTEN CELLS WITH RESPECT TO THE VIRGIN CELLS | 4/28/1991 | 07/691,768 | 1/12/1993 | 5,179,300 | US |
| NMKS-1123.00/US | Utility - ORG | Expired | METHOD FOR FORMATION OF CONTACT PLUGS UTILIZING ETCHBACK | 7/5/1991 | 07/725,987 | 11/30/1993 | 5,267,202 | US |
| NMKS-1124.00/US | Utility - ORG | Expired | MONOSTABILIZED DYNAMIC PROGRAMMABLE LOGIC ARRAY IN CMOS TECHNOLOGY | 10/1/1991 | 07/769,600 | 7/27/1993 | 5,231,051 | US |
| NMKS-1125.00/US | Utility - CON | Expired | TWO PHASES SCAN PATH WITH SINGLECLOCK | 10/30/1992 | 07/970,609 | 12/28/1993 | 5,274,282 | US |
| NMKS-1126.00/US | Utility - ORG | Abandoned | OPERATIONAL ANALYSIS DEVICE OF THE SCAN PATH TYPE HAVING A SINGLE SCANNING CLOCK AND A SINGLE OUTPUT PHASE FOR AN INTEGRATED CIRCUIT | 10/22/1991 | 07/781,360 | 7/6/1993 | 5,225,724 | US |
| NMKS-1126.00/RE | Utility - REIS | Expired | COMPENSATED SENSE CIRCUIT FOR STORAGE DEVICES | 6/23/1997 | 08/876,130 | 7/6/1993 | RE36,292 | US |
| NMKS-1127.00/US | Utility - ORG | Expired | SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES WITH COMPENSATED OFFSET CURRENT | 11/13/1991 | 07/791,973 | 1/25/1994 | 5,287,169 | US |
| NMKS-1128.00/US | Utility - ORG | Expired | SENSE CIRCUIT FOR STORAGE DEVICES SUCH AS NON-VOLATILE MEMORIES, WITH ENHANCED SENSING DISCRIMINATION | 11/13/1991 | 07/791,453 | 1/4/1994 | 5,276,644 | US |
| NMKS-1129.00/US | Utility - ORG | Expired | FAST CAPACITIVE-LOAD DRIVING CIRCUIT PARTICULARLY MEMORIES | 12/12/1991 | 07/806,118 | 12/14/1993 | 5,270,590 | US |
| NMKS-1130.00/US | Utility - ORG | Expired | MEMORY CELL READING CIRCUIT | 12/20/1991 | 07/811,323 | 2/1/1994 | 5,283,478 | US |
| NMKS-1131.00/US | Utility - ORG | Expired | CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES | 12/19/1991 | 07/810,480 | 11/2/1993 | 5,258,959 | US |
| NMKS-1132.00/US | Utility - ORG | Issued | CURRENT OFFSET SENSE AMPLIFIER OF A MODULATED CURRENT OR CURRENT UNBALANCE TYPE FOR PROGRAMMABLE MEMORIES | 5/4/1992 | 07/878,823 | 7/5/1994 | 5,327,379 | US |
| NMKS-1132.01/US | Utility - CIP | Issued | SENSE AMPLIFIER FOR PROGRAMMABLE MEMORIES WITH A VIRTUALLY ENHANCED SOURCE OF SIGNAL | 7/5/1994 | 08/270,498 | 10/24/1995 | 5,461,713 | US |
| NMKS-1133.00/US | Utility - ORG | Issued | ZERO-CONSUMPTION POWER-ON RESET CIRCUIT | 7/24/1992 | 07/919,606 | 4/18/1995 | 5,408,148 | US |
| NMKS-1134.00/US | Utility - ORG | Issued | ROW DECODER FOR NAND-TYPE ROM | 8/27/1992 | 07/936,857 | 6/14/1994 | 5,321,317 | US |
| NMKS-1135.00/US | Utility - ORG | Issued | METHOD OF FORMING HIGH-STABILITY METALLIC CONTACTS IN AN INTEGRATED CIRCUIT WITH ONE OR MORE METALLIZED LAYERS | 8/31/1992 | 07/938,731 | 9/13/1994 | 5,347,493 | US |
| NMKS-1136.00/US | Utility - CON | Issued | PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS | 3/28/1995 | 08/411,385 | 2/26/2002 | 6,350,676 | US |
| NMKS-1137.01/US | Utility - DIV | Issued | PROCESS FOR MANUFACTURING MOS-TYPE INTEGRATED CIRCUITS | 6/7/1995 | 08/475,555 | 12/9/1997 | 5,696,399 | US |
| NMKS-1137.02/US | Utility - CON | Issued | DYNAMIC REFERENCE SYSTEM FOR SENSE AMPLIFIER | 9/6/1995 | 08/524,080 | 9/2/1997 | 5,663,080 | US |
| NMKS-1138.01/US | Utility - CON | Issued | METALLIZATION OVER TUNGSTEN PLUGS | 10/12/1993 | 08/135,842 | 10/11/1994 | 5,355,333 | US |
| NMKS-1139.00/US | Utility - ORG | Issued | METALLIZATION OVER TUNGSTEN PLUGS | 5/26/1993 | 08/068,139 | 4/18/1995 | 5,407,861 | US |
| NMKS-1139.01/US | Utility - CON | Issued | METALLIZATION OVER TUNGSTEN PLUGS | 4/18/1995 | 08/423,397 | 7/28/1998 | 5,786,272 | US |

PATENT

REEL: 029505 FRAME: 0075

Exhibit A - US Issued Patents

| MEMO No. | Matter Type | Matter Status | Title | Filed Date | Serial No. | Issued Date | Patent No. | Country |
|------------------|-----------------|---------------|--|------------|------------|-------------|------------|---------|
| NMXXS-1140.00/US | Utility - ORG | Issued | LOW SWITCHING NOISE OUTPUT BUFFER | 6/28/1993 | 08/084,727 | 5/30/1995 | 5,420,525 | US |
| NMXXS-1141.00/US | Utility - ORG | Issued | INTEGRATED CIRCUIT ENTIRELY PROTECTED AGAINST ULTRAVIOLET RAYS | 6/30/1993 | 08/086,342 | 8/8/1995 | 5,440,510 | US |
| NMXXS-1142.02/US | Utility - CON | Issued | VOLTAGE REGULATOR FOR MEMORY DEVICE | 3/13/1996 | 08/615,727 | 1/6/1998 | 5,706,240 | US |
| NMXXS-1143.01/US | Utility - DIV | Issued | A NON-VOLATILE MEMORY IN AN INTEGRATED CIRCUIT | 5/23/1995 | 08/447,772 | 10/22/1996 | 5,568,418 | US |
| NMXXS-1143.02/US | Utility - CON | Issued | METHOD OF FABRICATING NON-VOLATILE MEMORIES WITH OVERLAPPING LAYERS | 6/6/1995 | 08/469,431 | 8/25/1998 | 5,798,279 | US |
| NMXXS-1144.00/US | Utility - ORG | Issued | METHOD OF MAKING NOR-TYPE ROM WITH LDD CELLS | 6/28/1993 | 08/084,971 | 4/18/1995 | 5,407,852 | US |
| NMXXS-1144.02/US | Utility - CON | Issued | NOR-TYPE ROM WITH LDD CELLS AND PROCESS OF FABRICATION | 12/23/1996 | 08/772,301 | 8/11/1998 | 5,793,086 | US |
| NMXXS-1145.01/US | Utility - DIV | Issued | METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES | 6/2/1995 | 08/460,540 | 5/7/1996 | 5,515,318 | US |
| NMXXS-1145.02/US | Utility - CON | Issued | METHOD OF EVALUATING THE GATE OXIDE OF NON-VOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES | 4/1/1997 | 08/829,935 | 8/11/1998 | 5,793,675 | US |
| NMXXS-1146.00/US | Utility - ORG | Issued | METHOD FOR MAKING DIRECT CONTACTS IN HIGH DENSITY MOS/CMOS PROCESSES | 11/17/1993 | 08/153,620 | 12/13/1994 | 5,372,956 | US |
| NMXXS-1147.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR FILTERING HIGH RESOLUTION DIGITAL SIGNALS | 1/28/1994 | 08/189,271 | 1/14/1997 | 5,594,677 | US |
| NMXXS-1148.00/US | Utility - ORG | Issued | METHOD AND APPARATUS FOR FILTERING DIGITAL SIGNALS | 1/28/1994 | 08/188,569 | 3/3/1998 | 5,724,395 | US |
| NMXXS-1149.00/US | Utility - ORG | Issued | PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING FLASH-EEPROM MEMORIES AND TRANSISTORS | 2/10/1994 | 08/195,369 | 6/10/1997 | 5,637,520 | US |
| NMXXS-1150.00/US | Utility - ORG | Abandoned | PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION | 2/15/1994 | 08/196,634 | 11/14/1995 | 5,466,622 | US |
| NMXXS-1150.01/US | Utility - CON | Issued | PROCESS FOR FABRICATING INTEGRATED DEVICES INCLUDING NONVOLATILE MEMORIES AND TRANSISTORS WITH TUNNEL OXIDE PROTECTION | 7/13/1995 | 08/502,329 | 6/15/1999 | 5,913,120 | US |
| NMXXS-1151.00/US | Utility - ORG | Issued | NONVOLATILE EPROM, EEPROM OR FLASH-EEPROM MEMORY WITH TUNNEL OXIDE PROTECTION | 2/15/1994 | 08/196,572 | 3/5/1996 | 5,497,345 | US |
| NMXXS-1152.00/US | Utility - ORG | Issued | NONVOLATILE FLASH-EEPROM MEMORY ARRAY WITH SOURCE CONTROL TRANSISTORS | 3/15/1994 | 08/214,049 | 4/16/1996 | 5,508,956 | US |
| NMXXS-1153.00/US | Utility - ORG | Issued | METHOD OF READING, ERASING AND PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS | 3/15/1994 | 08/212,907 | 12/24/1996 | 5,587,946 | US |
| NMXXS-1153.01/US | Utility - DIV | Issued | METHOD OF PROGRAMMING A NONVOLATILE FLASH-EEPROM MEMORY ARRAY USING SOURCE LINE SWITCHING TRANSISTORS | 6/2/1995 | 08/458,346 | 5/27/1997 | 5,633,822 | US |
| NMXXS-1154.00/US | Utility - ORG | Issued | SEMICONDUCTOR MEMORY WITH MEMORY MATRIX COMPRISING REDUNDANCY CELL COLUMNS ASSOCIATED WITH SINGLE MATRIX SECTORS | 3/29/1994 | 08/219,204 | 11/21/1995 | 5,469,399 | US |
| NMXXS-1155.01/US | Utility - DIV | Issued | METHOD OF EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES | 5/31/1995 | 08/454,854 | 2/18/1997 | 5,604,699 | US |
| NMXXS-1155.02/US | Utility - CON | Issued | METHOD FOR EVALUATING THE DIELECTRIC LAYER OF NONVOLATILE EPROM, EEPROM AND FLASH-EEPROM MEMORIES | 7/24/1996 | 08/685,782 | 1/27/1998 | 5,712,816 | US |
| NMXXS-1157.00/US | Utility - NSPCT | Issued | METHOD AND APPARATUS FOR CHECKING POST-ERASURE CONTENTS OF AN ERASABLE PERMANENT MEMORY | 10/9/1992 | 08/075,543 | 1/9/1996 | 5,483,492 | US |
| NMXXS-1158.00/US | Utility - ORG | Issued | SUPPLY VOLTAGE DISTRIBUTION SYSTEM WITH REDUCED RESISTANCE FOR SEMICONDUCTOR DEVICES | 7/27/2007 | 11/881,505 | 9/27/2011 | 8,027,217 | US |

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